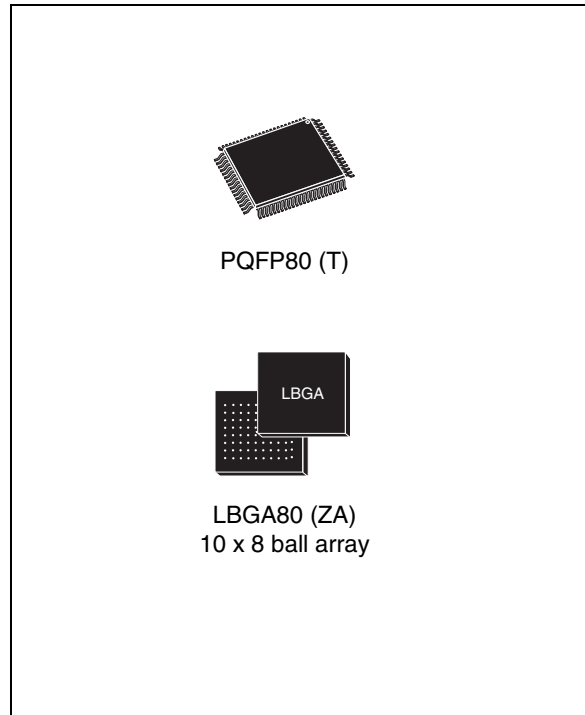


## Features

- Supply voltage
  - $V_{DD} = 2.7\text{ V to }3.6\text{ V}$  (45 ns) or  
 $V_{DD} = 2.5\text{ V to }3.3\text{ V}$  (55 ns)
  - $V_{DDQ} = V_{DDQIN} = 2.4\text{ V to }3.6\text{ V}$  for I/O buffers
- High performance
  - Access times: 45 and 55 ns
  - Synchronous burst reads
  - 75 MHz effective zero wait-state burst read
  - Asynchronous page reads
- M58BW32F memory organization:
  - Eight 64 Kbit small parameter blocks
  - Four 128 Kbit large parameter blocks
  - Sixty-two 512 Kbit main blocks
- M58BW16F memory organization:
  - Eight 64 Kbit parameter blocks
  - Thirty-one 512 Kbit main blocks
- Hardware block protection
  - $\overline{WP}$  pin to protect any block combination from Program and Erase operations
  - PEN signal for Program/Erase Enable
- Irreversible modify protection (OTP like) on 128 Kbits:
  - Block 1 (bottom device) or block 72 (top device) in the M58BW32F
  - Blocks 2 and 3 (bottom device) or blocks 36 and 35 (top device) in the M58BW16F
- Security
  - 64-bit unique device identifier (UID)
- Fast programming
  - Write to buffer and program capability
- Optimized for FDI drivers
  - Common Flash interface (CFI)
  - Fast Program/Erase Suspend feature in each block
- Low power consumption



- 100  $\mu\text{A}$  typical Standby current
- Electronic signature
  - Manufacturer code: 0020h
  - Top device codes:  
M58BW32FT: 8838h  
M58BW16FT: 883Ah
  - Bottom device codes:  
M58BW32FB: 8837h  
M58BW16FB: 8839h
- Automotive device grade 3:
  - Temperature:  $-40\text{ to }125\text{ }^\circ\text{C}$
  - Automotive grade certified

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|-------------------|-------------------------------------------|-----------|
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# 1 Description

The M58BW16F and M58BW32F are 16 and 32 Mbit non-volatile Flash memories, respectively. They can be erased electrically at block level and programmed in-system on a double-word basis using a 2.7 V to 3.6 V or 2.5 V to 3.3 V  $V_{DD}$  supply for the circuit and a 2.4 V to 3.6 V  $V_{DDQ}$  supply voltage for the input and output buffers.

In the rest of the document the M58BW16F and M58BW32F will be referred to as M58BWxxF unless otherwise specified.

The devices support Asynchronous (Latch Controlled and Page Read) and Synchronous Bus operations. The Synchronous Burst Read interface allows a high data transfer rate controlled by the Burst Clock signal, K. It is capable of bursting fixed or unlimited lengths of data. The burst type, latency and length are configurable and can be easily adapted to a large variety of system clock frequencies and microprocessors. All write operations are asynchronous. On power-up the memory defaults to Read mode with an Asynchronous Bus.

The device features an asymmetrical block architecture:

- The M58BW32F has an array of 62 main blocks of 512 Kbits each, plus 4 large parameter blocks of 128 Kbits each and 8 small parameter blocks of 64 Kbits each. The large and small parameter blocks are located either at the top (M58BW32FT) or at the bottom (M58BW32FB) of the address space. The first large parameter block is referred to as boot block and can be used either to store a boot code or parameters. The memory array organization is detailed in [Table 2: M58BW32F top boot block addresses](#) and [Table 3: M58BW32F bottom boot block addresses](#).
- The M58BW16F has an array of 8 parameter blocks of 64 Kbits each and 31 main blocks of 512 Kbits each. In the M58BW16FT the parameter blocks are located at the top of the address space whereas in the M58BW16FB, they are located at the bottom. The memory array organization is detailed in [Table 4: M58BW16F top boot block addresses](#) and [Table 5: M58BW16F bottom boot block addresses](#).

Program and Erase commands are written to the command interface of the memory. An on-chip Program/Erase controller simplifies the process of programming or erasing the memory by taking care of all of the special operations that are required to update the memory contents. The end of a Program or Erase operation can be detected and any error conditions identified in the Status Register. The command set required to control the memory is consistent with JEDEC standards.

Erase can be suspended in order to perform either Read or Program in any other block, and then resumed. Program can be suspended to Read data in any other block, and then resumed. Each block can be programmed and erased over 100,000 cycles.

All blocks are protected during power-up. The M58BWxxF features five different levels of hardware and software block protection to avoid unwanted Program/Erase operations:

- Write/Protect Enable input,  $\overline{WP}$ , hardware protects a combination of blocks from Program and Erase operations. The blocks to be protected are configured individually by issuing a Set Block Protection Configuration Register or a Clear Block Protection Configuration Register command.
- All Program or Erase operations are blocked when Reset,  $\overline{RP}$ , is held Low.
- A Program/Erase Enable input, PEN, is used to protect all blocks, preventing Program and Erase operations from affecting their data.
- A permanent user-enabled protection against Modify operations is available:
  - on one specific 128-Kbit parameter block in the M58BW32F – block 1 for bottom devices or block 72 for top devices
  - on two specific 64-Kbit parameter blocks in the M58BW16F – blocks 2 and 3 for bottom devices or blocks 36 and 35 for top devices.

A Reset/Power-down mode is entered when the  $\overline{RP}$  input is Low. In this mode the power consumption is reduced to the standby level, the device is write protected and both the Status and Burst Configuration Registers are cleared. A recovery time is required when the  $\overline{RP}$  input goes High.

A manufacturer code and a device code are available. They can be read from the memory allowing programming equipment or applications to automatically match their interface to the characteristics of the memory.

Finally, the M58BWxxF features a 64-bit unique device identifier (UID) which is programmed by Numonyx on the production line. It is unique for each die and can be used to implement cryptographic algorithms to improve security. Information is available in the CFI area (see [Table 32: M58BW16F extended query information](#)).

The memory is offered in PQFP80 (14 x 20 mm) and LPGA80 (1.0 mm pitch) packages and it is supplied with all the bits erased (set to '1').



Figure 1. Logic diagram

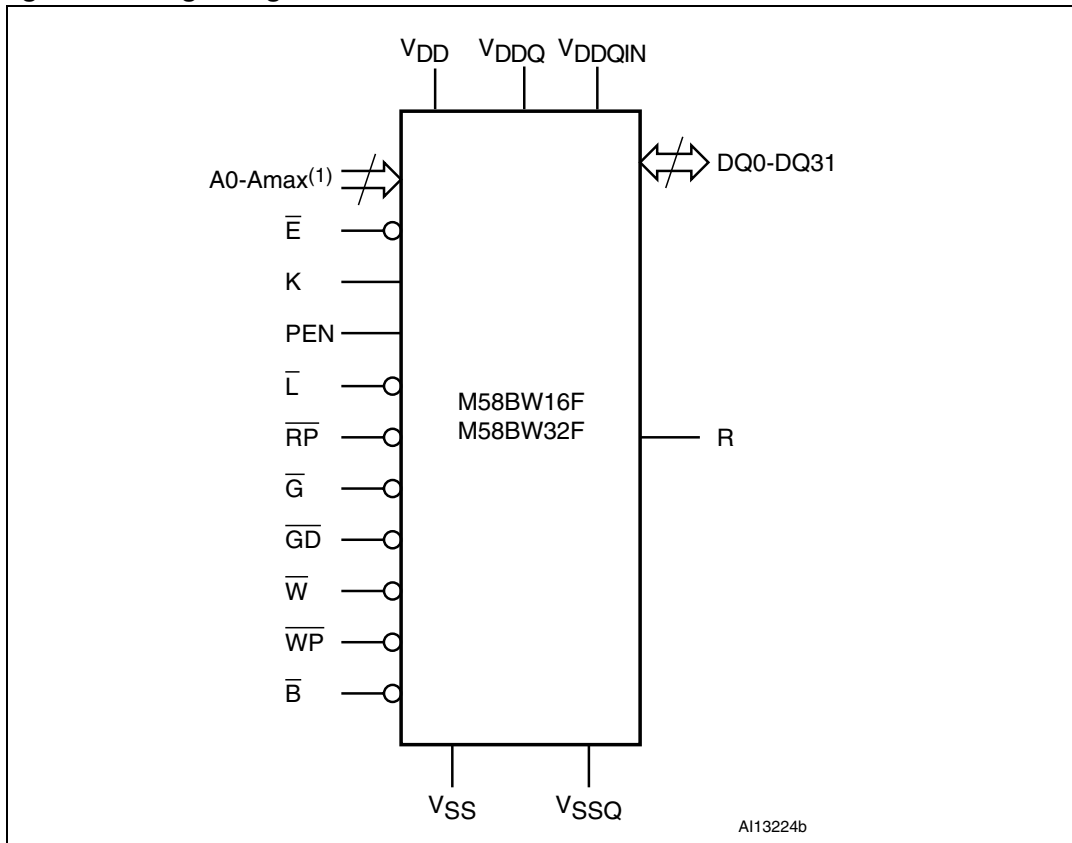
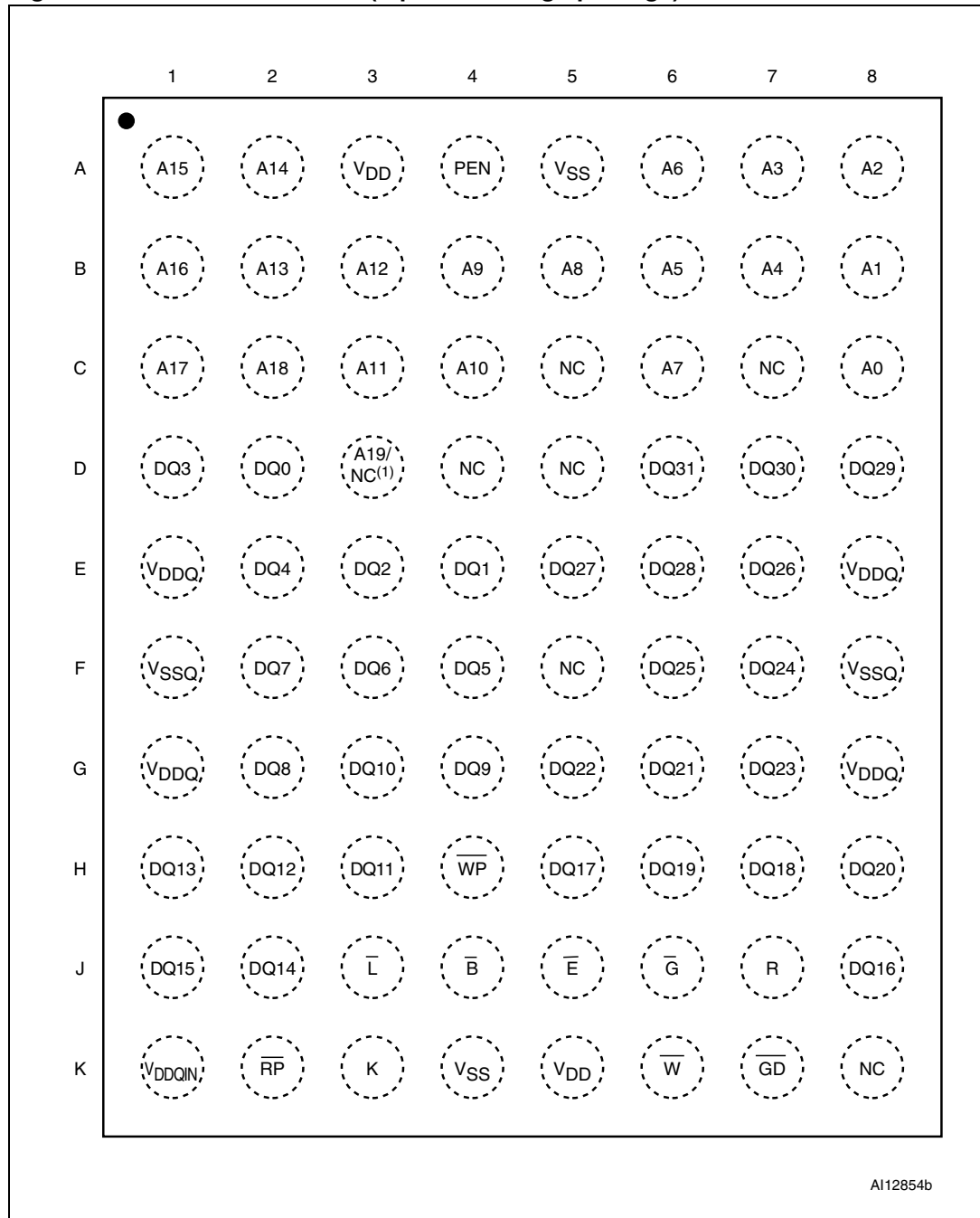


Table 1. Signal names

| Signal name            | Function                                        | Direction |
|------------------------|-------------------------------------------------|-----------|
| A0-Amax <sup>(1)</sup> | Address inputs                                  | Inputs    |
| DQ0-DQ7                | Data input/output, command input                | I/O       |
| DQ8-DQ15               | Data input/output, Burst Configuration Register | I/O       |
| DQ16-DQ31              | Data input/output                               | I/O       |
| $\overline{B}$         | Burst Address Advance input                     | Input     |
| $\overline{E}$         | Chip Enable input                               | Input     |
| $\overline{G}$         | Output Enable input                             | Input     |
| K                      | Burst Clock input                               | Input     |
| $\overline{L}$         | Latch Enable input                              | Input     |
| R                      | Valid Data Ready output                         | Output    |
| $\overline{RP}$        | Reset/Power-down input                          | Input     |
| $\overline{W}$         | Write Enable input                              | Input     |
| $\overline{GD}$        | Output Disable input                            | Input     |
| $\overline{WP}$        | Write Protect input                             | Input     |
| V <sub>DD</sub>        | Supply voltage                                  |           |
| V <sub>DDQ</sub>       | Power supply for output buffers                 |           |
| V <sub>DDQIN</sub>     | Power supply for input buffers only             |           |
| PEN                    | Program/Erase Enable                            | Input     |
| V <sub>SS</sub>        | Ground                                          |           |
| V <sub>SSQ</sub>       | Input/output ground                             |           |
| NC                     | Not connected internally                        |           |
| DU                     | Don't use as internally connected               |           |

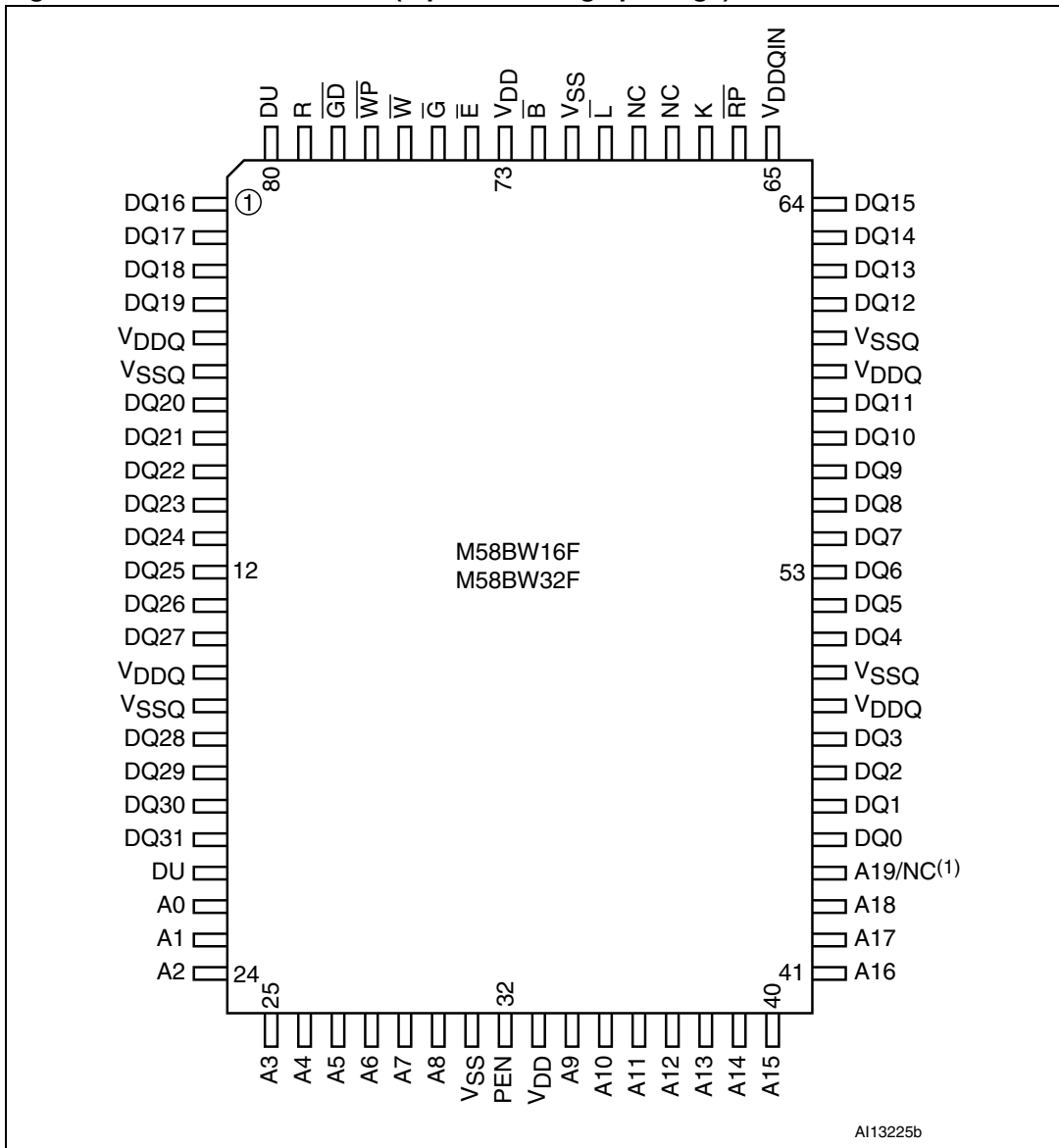
1. Amax is equal to A18 in the M58BW16F, and to A19 in the M58BW32F.

Figure 2. LPGA connections (top view through package)



1. Ball D3 is NC in the M58BW16F and A19 in the M58BW32F.

Figure 3. PQFP connections (top view through package)



## 1.1 Block protection

The M58BWxxF features four different levels of block protection.

- **Write Protect pin,  $\overline{WP}$** , - When  $\overline{WP}$  is Low,  $V_{IL}$ , the protection status that has been configured in the Block Protection Configuration Register is activated. The Block Protection Configuration Register is volatile. Any combination of blocks is possible. Any attempt to program or erase a protected block will return an error in the Status Register (see [Table 13: Status Register bits](#)).
- **Reset/Power-down pin,  $\overline{RP}$** , - If the device is held in reset mode ( $\overline{RP}$  at  $V_{IL}$ ), no Program or Erase operation can be performed on any block.
- **Program/Erase Enable,  $PEN$** , - The Program/Erase Enable input,  $PEN$ , protects all blocks by preventing Program and Erase operations from modifying the data. Prior to issuing a Program or Erase command, the Program/Erase Enable must be set to High ( $V_{IH}$ ). If it is Low ( $V_{IL}$ ), the Program or Erase operation is not accepted and an error is generated in the Status Register.
- **Permanent protection against modify operations** - specific OTP-like blocks can be permanently protected against modify operations (Program/Erase):
  - in the M58BW32F, a unique 128-Kbit parameter block – block 1 (01000h-01FFFh) for bottom devices or block 72 (FE000h-FEFFFh) for top devices
  - in the M58BW16F, two 64-Kbit parameter blocks – blocks 2 and 3 (01000h-01FFFh) for bottom devices or blocks 36 and 35 (7E000h-7EFFFh) for top devices

This protection is user-enabled. Details of how this protection is activated are provided in a dedicated application note.

After a device reset the first two kinds of block protection ( $\overline{WP}$ ,  $\overline{RP}$ ) can be combined to give a flexible block protection. All blocks are protected at power-up.

Table 2. M58BW32F top boot block addresses

| #  | Size (Kbit) | Address range <sup>(1)</sup> |
|----|-------------|------------------------------|
| 73 | 128         | FF000h-FFFFFh                |
| 72 | 128         | FE000h-FEFFFh <sup>(2)</sup> |
| 71 | 128         | FD000h-FDFFFh                |
| 70 | 128         | FC000h-FCFFFh                |
| 69 | 64          | FB800h-FBFFFh                |
| 68 | 64          | FB000h-FB7FFh                |
| 67 | 64          | FA800h-FAFFFh                |
| 66 | 64          | FA000h-FA7FFh                |
| 65 | 64          | F9800h-F9FFFh                |
| 64 | 64          | F9000h-F97FFh                |
| 63 | 64          | F8800h-F8FFFh                |
| 62 | 64          | F8000h-F87FFh                |
| 61 | 512         | F4000h-F7FFFh                |
| 60 | 512         | F0000h-F3FFFh                |
| 59 | 512         | EC000h-EFFFFh                |
| 58 | 512         | E8000h-EBFFFh                |
| 57 | 512         | E4000h-E7FFFh                |
| 56 | 512         | E0000h-E3FFFh                |
| 55 | 512         | DC000h-DFFFFh                |
| 54 | 512         | D8000h-DBFFFh                |
| 53 | 512         | D4000h-D7FFFh                |
| 52 | 512         | D0000h-D3FFFh                |
| 51 | 512         | CC000h-CFFFFh                |
| 50 | 512         | C8000h-CBFFFh                |
| 49 | 512         | C4000h-C7FFFh                |
| 48 | 512         | C0000h-C3FFFh                |
| 47 | 512         | BC000h-BFFFFh                |
| 46 | 512         | B8000h-BBFFFh                |
| 45 | 512         | B4000h-B7FFFh                |
| 44 | 512         | B0000h-B3FFFh                |
| 43 | 512         | AC000h-AFFFFh                |
| 42 | 512         | A8000h-ABFFFh                |
| 41 | 512         | A4000h-A7FFFh                |
| 40 | 512         | A0000h-A3FFFh                |
| 39 | 512         | 9C000h-9FFFFh                |
| 38 | 512         | 98000h-9BFFFh                |
| 37 | 512         | 94000h-97FFFh                |
| 36 | 512         | 90000h-93FFFh                |

**Table 2. M58BW32F top boot block addresses (continued)**

| #  | Size (Kbit) | Address range <sup>(1)</sup> |
|----|-------------|------------------------------|
| 35 | 512         | 8C000h-8FFFFh                |
| 34 | 512         | 88000h-8BFFFh                |
| 33 | 512         | 84000h-87FFFh                |
| 32 | 512         | 80000h-83FFFh                |
| 31 | 512         | 7C000h-7FFFFh                |
| 30 | 512         | 78000h-7BFFFh                |
| 29 | 512         | 74000h-77FFFh                |
| 28 | 512         | 70000h-73FFFh                |
| 27 | 512         | 6C000h-6FFFFh                |
| 26 | 512         | 68000h-6BFFFh                |
| 25 | 512         | 64000h-67FFFh                |
| 24 | 512         | 60000h-63FFFh                |
| 23 | 512         | 5C000h-5FFFFh                |
| 22 | 512         | 58000h-5BFFFh                |
| 21 | 512         | 54000h-57FFFh                |
| 20 | 512         | 50000h-53FFFh                |
| 19 | 512         | 4C000h-4FFFFh                |
| 18 | 512         | 48000h-4BFFFh                |
| 17 | 512         | 44000h-47FFFh                |
| 16 | 512         | 40000h-43FFFh                |
| 15 | 512         | 3C000h-3FFFFh                |
| 14 | 512         | 38000h-3BFFFh                |
| 13 | 512         | 34000h-37FFFh                |
| 12 | 512         | 30000h-33FFFh                |
| 11 | 512         | 2C000h-2FFFFh                |
| 10 | 512         | 28000h-2BFFFh                |
| 9  | 512         | 24000h-27FFFh                |
| 8  | 512         | 20000h-23FFFh                |
| 7  | 512         | 1C000h-1FFFFh                |
| 6  | 512         | 18000h-1BFFFh                |
| 5  | 512         | 14000h-17FFFh                |
| 4  | 512         | 10000h-13FFFh                |
| 3  | 512         | 0C000h-0FFFFh                |
| 2  | 512         | 08000h-0BFFFh                |
| 1  | 512         | 04000h-07FFFh                |
| 0  | 512         | 00000h-03FFFh                |

1. Addresses are indicated in 32-bit addressing.

2. OTP block.

**Table 3. M58BW32F bottom boot block addresses**

| #  | Size (Kbit) | Address range <sup>(1)</sup> |
|----|-------------|------------------------------|
| 73 | 512         | FC000h-FFFFFh                |
| 72 | 512         | F8000h-FBFFFh                |
| 71 | 512         | F4000h-F7FFFh                |
| 70 | 512         | F0000h-F3FFFh                |
| 69 | 512         | EC000h-EFFFFh                |
| 68 | 512         | E8000h-EBFFFh                |
| 67 | 512         | E4000h-E7FFFh                |
| 66 | 512         | E0000h-E3FFFh                |
| 65 | 512         | DC000h-DFFFFh                |
| 64 | 512         | D8000h-DBFFFh                |
| 63 | 512         | D4000h-D7FFFh                |
| 62 | 512         | D0000h-D3FFFh                |
| 61 | 512         | CC000h-CFFFFh                |
| 60 | 512         | C8000h-CBFFFh                |
| 59 | 512         | C4000h-C7FFFh                |
| 58 | 512         | C0000h-C3FFFh                |
| 57 | 512         | BC000h-BFFFFh                |
| 56 | 512         | B8000h-BBFFFh                |
| 55 | 512         | B4000h-B7FFFh                |
| 54 | 512         | B0000h-B3FFFh                |
| 53 | 512         | AC000h-AFFFFh                |
| 52 | 512         | A8000h-ABFFFh                |
| 51 | 512         | A4000h-A7FFFh                |
| 50 | 512         | A0000h-A3FFFh                |
| 49 | 512         | 9C000h-9FFFFh                |
| 48 | 512         | 98000h-9BFFFh                |
| 47 | 512         | 94000h-97FFFh                |
| 46 | 512         | 90000h-93FFFh                |
| 45 | 512         | 8C000h-8FFFFh                |
| 44 | 512         | 88000h-8BFFFh                |
| 43 | 512         | 84000h-87FFFh                |
| 42 | 512         | 80000h-83FFFh                |
| 41 | 512         | 7C000h-7FFFFh                |
| 40 | 512         | 78000h-7BFFFh                |
| 39 | 512         | 74000h-77FFFh                |
| 38 | 512         | 70000h-73FFFh                |
| 37 | 512         | 6C000h-6FFFFh                |
| 36 | 512         | 68000h-6BFFFh                |



**Table 3. M58BW32F bottom boot block addresses (continued)**

| #  | Size (Kbit) | Address range <sup>(1)</sup> |
|----|-------------|------------------------------|
| 35 | 512         | 64000h-67FFFh                |
| 34 | 512         | 60000h-63FFFh                |
| 33 | 512         | 5C000h-5FFFFh                |
| 32 | 512         | 58000h-5BFFFh                |
| 31 | 512         | 54000h-57FFFh                |
| 30 | 512         | 50000h-53FFFh                |
| 29 | 512         | 4C000h-4FFFFh                |
| 28 | 512         | 48000h-4BFFFh                |
| 27 | 512         | 44000h-47FFFh                |
| 26 | 512         | 40000h-43FFFh                |
| 25 | 512         | 3C000h-3FFFFh                |
| 24 | 512         | 38000h-3BFFFh                |
| 23 | 512         | 34000h-37FFFh                |
| 22 | 512         | 30000h-33FFFh                |
| 21 | 512         | 2C000h-2FFFFh                |
| 20 | 512         | 28000h-2BFFFh                |
| 19 | 512         | 24000h-27FFFh                |
| 18 | 512         | 20000h-23FFFh                |
| 17 | 512         | 1C000h-1FFFFh                |
| 16 | 512         | 18000h-1BFFFh                |
| 15 | 512         | 14000h-17FFFh                |
| 14 | 512         | 10000h-13FFFh                |
| 13 | 512         | 0C000h-0FFFFh                |
| 12 | 512         | 08000h-0BFFFh                |
| 11 | 64          | 07800h-07FFFh                |
| 10 | 64          | 07000h-077FFh                |
| 9  | 64          | 06800h-06FFFh                |
| 8  | 64          | 06000h-067FFh                |
| 7  | 64          | 05800h-05FFFh                |
| 6  | 64          | 05000h-057FFh                |
| 5  | 64          | 04800h-04FFFh                |
| 4  | 64          | 04000h-047FFh                |
| 3  | 128         | 03000h-03FFFh                |
| 2  | 128         | 02000h-02FFFh                |
| 1  | 128         | 01000h-01FFFh <sup>(2)</sup> |
| 0  | 128         | 00000h-00FFFh                |

1. Addresses are indicated in 32-bit word addressing.

2. OTP block.

**Table 4. M58BW16F top boot block addresses**

| #                 | Size (Kbit) | Address range |
|-------------------|-------------|---------------|
| 38                | 64          | 7F800h-7FFFFh |
| 37                | 64          | 7F000h-7F7FFh |
| 36 <sup>(1)</sup> | 64          | 7E800h-7EFFFh |
| 35 <sup>(1)</sup> | 64          | 7E000h-7E7FFh |
| 34                | 64          | 7D800h-7DFFFh |
| 33                | 64          | 7D000h-7D7FFh |
| 32                | 64          | 7C800h-7CFFFh |
| 31                | 64          | 7C000h-7C7FFh |
| 30                | 512         | 78000h-7BFFFh |
| 29                | 512         | 74000h-77FFFh |
| 28                | 512         | 70000h-73FFFh |
| 27                | 512         | 6C000h-6FFFFh |
| 26                | 512         | 68000h-6BFFFh |
| 25                | 512         | 64000h-67FFFh |
| 24                | 512         | 60000h-63FFFh |
| 23                | 512         | 5C000h-5FFFFh |
| 22                | 512         | 58000h-5BFFFh |
| 21                | 512         | 54000h-57FFFh |
| 20                | 512         | 50000h-53FFFh |
| 19                | 512         | 4C000h-4FFFFh |
| 18                | 512         | 48000h-4BFFFh |
| 17                | 512         | 44000h-47FFFh |
| 16                | 512         | 40000h-43FFFh |
| 15                | 512         | 3C000h-3FFFFh |
| 14                | 512         | 38000h-3BFFFh |
| 13                | 512         | 34000h-37FFFh |
| 12                | 512         | 30000h-33FFFh |
| 11                | 512         | 2C000h-2FFFFh |
| 10                | 512         | 28000h-2BFFFh |
| 9                 | 512         | 24000h-27FFFh |
| 8                 | 512         | 20000h-23FFFh |
| 7                 | 512         | 1C000h-1FFFFh |
| 6                 | 512         | 18000h-1BFFFh |
| 5                 | 512         | 14000h-17FFFh |
| 4                 | 512         | 10000h-13FFFh |
| 3                 | 512         | 0C000h-0FFFFh |
| 2                 | 512         | 08000h-0BFFFh |
| 1                 | 512         | 04000h-07FFFh |
| 0                 | 512         | 00000h-03FFFh |

1. OTP block.

Table 5. M58BW16F bottom boot block addresses

| #                | Size (Kbit) | Address range |
|------------------|-------------|---------------|
| 38               | 512         | 7C000h-7FFFFh |
| 37               | 512         | 78000h-7BFFFh |
| 36               | 512         | 74000h-77FFFh |
| 35               | 512         | 70000h-73FFFh |
| 34               | 512         | 6C000h-6FFFFh |
| 33               | 512         | 68000h-6BFFFh |
| 32               | 512         | 64000h-67FFFh |
| 31               | 512         | 60000h-63FFFh |
| 30               | 512         | 5C000h-5FFFFh |
| 29               | 512         | 58000h-5BFFFh |
| 28               | 512         | 54000h-57FFFh |
| 27               | 512         | 50000h-53FFFh |
| 26               | 512         | 4C000h-4FFFFh |
| 25               | 512         | 48000h-4BFFFh |
| 24               | 512         | 44000h-47FFFh |
| 23               | 512         | 40000h-43FFFh |
| 22               | 512         | 3C000h-3FFFFh |
| 21               | 512         | 38000h-3BFFFh |
| 20               | 512         | 34000h-37FFFh |
| 19               | 512         | 30000h-33FFFh |
| 18               | 512         | 2C000h-2FFFFh |
| 17               | 512         | 28000h-2BFFFh |
| 16               | 512         | 24000h-27FFFh |
| 15               | 512         | 20000h-23FFFh |
| 14               | 512         | 1C000h-1FFFFh |
| 13               | 512         | 18000h-1BFFFh |
| 12               | 512         | 14000h-17FFFh |
| 11               | 512         | 10000h-13FFFh |
| 10               | 512         | 0C000h-0FFFFh |
| 9                | 512         | 08000h-0BFFFh |
| 8                | 512         | 04000h-07FFFh |
| 7                | 64          | 03800h-03FFFh |
| 6                | 64          | 03000h-037FFh |
| 5                | 64          | 02800h-02FFFh |
| 4                | 64          | 02000h-027FFh |
| 3 <sup>(1)</sup> | 64          | 01800h-01FFFh |
| 2 <sup>(1)</sup> | 64          | 01000h-017FFh |
| 1                | 64          | 00800h-00FFFh |
| 0                | 64          | 00000h-007FFh |

1. OTP block.

## 2 Signal descriptions

See [Figure 1: Logic diagram](#) and [Table 1: Signal names](#), for a brief overview of the signals connected to this device.

### 2.1 Address inputs (A0-Amax)

Amax is equal to A18 in the M58BW16F, and to A19 in the M58BW32F.

The Address inputs are used to select the cells to access in the memory array during Bus operations. During Bus Write operations they control the commands sent to the command interface of the Program/Erase controller. Chip Enable must be Low when selecting the addresses.

The Address inputs are latched on the rising edge of Latch Enable  $\bar{L}$  or Burst Clock K, whichever occurs first, in a Read operation. The Address inputs are latched on the rising edge of Chip Enable, Write Enable or Latch Enable, whichever occurs first in a Write operation. The address latch is transparent when Latch Enable is Low,  $V_{IL}$ . The address is internally latched in an Erase or Program operation.

### 2.2 Data inputs/outputs (DQ0-DQ31)

The Data inputs/outputs output the data stored at the selected address during a Bus Read operation, or are used to input the data during a program operation. During Bus Write operations they represent the commands sent to the command interface of the Program/Erase controller. When used to input data or Write commands they are latched on the rising edge of Write Enable or Chip Enable, whichever occurs first.

When Chip Enable and Output Enable are both Low,  $V_{IL}$ , and Output Disable is at  $V_{IH}$ , the data bus outputs data from the memory array, the Electronic Signature, the Block Protection Configuration Register, the CFI information or the contents of Burst Configuration Register or Status Register. The data bus is high impedance when the device is deselected with Chip Enable at  $V_{IH}$ , Output Enable at  $V_{IH}$ , Output Disable at  $V_{IL}$  or Reset/Power-down at  $V_{IL}$ . The Status Register content is output on DQ0-DQ7 and DQ8-DQ31 are at  $V_{IL}$ .

### 2.3 Chip Enable ( $\bar{E}$ )

The Chip Enable,  $\bar{E}$ , input activates the memory control logic, input buffers, decoders and sense amplifiers. Chip Enable,  $\bar{E}$ , at  $V_{IH}$  deselects the memory and reduces the power consumption to the standby level.

### 2.4 Output Enable ( $\bar{G}$ )

The Output Enable,  $\bar{G}$ , gates the outputs through the data output buffers during a Read operation, when Output Disable  $\bar{GD}$  is at  $V_{IH}$ . When Output Enable  $\bar{G}$  is at  $V_{IH}$ , the outputs are high impedance independently of Output Disable.

## 2.5 Output Disable ( $\overline{\text{GD}}$ )

The Output Disable,  $\overline{\text{GD}}$ , deactivates the data output buffers. When Output Disable,  $\overline{\text{GD}}$ , is at  $V_{\text{IH}}$ , the outputs are driven by the Output Enable. When Output Disable,  $\overline{\text{GD}}$ , is at  $V_{\text{IL}}$ , the outputs are high impedance independently of Output Enable. The Output Disable pin must be connected to an external pull-up resistor as there is no internal pull-up resistor to drive the pin.

## 2.6 Write Enable ( $\overline{\text{W}}$ )

The Write Enable,  $\overline{\text{W}}$ , input controls writing to the command interface, input address and data latches. Both addresses and data can be latched on the rising edge of Write Enable (also see Latch Enable,  $\overline{\text{L}}$ ).

## 2.7 Reset/Power-down ( $\overline{\text{RP}}$ )

The Reset/Power-down,  $\overline{\text{RP}}$ , is used to apply a hardware reset to the memory. A hardware reset is achieved by holding Reset/Power-down Low,  $V_{\text{IL}}$ , for at least  $t_{\text{PLPH}}$ . Writing is inhibited to protect data, the command interface and the Program/Erase controller are reset. The Status Register information is cleared and power consumption is reduced to the standby level ( $I_{\text{DD1}}$ ). The device acts as deselected, that is the data outputs are high impedance.

After Reset/Power-down goes High,  $V_{\text{IH}}$ , the memory will be ready for Bus Read operations after a delay of  $t_{\text{PHEL}}$  or Bus Write operations after  $t_{\text{PHWL}}$ .

If Reset/Power-down goes Low,  $V_{\text{IL}}$ , during a Block Erase or a Program operation, the internal state machine handles the operation as a Program/Erase Suspend, so the maximum time defined in [Table 12: Program, Erase times and endurance cycles](#) must be applied.

During power-up power should be applied simultaneously to  $V_{\text{DD}}$  and  $V_{\text{DDQIN}}$  with  $\overline{\text{RP}}$  held at  $V_{\text{IL}}$ . When the supplies are stable  $\overline{\text{RP}}$  is taken to  $V_{\text{IH}}$ . Output Enable,  $\overline{\text{G}}$ , Chip Enable,  $\overline{\text{E}}$ , and Write Enable,  $\overline{\text{W}}$ , should be held at  $V_{\text{IH}}$  during power-up.

In an application, it is recommended to associate the Reset/Power-down pin,  $\overline{\text{RP}}$ , with the reset signal of the microprocessor. Otherwise, if a Reset operation occurs while the memory is performing an Erase or program operation, the memory may output the Status Register information instead of being initialized to the default Asynchronous Random Read mode.

See [Table 24](#) and [Figure 22: Reset, Power-down and Power-up AC waveforms - Control pins Low](#), for more details.

## 2.8 Program/Erase Enable (PEN)

The Program/Erase Enable input, PEN, protects all blocks by preventing Program and Erase operations from modifying the data.

Prior to issuing a Program or Erase command, the Program/Erase Enable must be set to High ( $V_{\text{IH}}$ ). If it is Low ( $V_{\text{IL}}$ ), the Program or Erase operation is not accepted and an error is generated in the Status Register.

## 2.9 Latch Enable ( $\overline{L}$ )

The Bus Interface can be configured to latch the Address inputs on the rising edge of Latch Enable,  $\overline{L}$ , for Asynchronous Latch Enable Controlled Read or Write or Synchronous Burst Read operations. In Synchronous Burst Read operations the address is latched on the active edge of the Clock when Latch Enable is Low,  $V_{IL}$ . Once latched, the addresses may change without affecting the address used by the memory. When Latch Enable is Low,  $V_{IL}$ , the latch is transparent. Latch Enable,  $\overline{L}$ , can remain at  $V_{IL}$  for Asynchronous Random Read and Write operations.

## 2.10 Burst Clock (K)

The Burst Clock, K, is used to synchronize the memory with the external bus during Synchronous Burst Read operations. Bus signals are latched on the active edge of the Clock. In Synchronous Burst Read mode the address is latched on the first rising clock edge when Latch Enable is Low,  $V_{IL}$ , or on the rising edge of Latch Enable, whichever occurs first. During Asynchronous Bus Operations the Clock is not used.

## 2.11 Burst Address Advance ( $\overline{B}$ )

The Burst Address Advance,  $\overline{B}$ , controls the advancing of the address by the internal address counter during Synchronous Burst Read operations.

Burst Address Advance,  $\overline{B}$ , is only sampled on the active clock edge of the Clock when the X-latency time has expired. If Burst Address Advance is Low,  $V_{IL}$ , the internal address counter advances. If Burst Address Advance is High,  $V_{IH}$ , the internal address counter does not change; the same data remains on the Data inputs/outputs and Burst Address Advance is not sampled until the Y-latency expires.

The Burst Address Advance,  $\overline{B}$ , may be tied to  $V_{IL}$ .

## 2.12 Valid Data Ready (R)

The Valid Data Ready output, R, can be used during Synchronous Burst Read operations to identify if the memory is ready to output data or not. The Valid Data Ready output can be configured to be active on the clock edge of the invalid data read cycle or one cycle before. Valid Data Ready, at  $V_{IH}$ , indicates that new data is or will be available. When Valid Data Ready is Low,  $V_{IL}$ , the previous data outputs remain active.

## 2.13 Write Protect ( $\overline{WP}$ )

The Write Protect,  $\overline{WP}$ , provides protection against Program or Erase operations. When Write Protect,  $\overline{WP}$ , is at  $V_{IL}$ , the protection status that has been configured in the Block Protection Configuration Register is activated. Program and Erase operations to protected blocks are disabled. When Write Protect  $\overline{WP}$  is at  $V_{IH}$  all the blocks can be programmed or erased, if no other protection is used.

## 2.14 Supply voltage ( $V_{DD}$ )

The supply voltage,  $V_{DD}$ , is the core power supply. All internal circuits draw their current from the  $V_{DD}$  pin, including the Program/Erase controller.

## 2.15 Output supply voltage ( $V_{DDQ}$ )

The output supply voltage,  $V_{DDQ}$ , is the output buffer power supply for all operations (Read, Program and Erase) used for DQ0-DQ31 when used as outputs.

## 2.16 Input supply voltage ( $V_{DDQIN}$ )

The input supply voltage,  $V_{DDQIN}$ , is the power supply for all input signal. Input signals are:  $\overline{K}$ ,  $\overline{B}$ ,  $\overline{L}$ ,  $\overline{W}$ ,  $\overline{GD}$ ,  $\overline{G}$ ,  $\overline{E}$ , A0-Amax and DQ0-DQ31, when used as inputs.

## 2.17 Ground ( $V_{SS}$ and $V_{SSQ}$ )

The ground  $V_{SS}$  is the reference for the internal supply voltage  $V_{DD}$ . The ground  $V_{SSQ}$  is the reference for the output and input supplies  $V_{DDQ}$ , and  $V_{DDQIN}$ . It is essential to connect  $V_{SS}$  and  $V_{SSQ}$  together.

*Note:* A 0.1  $\mu\text{F}$  capacitor should be connected between the supply voltages,  $V_{DD}$ ,  $V_{DDQ}$  and  $V_{DDQIN}$  and the grounds,  $V_{SS}$  and  $V_{SSQ}$  to decouple the current surges from the power supply. The PCB track widths must be sufficient to carry the currents required during all operations of the parts, see [Table 18: DC characteristics](#), for maximum current supply requirements.

## 2.18 Don't use (DU)

This pin should not be used as it is internally connected. Its voltage level can be between  $V_{SS}$  and  $V_{DDQ}$  or leave it unconnected.

## 2.19 Not connected (NC)

This pin is not physically connected to the device.

## 3 Bus operations

Each bus operations that controls the memory is described in this section, see tables 6 and 7 Bus operations, for a summary. The bus operation is selected through the Burst Configuration Register; the bits in this register are described at the end of this section.

On power-up or after a hardware reset the memory defaults to Asynchronous Bus Read and Asynchronous Bus Write. No synchronous operation can be performed until the Burst Control Register has been configured.

The Electronic Signature, Block Protection Configuration, CFI or Status Register will be read in asynchronous mode regardless of the Burst Control Register settings.

Typically glitches of less than 5 ns on Chip Enable or Write Enable are ignored by the memory and do not affect bus operations.

### 3.1 Asynchronous Bus operations

For asynchronous bus operations refer to [Table 6](#) together with the following text. The read access will start at whichever of the three following events occurs last: valid address transition, Chip Enable,  $\bar{E}$ , going Low,  $V_{IL}$  or Latch Enable,  $\bar{L}$ , going Low,  $V_{IL}$ .

#### 3.1.1 Asynchronous Bus Read

Asynchronous Bus Read operations read from the memory cells, or specific registers (Electronic Signature, Block Protection Configuration Register, Status Register, CFI and Burst Configuration Register) in the command interface. A valid bus operation involves setting the desired address on the Address inputs, applying a Low signal,  $V_{IL}$ , to Chip Enable and Output Enable and keeping Write Enable and Output Disable High,  $V_{IH}$ . The Data inputs/outputs will output the value, see [Figure 7: Asynchronous Bus Read AC waveforms](#), and [Table 19: Asynchronous Bus Read AC characteristics](#), for details of when the output becomes valid.

Asynchronous Read is the default read mode which the device enters on power-up or on return from Reset/Power-down.

#### 3.1.2 Asynchronous Latch Controlled Bus Read

Asynchronous Latch Controlled Bus Read operations read from the memory cells or specific registers in the command interface. The address is latched in the memory before the value is output on the data bus, allowing the address to change during the cycle without affecting the address that the memory uses.

A valid bus operation involves setting the desired address on the Address inputs, setting Chip Enable and Latch Enable Low,  $V_{IL}$  and keeping Write Enable High,  $V_{IH}$ ; the address is latched on the rising edge of Latch Enable. Once latched, the Address inputs can change. Set Output Enable Low,  $V_{IL}$ , to read the data on the Data inputs/outputs; see [Figure 8: Asynchronous Latch Controlled Bus Read AC waveforms](#) and [Table 19: Asynchronous Bus Read AC characteristics](#), for details on when the output becomes valid.

Note that, since the Latch Enable input is transparent when set Low,  $V_{IL}$ , Asynchronous Bus Read operations can be performed when the memory is configured for Asynchronous Latch Enable bus operations by holding Latch Enable Low,  $V_{IL}$  throughout the bus operation.



### 3.1.3 Asynchronous Page Read

Asynchronous Page Read operations are used to read from several addresses within the same memory page. Each memory page is 4 double-words and is addressed by the address inputs A0 and A1.

Data is read internally and stored in the page buffer. Valid bus operations are the same as Asynchronous Bus Read operations but with different timings. The first read operation within the page has identical timings, subsequent reads within the same page have much shorter access times. If the page changes then the normal, longer timings apply again. Page Read does not support Latched Controlled Read.

See [Figure 11: Asynchronous Page Read AC waveforms](#), and [Table 20: Asynchronous Page Read AC characteristics](#), for details on when the outputs become valid.

### 3.1.4 Asynchronous Bus Write

Asynchronous Bus Write operations write to the command interface in order to send commands to the memory or to latch addresses and input data to program. Bus Write operations are asynchronous, the clock, K, is Don't care during Bus Write operations.

A valid Asynchronous Bus Write operation begins by setting the desired address on the Address inputs, and setting Chip Enable, Write Enable and Latch Enable Low,  $V_{IL}$ , and Output Enable High,  $V_{IH}$ , or Output Disable Low,  $V_{IL}$ . The Address inputs are latched by the command interface on the rising edge of Chip Enable or Write Enable, whichever occurs first. Commands and input data are latched on the rising edge of Chip Enable,  $\bar{E}$ , or Write Enable,  $\bar{W}$ , whichever occurs first. Output Enable must remain High, and Output Disable Low, during the whole Asynchronous Bus Write operation.

See [Figure 12: Asynchronous Write AC waveforms](#), and [Table 21: Asynchronous Write and Latch controlled Write AC characteristics](#), for details of the timing requirements.

### 3.1.5 Asynchronous Latch Controlled Bus Write

Asynchronous Latch Controlled Bus Write operations write to the command interface in order to send commands to the memory or to latch addresses and input data to program. Bus Write operations are asynchronous, the clock, K, is Don't care during Bus Write operations.

A valid Asynchronous Latch Controlled Bus Write operation begins by setting the desired address on the Address inputs and pulsing Latch Enable Low,  $V_{IL}$ . The Address inputs are latched by the command interface on the rising edge of Latch Enable, Write Enable or Chip Enable, whichever occurs first. Commands and input data are latched on the rising edge of Chip Enable,  $\bar{E}$ , or Write Enable,  $\bar{W}$ , whichever occurs first. Output Enable must remain High, and Output Disable Low, during the whole Asynchronous Bus Write operation.

See [Figure 13: Asynchronous Latch controlled Write AC waveforms](#), and [Table 21: Asynchronous Write and Latch controlled Write AC characteristics](#), for details of the timing requirements.

### 3.1.6 Output Disable

The data outputs are high impedance when the Output Enable,  $\bar{G}$ , is at  $V_{IH}$  or Output Disable,  $\bar{GD}$ , is at  $V_{IL}$ .

### 3.1.7 Standby

When Chip Enable is High,  $V_{IH}$ , and the Program/Erase controller is idle, the memory enters Standby mode, the power consumption is reduced to the standby level ( $I_{DD1}$ ) and the Data inputs/outputs pins are placed in the high impedance state regardless of Output Enable, Write Enable or Output Disable inputs.

The Standby mode can be disabled by setting the Standby Disable bit (M14) of the Burst Configuration Register to '1' (see [Table 18: DC characteristics](#)).

### 3.1.8 Reset/Power-down

The memory is in Reset/Power-down mode when Reset/Power-down,  $\overline{RP}$ , is at  $V_{IL}$ . The power consumption is reduced to the standby level ( $I_{DD1}$ ) and the outputs are high impedance, independent of the Chip Enable,  $\overline{E}$ , Output Enable,  $\overline{G}$ , Output Disable,  $\overline{GD}$ , or Write Enable,  $\overline{W}$ , inputs. In this mode the device is write protected and both the Status and the Burst Configuration Registers are cleared. A recovery time is required when the  $\overline{RP}$  input goes High.

**Table 6. Asynchronous Bus operations<sup>(1)</sup>**

| Bus operation                           | Step          | $\overline{E}$ | $\overline{G}$ | $\overline{GD}$ | $\overline{W}$ | $\overline{RP}$ | $\overline{L}$ | A0-Amax | DQ0-DQ31    |
|-----------------------------------------|---------------|----------------|----------------|-----------------|----------------|-----------------|----------------|---------|-------------|
| Asynchronous Bus Read <sup>(2)</sup>    |               | $V_{IL}$       | $V_{IL}$       | $V_{IH}$        | $V_{IH}$       | $V_{IH}$        | $V_{IL}$       | Address | Data output |
| Asynchronous Latch Controlled Bus Read  | Address Latch | $V_{IL}$       | $V_{IH}$       | $V_{IH}$        | $V_{IL}$       | $V_{IH}$        | $V_{IL}$       | Address | High Z      |
|                                         | Read          | $V_{IL}$       | $V_{IL}$       | $V_{IH}$        | $V_{IH}$       | $V_{IH}$        | $V_{IH}$       | X       | Data output |
| Asynchronous Page Read                  |               | $V_{IL}$       | $V_{IL}$       | $V_{IH}$        | $V_{IH}$       | $V_{IH}$        | X              | Address | Data output |
| Asynchronous Bus Write                  |               | $V_{IL}$       | $V_{IH}$       | X               | $V_{IL}$       | $V_{IH}$        | $V_{IL}$       | Address | Data input  |
| Asynchronous Latch Controlled Bus Write | Address Latch | $V_{IL}$       | $V_{IH}$       | X               | $V_{IH}$       | $V_{IH}$        | $V_{IL}$       | Address | High Z      |
|                                         | Write         | $V_{IL}$       | $V_{IH}$       | X               | $V_{IL}$       | $V_{IH}$        | $V_{IH}$       | X       | Data input  |
| Output Enable, $\overline{G}$           |               | $V_{IL}$       | $V_{IH}$       | $V_{IH}$        | $V_{IH}$       | $V_{IH}$        | X              | X       | High Z      |
| Output Disable, $\overline{GD}$         |               | $V_{IL}$       | $V_{IL}$       | $V_{IL}$        | $V_{IH}$       | $V_{IH}$        | X              | X       | High Z      |
| Standby                                 |               | $V_{IH}$       | X              | X               | X              | $V_{IH}$        | X              | X       | High Z      |
| Reset/Power-down                        |               | X              | X              | X               | X              | $V_{IL}$        | X              | X       | High Z      |

1. X = Don't care.

2. Data, Manufacturer code, Device code, Burst Configuration Register, Standby Status and Block Protection Configuration Register are read using the Asynchronous Bus Read command.

## 3.2 Synchronous Bus operations

For Synchronous Bus Operations refer to [Table 7](#) together with the following text. The read access will start at whichever of the three following events occurs last: valid address transition, Chip Enable,  $\bar{E}$ , going Low,  $V_{IL}$  or Latch Enable,  $\bar{L}$ , going Low,  $V_{IL}$ .

### 3.2.1 Synchronous Burst Read

Synchronous Burst Read operations are used to read from the memory at specific times synchronized to an external reference clock. The valid edge of the Clock signal is the rising edge. Once the Flash memory is configured in Burst mode, it is mandatory to have an active clock signal since the switching of the output buffer databus is synchronized to the rising edge of the clock. In the absence of clock, no data is output.

The burst type, length and latency can be configured. The different configurations for Synchronous Burst Read operations are described in the Burst Configuration Register section. Refer to [Figure 4](#) for examples of Synchronous Burst operations.

A valid Synchronous Burst Read operation begins when the Burst Clock is active and Chip Enable and Latch Enable are Low,  $V_{IL}$ . The burst start address is latched and loaded into the internal Burst Address counter on the valid Burst Clock K edge or on the rising edge of Latch Enable, whichever occurs first.

After an initial memory latency time, the memory outputs data each clock cycle. The Burst Address Advance  $\bar{B}$  input controls the memory burst output. The second burst output is on the next clock valid edge after the Burst Address Advance  $\bar{B}$  has been pulled Low.

Valid Data Ready, R, monitors if the memory burst boundary is exceeded and the Burst Controller of the microprocessor needs to insert wait states. When Valid Data Ready is Low on the rising clock edge, no new data is available and the memory does not increment the internal address counter at the active clock edge even if Burst Address Advance,  $\bar{B}$ , is Low.

Valid Data Ready may be configured (by bit M8 of Burst Configuration Register) to be valid immediately at the rising clock edge.

Synchronous Burst Read will be suspended if Burst Address Advance,  $\bar{B}$ , goes High,  $V_{IH}$ .

If Output Enable is at  $V_{IL}$  and Output Disable is at  $V_{IH}$ , the last data is still valid.

If Output Enable,  $\bar{G}$ , is at  $V_{IH}$  or Output Disable,  $\bar{GD}$ , is at  $V_{IL}$ , but the Burst Address Advance,  $\bar{B}$ , is at  $V_{IL}$  the internal Burst Address counter is incremented at each Burst Clock K rising edge.

The Synchronous Burst Read timing diagrams and AC characteristics are described in the AC and DC parameters section. See [Figures 14, 17, 18 and 19](#), and [Table 22](#).

### 3.2.2 Synchronous Burst Read Suspend

During a Synchronous Burst Read operation it is possible to suspend the operation, freeing the data bus for other higher priority devices.

A valid Synchronous Burst Read operation is suspended when both Output Enable and Burst Address Advance are High,  $V_{IH}$ . The Burst Address Advance going High,  $V_{IH}$ , stops the Burst counter and the Output Enable going High,  $V_{IH}$ , inhibits the data outputs. The Synchronous Burst Read operation can be resumed by setting Output Enable Low.

**Table 7. Synchronous Burst Read Bus operations<sup>(1)</sup>**

| Bus operation                            | Step                   | $\bar{E}$ | $\bar{G}$ | $\bar{GD}$ | $\bar{RP}$ | K         | $\bar{L}$ | $\bar{B}$ | A0-Amax<br>DQ0-DQ31 |
|------------------------------------------|------------------------|-----------|-----------|------------|------------|-----------|-----------|-----------|---------------------|
| Synchronous<br>Burst Read <sup>(2)</sup> | Address Latch          | $V_{IL}$  | $V_{IH}$  | X          | $V_{IH}$   | $R^{(3)}$ | $V_{IL}$  | X         | Address input       |
|                                          | Read                   | $V_{IL}$  | $V_{IL}$  | $V_{IH}$   | $V_{IH}$   | $R^{(3)}$ | $V_{IH}$  | $V_{IL}$  | Data output         |
|                                          | Read Suspend           | $V_{IL}$  | $V_{IH}$  | X          | $V_{IH}$   | X         | $V_{IH}$  | $V_{IH}$  | High Z              |
|                                          | Read Resume            | $V_{IL}$  | $V_{IL}$  | $V_{IH}$   | $V_{IH}$   | $R^{(3)}$ | $V_{IH}$  | $V_{IL}$  | Data output         |
|                                          | Burst Address Advance  | $V_{IL}$  | $V_{IH}$  | X          | $V_{IH}$   | $R^{(3)}$ | $V_{IH}$  | $V_{IL}$  | High Z              |
|                                          | Read Abort, $\bar{E}$  | $V_{IH}$  | X         | X          | $V_{IH}$   | X         | X         | X         | High Z              |
|                                          | Read Abort, $\bar{RP}$ | X         | X         | X          | $V_{IL}$   | X         | X         | X         | High Z              |

1. X = Don't care,  $V_{IL}$  or  $V_{IH}$ .
2. M15 = 0, Bit M15 is in the Burst Configuration Register.
3. R = Rising edge.

## 3.3 Burst Configuration Register

The Burst Configuration Register is used to configure the type of bus access that the memory will perform.

The Burst Configuration Register is set through the command interface and will retain its information until it is re-configured, the device is reset, or the device goes into Reset/Power-down mode. The Burst Configuration Register bits are described in [Table 8](#). They specify the selection of the Burst length, Burst type, Burst X and Y latencies and the Read operation. Refer to [Figure 4](#) for examples of Synchronous Burst configurations.

### 3.3.1 Read Select bit (M15)

The Read Select bit, M15, is used to switch between Asynchronous and Synchronous Bus Read operations. When the Read Select bit is set to '1', Bus Read operations are asynchronous; when the Read Select bit is set to '0', Bus Read operations are synchronous.

On reset or power-up the Read Select bit is set to '1' for asynchronous accesses.

### 3.3.2 Standby Disable bit (M14)

The Standby Disable bit, M14, is used to disable the Standby mode. When the Standby bit is '1', the device will not enter Standby mode when Chip Enable goes High,  $V_{IH}$ .

### 3.3.3 X-Latency bits (M13-M11)

The X-Latency bits are used during Synchronous Bus Read operations to set the number of clock edges between the address being latched and the edge where the first data become available. For correct operation the X-Latency bits can only assume the values in [Table 8: Burst Configuration Register](#).

### 3.3.4 Y-Latency bit (M9)

The Y-Latency bit is used during Synchronous Bus Read operations to set the number of clock cycles between consecutive reads. The Y-Latency value depends on both the X-Latency value and the setting in M9.

When the Y-Latency is 1 the data changes each clock cycle.

### 3.3.5 Valid Data Ready bit (M8)

The Valid Data Ready bit controls the timing of the Valid Data Ready output pin, R. When the Valid Data Ready bit is '0' the Valid Data Ready output pin is driven Low for the rising clock edge when invalid data is output on the bus.

### 3.3.6 Wrap Burst bit (M3)

Burst Read can be confined inside the 4 double-word boundary (wrap) or overcome the boundary (no wrap). When the wrap burst bit is set to '1' the burst read does not wrap. The wrap mode is not available (M3 is always '1').

### 3.3.7 Burst Length bit (M2-M0)

The Burst Length bits set the maximum number of double-words that can be output during a Synchronous Burst Read operation. Burst lengths of 4 or 8 are available.

[Table 8: Burst Configuration Register](#) gives the valid combinations of the Burst Length bits that the memory accepts.

If a Burst Read operation (no wrap) has been initiated the device will output data synchronously. Depending on the starting address, the device activates the Valid Data Ready output to indicate that a delay is necessary before the data is output. If the starting address is aligned to a 4 double word boundary, the 8-double-word burst mode will run without activating the Valid Data Ready output. If the starting address is not aligned to a 4 double word boundary, Valid Data Ready is activated to indicate that the device needs an internal delay to read the successive words in the array.

**M10, M7 to M4** are reserved for future use.

**Table 8. Burst Configuration Register**

| Bit               | Description              | Value | Description                                               |
|-------------------|--------------------------|-------|-----------------------------------------------------------|
| M15               | Read Select              | 0     | Synchronous Burst Read                                    |
|                   |                          | 1     | Asynchronous Read (default at power-on)                   |
| M14               | Standby Disable          | 0     | Standby mode enabled (default at power-up)                |
|                   |                          | 1     | Standby mode disabled                                     |
| M13-M11           | X-Latency <sup>(1)</sup> | 000   | Reserved (default value)                                  |
|                   |                          | 001   | 3, 3-1-1-1, 3-2-2-2                                       |
|                   |                          | 010   | 4, 4-1-1-1, 4-2-2-2                                       |
|                   |                          | 011   | 5, 5-1-1-1, 5-2-2-2                                       |
|                   |                          | 100   | 6, 6-1-1-1, 6-2-2-2                                       |
|                   |                          | 101   | 7, 7-1-1-1, 7-2-2-2                                       |
|                   |                          | 110   | 8, 8-1-1-1, 8-2-2-2                                       |
|                   |                          | 111   | Reserved                                                  |
| M10               |                          | 0     | Reserved (default value)                                  |
|                   |                          | 1     | Reserved                                                  |
| M9                | Y-Latency <sup>(2)</sup> | 0     | One Burst Clock cycle (default value)                     |
|                   |                          | 1     | Two Burst Clock cycle                                     |
| M8                | Valid Data Ready         | 0     | R valid Low during valid Burst Clock edge (default value) |
|                   |                          | 1     | R valid Low 1 data cycle before valid Burst Clock edge    |
| M7                |                          | 0     | Reserved (default value)                                  |
|                   |                          | 1     | Reserved                                                  |
| M6 <sup>(3)</sup> |                          | 0     | Falling Burst Clock edge (default value)                  |
|                   |                          | 1     | Rising Burst Clock edge                                   |
| M5-M4             |                          | 00    | Reserved (default value)                                  |
|                   |                          | 01    | Reserved                                                  |
|                   |                          | 10    | Reserved                                                  |
|                   |                          | 11    | Reserved                                                  |
| M3                | Wrapping                 | 0     | Wrap (default value)                                      |
|                   |                          | 1     | No Wrap                                                   |

**Table 8. Burst Configuration Register (continued)**

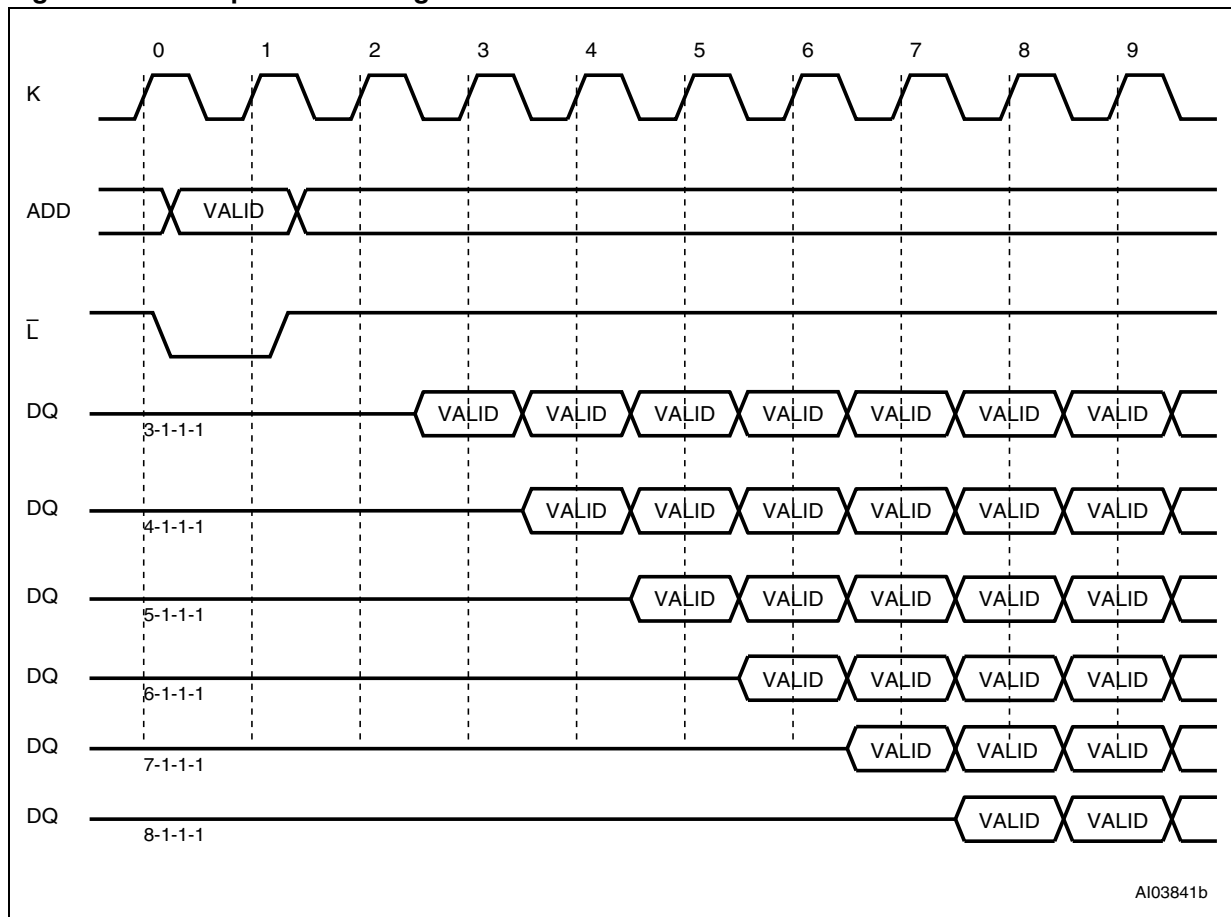
| Bit   | Description  | Value | Description              |
|-------|--------------|-------|--------------------------|
| M2-M0 | Burst Length | 000   | Reserved (default value) |
|       |              | 001   | 4 double-words           |
|       |              | 010   | 8 double-words           |
|       |              | 011   | Reserved                 |
|       |              | 100   | Reserved                 |
|       |              | 101   | Reserved                 |
|       |              | 110   | Reserved                 |
|       |              | 111   | Continuous               |

1. X latencies can be calculated as:  $(t_{AVQV} - t_{LLKH} + t_{QVKH}) + t_{SYSTEM\ MARGIN} < (X - 1) t_K$ . X is an integer number from 4 to 8,  $t_K$  is the clock period and  $t_{SYSTEM\ MARGIN}$  is the time margin required for the calculation.
2. Y latencies can be calculated as:  $t_{KHQV} + t_{SYSTEM\ MARGIN} + t_{QVKH} < Y t_K$ .
3. The M6 bit is Don't care in the M58BW32F and the device has the Rising Burst Clock edge set. To maintain the compatibility this could be modified and read.

Table 9. Burst type definition

| Start address | × 4 sequential | × 8 sequential        |
|---------------|----------------|-----------------------|
| 0             | 0-1-2-3        | 0-1-2-3-4-5-6-7       |
| 1             | 1-2-3-4        | 1-2-3-4-5-6-7-8       |
| 2             | 2-3-4-5        | 2-3-4-5-6-7-8-9       |
| 3             | 3-4-5-6        | 3-4-5-6-7-8-9-10      |
| 4             | 4-5-6-7        | 4-5-6-7-8-9-10-11     |
| 5             | 5-6-7-8        | 5-6-7-8-9-10-11-12    |
| 6             | 6-7-8-9        | 6-7-8-9-10-11-12-13   |
| 7             | 7-8-9-10       | 7-8-9-10-11-12-13-14  |
| 8             | 8-9-10-11      | 8-9-10-11-12-13-14-15 |

Figure 4. Example burst configuration X-1-1-1





## 4 Command interface

All Bus Write operations to the memory are interpreted by the command interface. Commands consist of one or more sequential Bus Write operations. The commands are summarized in [Table 10: Commands](#). Refer to [Table 10](#) in conjunction with the text descriptions below.

### 4.1 Read Memory Array command

The Read Memory Array command returns the memory to Read mode. One Bus Write cycle is required to issue the Read Memory Array command and return the memory to Read mode. Subsequent Read operations will output the addressed memory array data. Once the command is issued the memory remains in Read mode until another command is issued. From Read mode Bus Read commands will access the memory array.

### 4.2 Read Electronic Signature command

The Read Electronic Signature command is used to read the Manufacturer code, the Device code, the Block Protection Configuration Register and the Burst Configuration Register. One Bus Write cycle is required to issue the Read Electronic Signature command. Once the command is issued, subsequent Bus Read operations, depending on the address specified, read the Manufacturer code, the Device code, the Block Protection Configuration or the Burst Configuration Register until another command is issued; see [Table 11: Read electronic signature](#).

### 4.3 Read Query command

The Read Query command is used to read data from the common Flash interface (CFI) memory area. One Bus Write cycle is required to issue the Read Query command. Once the command is issued subsequent Bus Read operations, depending on the address specified, read from the common Flash interface memory area.

## 4.4 Read Status Register command

The Read Status Register command is used to read the Status Register. One Bus Write cycle is required to issue the Read Status Register command. Once the command is issued subsequent Bus Read operations read the Status Register until another command is issued.

The Status Register information is present on the output data bus (DQ0-DQ7) when Chip Enable  $\bar{E}$  and Output Enable  $\bar{G}$  are at  $V_{IL}$  and Output Disable is at  $V_{IH}$ .

An interactive update of the Status Register bits is possible by toggling Output Enable or Output Disable. It is also possible during a Program or Erase operation, by de-activating the device with Chip Enable at  $V_{IH}$  and then reactivating it with Chip Enable and Output Enable at  $V_{IL}$  and Output Disable at  $V_{IH}$ .

The content of the Status Register may also be read at the completion of a Program, Erase or Suspend operation. During a Block Erase or Program command, DQ7 indicates the Program/Erase controller status. It is valid until the operation is completed or suspended.

See the section on the Status Register and [Table 13](#) for details on the definitions of the Status Register bits.

## 4.5 Clear Status Register command

The Clear Status Register command can be used to reset bits 1, 3, 4 and 5 in the Status Register to '0'. One Bus Write is required to issue the Clear Status Register command. Once the command is issued the memory returns to its previous mode, subsequent Bus Read operations continue to output the same data.

The bits in the Status Register are sticky and do not automatically return to '0' when a new Program, Erase, Block Protect or Block Unprotect command is issued. If any error occurs then it is essential to clear any error bits in the Status Register by issuing the Clear Status Register command before attempting a new Program, Erase or Resume command.

## 4.6 Block Erase command

The Block Erase command can be used to erase a block. It sets all of the bits in the block to '1'. All previous data in the block is lost. If the block is protected then the Erase operation will abort, the data in the block will not be changed and the Status Register will output the error.

Two Bus Write operations are required to issue the command; the first write cycle sets up the Block Erase command, the second write cycle confirms the Block Erase command and latches the block address in the Program/Erase controller and starts the Program/Erase controller. The sequence is aborted if the Confirm command is not given and the device will output the Status Register Data with bits 4 and 5 set to '1'.

Once the command is issued subsequent Bus Read operations read the Status Register. See the section on the Status Register for details on the definitions of the Status Register bits. During the Erase operation the memory will only accept the Read Status Register command and the Program/Erase Suspend command. All other commands will be ignored.

If PEN is at  $V_{IH}$ , the operation can be performed. If PEN goes below  $V_{IH}$ , the operation aborts, the PEN Status bit in the Status Register is set to '1' and the command must be re-issued.

Typical Erase times are given in [Table 12](#). See [Appendix A, Figure 28: Block Erase flowchart and pseudocode](#), for a suggested flowchart on using the Block Erase command.

## 4.7 Erase All Main Blocks command

The Erase All Main Blocks command is used to erase all 63 main blocks, without affecting the parameter blocks.

Issuing the Erase All Main Blocks command sets every bit in each main block to '1'. All data previously stored in the main blocks are lost.

Two Bus Write cycles are required to issue the Erase All Main Blocks command. The first cycle sets up the command, the second cycle confirms the command and starts the Program/Erase controller. If the Confirm command is not given the sequence is aborted, and Status Register bits 4 and 5 are set to '1'.

If the address given in the second cycle is located in a protected block, the Erase All Main Blocks operation aborts. The data remains unchanged in all blocks and the Status Register outputs the error.

Once the Erase All Main Blocks command has been issued, subsequent Bus Read operations output the Status Register. See the [Status Register](#) section for details.

During an Erase All Main Blocks operation, only the Read Status Register command is accepted by the memory; any other command are ignored. Erase All Main Blocks, once started, cannot be suspended.

If PEN is at  $V_{IH}$ , the operation will be performed. If PEN is lower than  $V_{IH}$  the operation aborts and the Status Register PEN bit (bit 3) is set to '1'.

## 4.8 Program command

The Program command is used to program the memory array. Two Bus Write operations are required to issue the command; the first write cycle sets up the Program command, the second write cycle latches the address and data to be programmed and starts the Program/Erase controller. A program operation can be aborted by writing FFFFFFFFh to any address after the program set-up command has been given.

The Program command is also used to program the OTP block. Refer to [Table 10: Commands](#), for details of the address.

Once the command is issued subsequent Bus Read operations read the Status Register. See the section on the Status Register for details on the definitions of the Status Register bits. During the Program operation the memory will only accept the Read Status Register command and the Program/Erase Suspend command. All other commands will be ignored.

If Reset/Power-down,  $\overline{RP}$ , falls to  $V_{IL}$  during programming the operation will be aborted.

If PEN is at  $V_{IH}$ , the operation can be performed. If PEN goes below  $V_{IH}$ , the operation aborts, the PEN Status bit in the Status Register is set to '1' and the command must be re-issued.

See [Appendix A, Figure 26: Program flowchart and pseudocode](#), for a suggested flowchart on using the Program command.

## 4.9 Write to Buffer and Program command

The Write to Buffer and Program command makes use of the device's double word (32 bit) Write Buffer to speed up programming.

Up to eight double words can be loaded into the Write Buffer and programmed into the memory.

Four successive steps are required to issue the command.

1. One Bus Write operation is required to set up the Write to Buffer and Program command. Any Bus Read operations will start to output the Status Register after the 1st cycle.
2. Use one Bus Write operation to write the selected memory block address (any address in the block where the values will be programmed can be used) along with the value N on the Data inputs/outputs, where N+1 is the number of words to be programmed. The maximum value of N+1 is 8 words.
3. Use N+1 Bus Write operations to load the address and data for each word into the write buffer. The address must be between Start address and Start address plus N, where Start address is the first word address.
4. Finally, use one Bus Write operation to issue the final cycle to confirm the command and start the Program operation.

If any address is outside the block boundaries or if the correct sequence is not followed, Status Register bits 4 and 5 are set to '1' and the operation will abort without affecting the data in the memory array. A protected block must be unprotected using the Blocks Unprotect command.

During a Write to Buffer and Program operation the memory will only accept the Read Status Register and the Program/Erase Suspend commands. All other commands are ignored. If PEN is at  $V_{IH}$ , the operation will be performed. If PEN is lower than  $V_{IH}$  the operation aborts and the Status Register PEN bit (bit 3) is set to '1'.

The Status Register should be cleared before re-issuing the command.

## 4.10 Program/Erase Suspend command

The Program/Erase Suspend command is used to pause a Program or Erase operation. The command will only be accepted during a Program or Erase operation. It can be issued at any time during a Program or Erase operation. The command is ignored if the device is already in suspend mode.

One Bus Write cycle is required to issue the Program/Erase Suspend command and pause the Program/Erase controller. Once the command is issued it is necessary to poll the Program/Erase Controller Status bit (bit 7) to find out when the Program/Erase controller has paused; no other commands will be accepted until the Program/Erase controller has paused. After the Program/Erase controller has paused, the memory will continue to output the Status Register until another command is issued.

During the polling period between issuing the Program/Erase Suspend command and the Program/Erase Controller pausing it is possible for the operation to complete. Once the Program/Erase Controller Status bit (bit 7) indicates that the Program/Erase controller is no longer active, the Program Suspend Status bit (bit 2) or the Erase Suspend Status bit (bit 6) can be used to determine if the operation has completed or is suspended. For timing on the delay between issuing the Program/Erase Suspend command and the Program/Erase controller pausing see [Table 12](#).

During Program/Erase Suspend the Read Memory Array, Read Status Register, Read Electronic Signature, Read Query and Program/Erase Resume commands will be accepted by the command interface. Additionally, if the suspended operation was Erase then the Program, the Write to Buffer and Program, the Set/Clear Block Protection Configuration Register and the Program Suspend commands will also be accepted. When a program operation is completed inside a Block Erase Suspend the Read Memory Array command must be issued to reset the device in Read mode, then the Erase Resume command can be issued to complete the whole sequence. Only the blocks not being erased may be read or programmed correctly.

Erase operations can be suspended in a systematic and periodical way, however, in order to ensure the effectiveness of erase operations and avoid infinite erase times, it is imperative to wait a minimum time between successive Erase Resume and Erase Suspend commands. This time, called the minimum effective erase time, is given in [Table 12 on page 40](#).

See [Appendix A, Figure 27: Program Suspend & Resume flowchart and pseudocode](#), and [Figure 29: Erase Suspend & Resume flowchart and pseudocode](#), for suggested flowcharts on using the Program/Erase Suspend command.

## 4.11 Program/Erase Resume command

The Program/Erase Resume command can be used to restart the Program/Erase controller after a Program/Erase Suspend operation has paused it. One Bus Write cycle is required to issue the Program/Erase Resume command.

See [Appendix A, Figure 27: Program Suspend & Resume flowchart and pseudocode](#), and [Figure 29: Erase Suspend & Resume flowchart and pseudocode](#), for suggested flowcharts on using the Program/Erase Suspend command.

## 4.12 Set Burst Configuration Register command

The Set Burst Configuration Register command is used to write a new value to the Burst Configuration Register which defines the burst length, type, X and Y latencies, Synchronous/Asynchronous Read mode.

Two Bus Write cycles are required to issue the Set Burst Configuration Register command. The first cycle writes the setup command. The second cycle writes the address where the new Burst Configuration Register content is to be written, and confirms the command. If the command is not confirmed, the sequence is aborted and the device outputs the Status Register with bits 4 and 5 set to '1'. Once the command is issued the memory returns to Read mode as if a Read Memory Array command had been issued.

The value for the Burst Configuration Register is always presented on A0-A15. M0 is on A0, M1 on A1, etc.; the other address bits are ignored.

## 4.13 Set Block Protection Configuration Register command

The Set Block Protection Configuration Register command is used to configure the Block Protection Configuration Register to 'protected', for a specific block. Protected blocks are fully protected from program or erase when  $\overline{WP}$  pin is Low,  $V_{IL}$ . The status of a protected block can be changed to 'unprotected' by using the Clear Block Protection Configuration Register command. At power-up, all block are configured as 'protected'.

Two bus operations are required to issue a Set Block Protection Configuration Register command:

- The first cycle writes the setup command
- The second write cycle specifies the address of the block to protect and confirms the command. If the command is not confirmed, the sequence is aborted and the device outputs the Status Register with bits 4 and 5 set to '1'.

To protect multiple blocks, the Set Block Protection Configuration Register command must be repeated for each block.

Any attempt to re-protect a block already protected does not change its status.

## 4.14 Clear Block Protection Configuration Register command

The Clear Block Protection Configuration Register command is used to configure the Block Protection Configuration Register to 'unprotected', for a specific block thus allowing program/erase operations to this block, regardless of the  $\overline{WP}$  pin status.

Two bus operations are required to issue a Clear Block Protection Configuration Register command:

- The first cycle writes the setup command
- The second write cycle specifies the address of the block to unprotect and confirms the command. If the command is not confirmed, the sequence is aborted and the device outputs the Status Register with bits 4 and 5 set to '1'.

To unprotect multiple blocks, the Clear Block Protection Configuration Register command must be repeated for each block.

Any attempt to unprotect a block already unprotected does not affect its status.

Table 10. Commands<sup>(1)</sup>

| Command                                       |           | Cycles | Bus operations |       |            |           |       |      |           |       |      |           |       |      |
|-----------------------------------------------|-----------|--------|----------------|-------|------------|-----------|-------|------|-----------|-------|------|-----------|-------|------|
|                                               |           |        | 1st cycle      |       |            | 2nd cycle |       |      | 3rd cycle |       |      | 4th cycle |       |      |
|                                               |           |        | Op.            | Addr. | Data       | Op.       | Addr. | Data | Op.       | Addr. | Data | Op.       | Addr. | Data |
| Read Memory Array                             |           | ≥ 2    | Write          | X     | FFh        | Read      | RA    | RD   |           |       |      |           |       |      |
| Read Electronic Signature <sup>(2)</sup>      |           | ≥ 2    | Write          | X     | 90h        | Read      | IDA   | IDD  |           |       |      |           |       |      |
| Read Status Register                          |           | 1      | Write          | X     | 70h        |           |       |      |           |       |      |           |       |      |
| Read Query                                    |           | ≥ 2    | Write          | X     | 98h        | Read      | RA    | RD   |           |       |      |           |       |      |
| Clear Status Register                         |           | 1      | Write          | X     | 50h        |           |       |      |           |       |      |           |       |      |
| Block Erase                                   |           | 2      | Write          | 55h   | 20h        | Write     | BA    | D0h  |           |       |      |           |       |      |
| Erase All Main Blocks                         |           | 2      | Write          | 55h   | 80h        | Write     | AAh   | D0h  |           |       |      |           |       |      |
| Program                                       | any block | 2      | Write          | AAh   | 40h<br>10h | Write     | PA    | PD   |           |       |      |           |       |      |
|                                               | OTP block | 2      | Write          | AAh   | 40h        | Write     | PA    | PD   |           |       |      |           |       |      |
| Write to Buffer and Program                   |           | N+4    | Write          | AAh   | E8h        | Write     | BA    | N    | Write     | PA    | PD   | Write     | X     | D0h  |
| Program/Erase Suspend                         |           | 1      | Write          | X     | B0h        |           |       |      |           |       |      |           |       |      |
| Program/Erase Resume                          |           | 1      | Write          | X     | D0h        |           |       |      |           |       |      |           |       |      |
| Set Burst Configuration Register              |           | Š3     | Write          | X     | 60h        | Write     | BCRh  | 03h  | Read      | RA    | RD   |           |       |      |
| Set Block Protection Configuration Register   |           | 2      | Write          | X     | 60h        | Write     | BA    | 01h  |           |       |      |           |       |      |
| Clear Block Protection Configuration Register |           | 2      | Write          | X     | 60h        | Write     | BA    | D0h  |           |       |      |           |       |      |

1. X Don't care; RA Read Address, RD Read Data, ID Device Code, IDA Identifier Address, IDD Identifier Data, SRD Status Register Data, PA Program Address; PD Program Data, QA Query Address, QD Query Data, BA Any address in the Block, BCR Burst Configuration Register value, N+1 number of Words to program, BA Block address.
2. The Manufacturer code, the Device code, the Burst Configuration Register, and the Block Protection Configuration Register of each block are read using the Read Electronic Signature command.

**Table 11. Read electronic signature**

| Code                                    | Device    | Amax-A0                | DQ31-DQ0                |
|-----------------------------------------|-----------|------------------------|-------------------------|
| Manufacturer                            | All       | 00000h                 | 00000020h               |
| Device                                  | M58BW16FT | 00001h                 | 0000883Ah               |
|                                         | M58BW16FB | 00001h                 | 00008839h               |
|                                         | M58BW32FT | 00001h                 | 00008838h               |
|                                         | M58BW32FB | 00001h                 | 00008837h               |
| Burst Configuration Register            |           | 00005h                 | BCR <sup>(1)</sup>      |
| Block Protection Configuration Register | All       | SBA+02h <sup>(2)</sup> | 00000000h (Unprotected) |
|                                         |           |                        | 00000001h (Protected)   |

1. BCR = Burst Configuration Register.
2. SBA is the start address of each block.

**Table 12. Program, Erase times and endurance cycles<sup>(1)</sup>**

| Parameters                                  | M58BW16F |     |         | M58BW32F |     |         | Unit   |
|---------------------------------------------|----------|-----|---------|----------|-----|---------|--------|
|                                             | Min      | Typ | Max     | Min      | Typ | Max     |        |
| Full Chip Program                           |          | 15  | 20      |          | 15  | 20      | s      |
| Double Word Program                         |          | 15  | 35      |          | 15  | 35      | µs     |
| 512 Kbit Block Erase                        |          | 1   | 2       |          | 1   | 2       | s      |
| 128 Kbit Block Erase                        |          | 0.8 | 1.6     |          | 0.8 | 1.6     | s      |
| 64 Kbit Block Erase                         |          | 0.6 | 1.2     |          | 0.6 | 1.2     | s      |
| Erase all main blocks                       |          | 45  | 60      |          | 30  | 50      | s      |
| Program Suspend Latency time                |          |     | 10      |          |     | 10      | µs     |
| Erase Suspend Latency time                  |          |     | 30      |          |     | 30      | µs     |
| Minimum effective erase time <sup>(2)</sup> |          |     | 40      |          |     | 40      | µs     |
| Program/Erase cycles (per block)            |          |     | 100,000 |          |     | 100,000 | cycles |

1.  $T_A = -40$  to  $125$  °C,  $V_{DD} = 2.7$  V to  $3.6$  V,  $V_{DDQ} = 2.6$  V to  $V_{DD}$ .
2. The minimum effective erase time is defined as the minimum time required between the last Erase Resume command and the next Erase Suspend command for the internal Flash memory Program/Erase controller to be able to execute its algorithm.



## 5 Status Register

The Status Register provides information on the current or previous Program, Erase or Block Protect operation. The various bits in the Status Register convey information and errors on the operation. They are output on DQ7-DQ0.

To read the Status Register the Read Status Register command can be issued. The Status Register is automatically read after Program, Erase, Block Protect, Program/Erase Resume commands. The Status Register can be read from any address.

The contents of the Status Register can be updated during an erase or program operation by toggling the Output Enable or Output Disable pins or by de-activating (Chip Enable,  $V_{IH}$ ) and then reactivating (Chip Enable and Output Enable,  $V_{IL}$ , and Output Disable,  $V_{IH}$ ) the device.

The Status Register bits are summarized in [Table 13: Status Register bits](#). Refer to [Table 13](#) in conjunction with the following text descriptions.

### 5.1 Program/Erase Controller Status (bit 7)

The Program/Erase Controller Status bit indicates whether the Program/Erase controller is active or inactive. When the Program/Erase Controller Status bit is set to '0', the Program/Erase controller is active; when bit 7 is set to '1', the Program/Erase controller is inactive.

The Program/Erase Controller Status is set to '0' immediately after a Program/Erase Suspend command is issued until the Program/Erase Controller pauses. After the Program/Erase Controller pauses the bit is set to '1'.

During Program and Erase operations the Program/Erase Controller Status bit can be polled to find the end of the operation. The other bits in the Status Register should not be tested until the Program/Erase controller completes the operation and the bit is set to '1'.

After the Program/Erase controller completes its operation the Erase Status (bit 5), Program Status (bit 4) bits should be tested for errors.

### 5.2 Erase Suspend Status (bit 6)

The Erase Suspend Status bit indicates that an Erase operation has been suspended and is waiting to be resumed. The Erase Suspend Status should only be considered valid when the Program/Erase Controller Status bit is set to '1' (Program/Erase controller inactive); after a Program/Erase Suspend command is issued the memory may still complete the operation rather than entering the Suspend mode.

When the Erase Suspend Status bit is set to '0', the Program/Erase controller is active or has completed its operation; when the bit is set to '1', a Program/Erase Suspend command has been issued and the memory is waiting for a Program/Erase Resume command.

When a Program/Erase Resume command is issued the Erase Suspend Status bit returns to '0'.

### 5.3 Erase Status (bit 5)

The Erase Status bit can be used to identify if the memory has failed to verify that the block has erased correctly. The Erase Status bit should be read once the Program/Erase Controller Status bit is High (Program/Erase controller inactive).

When the Erase Status bit is set to '0', the memory has successfully verified that the block has erased correctly. When the Erase Status bit is set to '1', the Program/Erase controller has applied the maximum number of pulses to the block and still failed to verify that the block has erased correctly.

Once set to '1', the Erase Status bit can only be reset to '0' by a Clear Status Register command or a hardware reset. If set to '1' it should be reset before a new Program or Erase command is issued, otherwise the new command will appear to fail.

### 5.4 Program/Write to Buffer and Program Status (bit 4)

The Program/Write to Buffer and Program Status bit is used to identify a Program failure or a Write to Buffer and Program failure. Bit 4 should be read once the Program/Erase Controller Status bit is High (Program/Erase controller inactive).

When bit 4 is set to '0' the memory has successfully verified that the device has programmed correctly. When bit 4 is set to '1' the device has failed to verify that the data has been programmed correctly.

Once set to '1', the Program Status bit can only be reset to '0' by a Clear Status Register command or a hardware reset. If set to '1' it should be reset before a new Program or Erase command is issued, otherwise the new command will appear to fail.

### 5.5 PEN Status (bit 3)

The PEN Status bit can be used to identify if a Program or Erase operation has been attempted when PEN is Low,  $V_{IL}$ .

When bit 3 is set to '0' no Program or Erase operations have been attempted with PEN Low,  $V_{IL}$ , since the last Clear Status Register command, or hardware reset.

When bit 3 is set to '1' a Program or Erase operation has been attempted with PEN Low,  $V_{IL}$ .

Once set to '1', bit 3 can only be reset by a Clear Status Register command or a hardware reset. If set to '1' it should be reset before a new Program or Erase command is issued, otherwise the new command will appear to fail.

## 5.6 Program Suspend Status (bit 2)

The Program Suspend Status bit indicates that a Program operation has been suspended and is waiting to be resumed. The Program Suspend Status should only be considered valid when the Program/Erase Controller Status bit is set to '1' (Program/Erase Controller inactive); after a Program/Erase Suspend command is issued the memory may still complete the operation rather than entering the Suspend mode.

When the Program Suspend Status bit is set to '0', the Program/Erase controller is active or has completed its operation; when the bit is set to '1', a Program/Erase Suspend command has been issued and the memory is waiting for a Program/Erase Resume command.

When a Program/Erase Resume command is issued the Program Suspend Status bit returns to '0'.

## 5.7 Block Protection Status (bit 1)

The Block Protection Status bit can be used to identify if a Program or Erase operation has tried to modify the contents of a protected block.

When the Block Protection Status bit is set to '0', no Program or Erase operations have been attempted to protected blocks since the last Clear Status Register command or hardware reset; when the Block Protection Status bit is set to '1', a Program or Erase operation has been attempted on a protected block.

Once set to '1', the Block Protection Status bit can only be reset Low by a Clear Status Register command or a hardware reset. If set to '1' it should be reset before a new Program or Erase command is issued, otherwise the new command will appear to fail.

## 5.8 Bit 0

Reserved bit (set to '1').

Table 13. Status Register bits

| Bit | Name                               | Logic level | Definition                              |
|-----|------------------------------------|-------------|-----------------------------------------|
| 7   | Program/Erase Controller Status    | '1'         | Ready                                   |
|     |                                    | '0'         | Busy                                    |
| 6   | Erase Suspend Status               | '1'         | Suspended                               |
|     |                                    | '0'         | In progress or completed                |
| 5   | Erase Status                       | '1'         | Erase error                             |
|     |                                    | '0'         | Erase success                           |
| 4   | Program Status,                    | '1'         | Program error                           |
|     |                                    | '0'         | Program success                         |
| 3   | PEN Status bit                     | '0'         | No program or erase attempted           |
|     |                                    | '1'         | Program or erase attempted              |
| 2   | Program Suspend Status             | '1'         | Suspended                               |
|     |                                    | '0'         | In progress or completed                |
| 1   | Erase/Program in a protected block | '1'         | Program/erase on protected block, abort |
|     |                                    | '0'         | No operations to protected blocks       |
| 0   | Reserved                           | '1'         | Reserved                                |

## 6 Maximum rating

Stressing the device above the ratings listed in [Table 14: Absolute maximum ratings](#), may cause permanent damage to the device. These are stress ratings only and operation of the device at these or any other conditions above those indicated in the operating sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability. Refer also to the Numonyx SURE Program and other relevant quality documents.

**Table 14. Absolute maximum ratings**

| Symbol                       | Parameter               | Value |                                      | Unit |
|------------------------------|-------------------------|-------|--------------------------------------|------|
|                              |                         | Min   | Max                                  |      |
| $T_{BIAS}$                   | Temperature under bias  | -40   | 125                                  | °C   |
| $T_{STG}$                    | Storage temperature     | -55   | 155                                  | °C   |
| $V_{IO}$                     | Input or output voltage | -0.6  | $V_{DDQ} + 0.6$<br>$V_{DDQIN} + 0.6$ | V    |
| $V_{DD}, V_{DDQ}, V_{DDQIN}$ | Supply voltage          | -0.6  | 4.2                                  | V    |

**Table 15. Data retention**

| Power supply<br>$V_{DD}$ | Unit | External temperature |        | Unit  |
|--------------------------|------|----------------------|--------|-------|
|                          |      | 25 °C                | 125 °C |       |
| 0                        | V    | 20                   | 7      | Years |
| 2.5                      | V    | –                    | 25     | Years |
| 2.7                      | V    | –                    | 15     | Years |

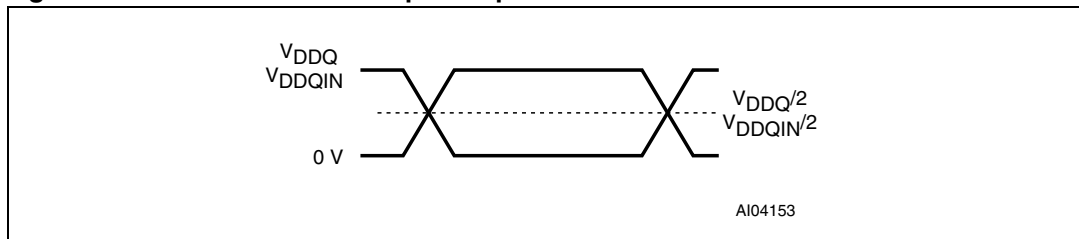
## 7 DC and AC parameters

This section summarizes the operating and measurement conditions, and the DC and AC characteristics of the device. The parameters in the DC and AC characteristics tables that follow, are derived from tests performed under the measurement conditions summarized in [Table 16: Operating and AC measurement conditions](#). Designers should check that the operating conditions in their circuit match the measurement conditions when relying on the quoted parameters.

**Table 16. Operating and AC measurement conditions**

| Parameter                                 |         | M58BW16F, M58BW32F |     |                |     | Units |
|-------------------------------------------|---------|--------------------|-----|----------------|-----|-------|
|                                           |         | 45 ns              |     | 55 ns          |     |       |
|                                           |         | Min                | Max | Min            | Max |       |
| Supply voltage ( $V_{DD}$ )               |         | 2.7                | 3.6 | 2.5            | 3.3 | V     |
| Input/output supply voltage ( $V_{DDQ}$ ) |         | 2.4                | 3.6 | 2.4            | 3.6 | V     |
| Ambient temperature ( $T_A$ )             | Grade 3 | -40                | 125 | -40            | 125 | °C    |
| Load capacitance ( $C_L$ )                |         | 30                 |     | 30             |     | pF    |
| Clock rise and fall times                 |         |                    | 3   |                | 3   | ns    |
| Input rise and fall times                 |         |                    | 3   |                | 3   | ns    |
| Input pulses voltages                     |         | 0 to $V_{DDQ}$     |     | 0 to $V_{DDQ}$ |     | V     |
| Input and output timing ref. voltages     |         | $V_{DDQ}/2$        |     | $V_{DDQ}/2$    |     | V     |

**Figure 5. AC measurement input/output waveform**



1.  $V_{DD} = V_{DDQ}$ .

**Figure 6. AC measurement load circuit**

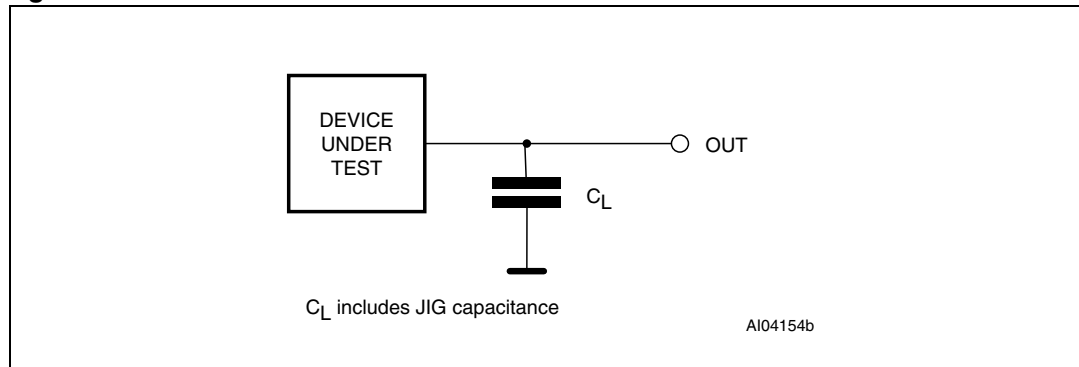


Table 17. Device capacitance<sup>(1)(2)</sup>

| Symbol    | Parameter          | Test condition         | Typ | Max | Unit |
|-----------|--------------------|------------------------|-----|-----|------|
| $C_{IN}$  | Input capacitance  | $V_{IN} = 0\text{ V}$  | 6   | 8   | pF   |
| $C_{OUT}$ | Output capacitance | $V_{OUT} = 0\text{ V}$ | 8   | 12  | pF   |

1.  $T_A = 25\text{ °C}$ ,  $f = 1\text{ MHz}$ .

2. Sampled only, not 100% tested.

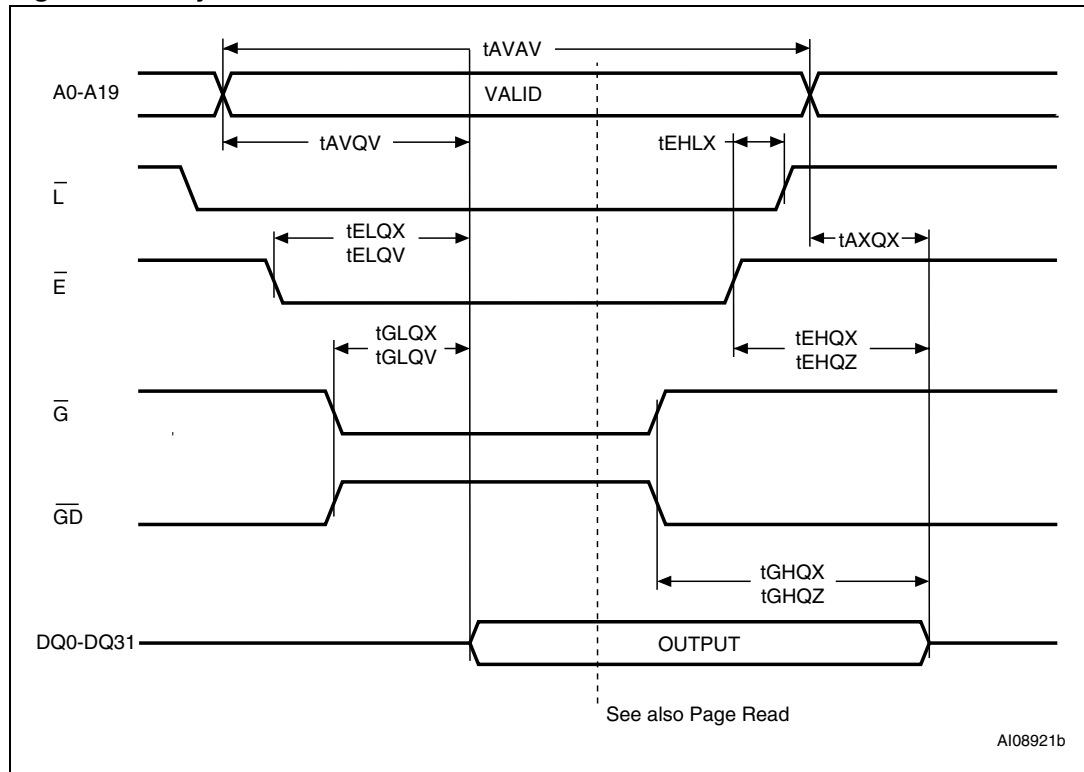
Table 18. DC characteristics

| Symbol             | Parameter                                           | Test condition                                                           | Min             | Typ | Max             | Unit          |
|--------------------|-----------------------------------------------------|--------------------------------------------------------------------------|-----------------|-----|-----------------|---------------|
| $I_{LI}$           | Input Leakage current                               | $0\text{ V} \leq V_{IN} \leq V_{DDQIN}$                                  |                 |     | $\pm 1$         | $\mu\text{A}$ |
| $I_{LO}$           | Output Leakage current                              | $0\text{ V} \leq V_{OUT} \leq V_{DDQ}$                                   |                 |     | $\pm 5$         | $\mu\text{A}$ |
| $I_{DD}$           | Supply current (Random Read)                        | $\bar{E} = V_{IL}$ , $\bar{G} = V_{IH}$ ,<br>$f_{add} = 6\text{ MHz}$    |                 |     | 25              | mA            |
| $I_{DDP-UP}^{(1)}$ | Supply current (power-up)                           |                                                                          |                 |     | 20              | mA            |
| $I_{DDB}$          | Supply current (Burst Read)                         | $\bar{E} = V_{IL}$ , $\bar{G} = V_{IH}$ ,<br>$f_{clock} = 75\text{ MHz}$ |                 |     | 50              | mA            |
| $I_{DD1}^{(2)}$    | Supply current (Standby)                            | $\bar{E} = \bar{RP} =$<br>$V_{DD} \pm 0.2\text{ V}$                      |                 |     | 150             | $\mu\text{A}$ |
| $I_{DD2}$          | Supply current (Program or Erase)                   | Program, Erase in progress                                               |                 |     | 30              | mA            |
| $I_{DD3}$          | Supply current (Erase/Program Suspend)              | $\bar{E} = V_{IH}$                                                       |                 |     | 150             | $\mu\text{A}$ |
| $I_{DD4}$          | Supply current (Standby Disable)                    |                                                                          |                 | 5   | 10              | mA            |
| $V_{IL}$           | Input Low voltage                                   |                                                                          | -0.5            |     | $0.2V_{DDQIN}$  | V             |
| $V_{IH}$           | Input High voltage (for DQ lines)                   |                                                                          | $0.8V_{DDQIN}$  |     | $V_{DDQ} + 0.3$ | V             |
| $V_{IH}$           | Input High voltage (for input only lines)           |                                                                          | $0.8V_{DDQIN}$  |     | 3.6             | V             |
| $V_{OL}$           | Output Low voltage                                  | $I_{OL} = 100\text{ }\mu\text{A}$                                        |                 |     | 0.1             | V             |
| $V_{OH}$           | Output High voltage CMOS                            | $I_{OH} = -100\text{ }\mu\text{A}$                                       | $V_{DDQ} - 0.1$ |     |                 | V             |
| $V_{LKO}$          | $V_{DD}$ supply voltage (Erase and Program lockout) |                                                                          |                 |     | 2.2             | V             |

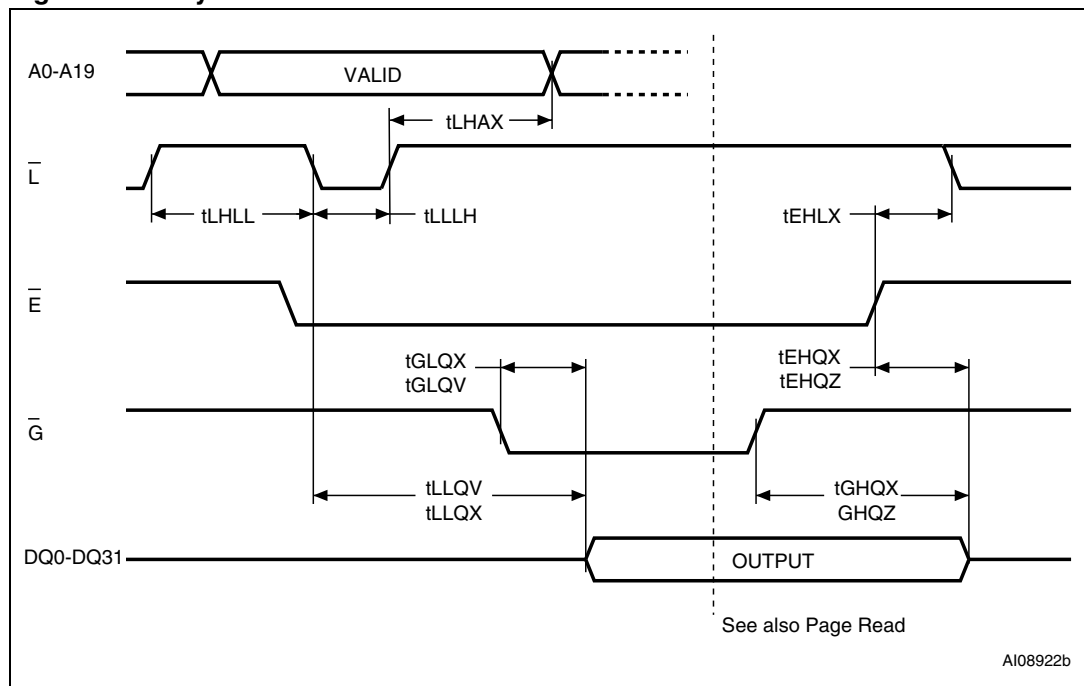
1.  $I_{DDP-UP}$  is the current needed from the device until  $\bar{RP}$  goes to its logic high level when the power supply is stable ( $t_{VDHPH}$ ). See [Figure 22](#) and [Figure 23](#).

2. The Standby mode can be disabled by setting the Standby Disable bit (M14) of the Burst Configuration Register to '1'.

**Figure 7. Asynchronous Bus Read AC waveforms**

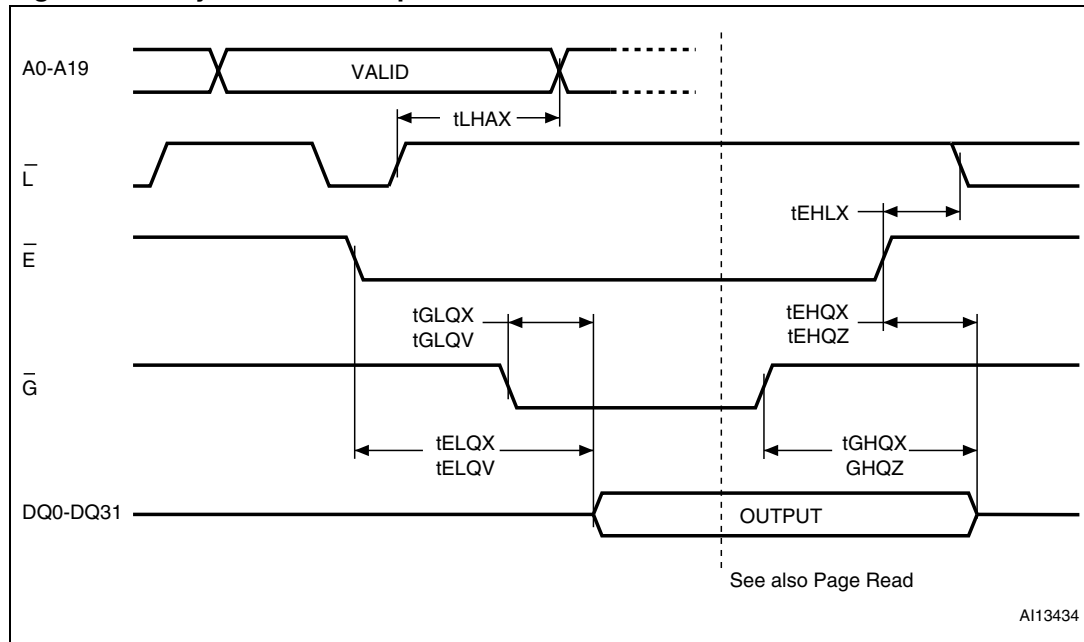


**Figure 8. Asynchronous Latch Controlled Bus Read AC waveforms**

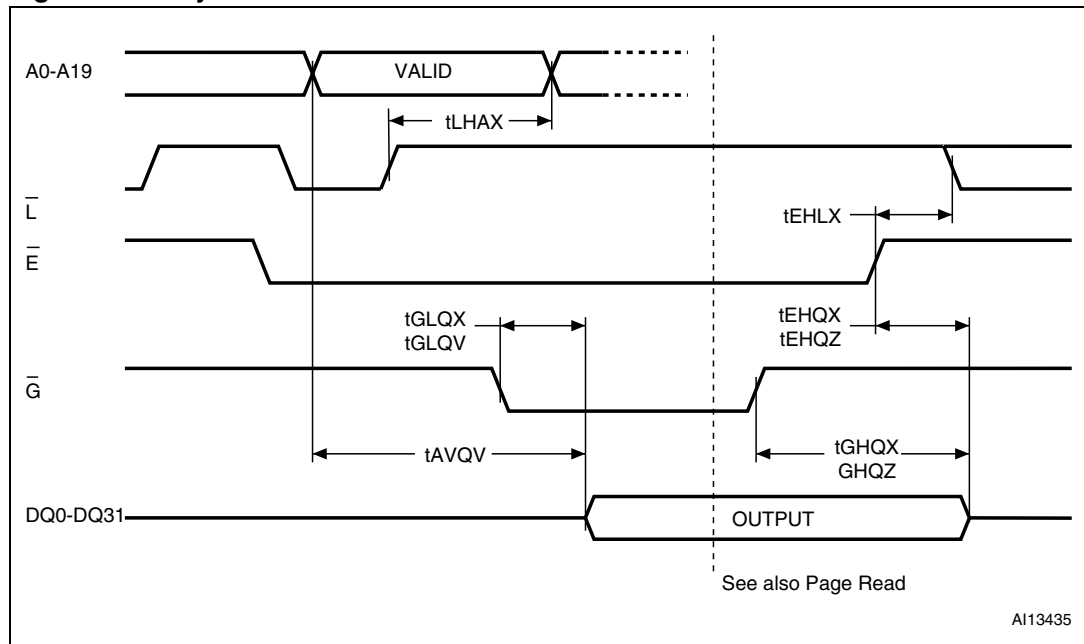




**Figure 9. Asynchronous Chip Enable Controlled Bus Read AC waveforms**



**Figure 10. Asynchronous Address Controlled Bus Read AC waveforms**



**Table 19. Asynchronous Bus Read AC characteristics**

| Symbol                           | Parameter                                                           | Test condition                       |     | M58BWxxF |    | Unit |
|----------------------------------|---------------------------------------------------------------------|--------------------------------------|-----|----------|----|------|
|                                  |                                                                     |                                      |     | 45       | 55 |      |
| t <sub>AVAV</sub>                | Address Valid to Address Valid                                      | $\bar{E} = V_{IL}, \bar{G} = V_{IL}$ | Min | 45       | 55 | ns   |
| t <sub>AVQV</sub>                | Address Valid to Output Valid                                       | $\bar{E} = V_{IL}, \bar{G} = V_{IL}$ | Max | 45       | 55 | ns   |
| t <sub>AXQX</sub>                | Address Transition to Output Transition                             | $\bar{L} = V_{IL}, \bar{G} = V_{IL}$ | Min | 0        | 0  | ns   |
| t <sub>EHLX</sub>                | Chip Enable High to Latch Enable Transition                         |                                      | Min | 0        | 0  | ns   |
| t <sub>EHQX</sub>                | Chip Enable High to Output Transition                               | $\bar{G} = V_{IL}$                   | Min | 0        | 0  | ns   |
| t <sub>EHQZ</sub>                | Chip Enable High to Output Hi-Z                                     | $\bar{G} = V_{IL}$                   | Max | 20       | 20 | ns   |
| t <sub>ELQV</sub> <sup>(1)</sup> | Chip Enable Low to Output Valid                                     | $\bar{G} = V_{IL}$                   | Max | 45       | 55 | ns   |
| t <sub>GHQX</sub>                | Output Enable High to Output Transition                             | $\bar{E} = V_{IL}$                   | Min | 0        | 0  | ns   |
| t <sub>GHQZ</sub>                | Output Enable High to Output Hi-Z                                   | $\bar{E} = V_{IL}$                   | Max | 15       | 15 | ns   |
| t <sub>GLQV</sub>                | Output Enable Low to Output Valid                                   | $\bar{E} = V_{IL}$                   | Max | 15       | 15 | ns   |
| t <sub>GLQX</sub>                | Output Enable Low to Output Transition                              | $\bar{E} = V_{IL}$                   | Min | 0        | 0  | ns   |
| t <sub>LHAX</sub>                | Latch Enable High to Address Transition                             | $\bar{E} = V_{IL}$                   | Min | 5        | 5  | ns   |
| t <sub>LHLL</sub>                | Latch Enable High to Latch Enable Low                               |                                      | Min | 10       | 10 | ns   |
| t <sub>LLLH</sub>                | Latch Enable Low to Latch Enable High                               | $\bar{E} = V_{IL}$                   | Min | 10       | 10 | ns   |
| t <sub>LLQV</sub>                | Latch Enable Low to Output Valid<br>Chip Enable Low to Output Valid | $\bar{E} = V_{IL}, \bar{G} = V_{IL}$ | Max | 45       | 55 | ns   |
| t <sub>LLQX</sub>                | Latch Enable Low to Output Transition                               | $\bar{E} = V_{IL}, \bar{G} = V_{IL}$ | Min | 0        | 0  | ns   |
| t <sub>ELQX</sub>                | Chip Enable Low to Output Transition                                | $\bar{L} = V_{IL}, \bar{G} = V_{IL}$ | Min | 0        | 0  | ns   |

1. Output Enable  $\bar{G}$  may be delayed up to t<sub>ELQV</sub> - t<sub>GLQV</sub> after the falling edge of Chip Enable  $\bar{E}$  without increasing t<sub>ELQV</sub>.

Figure 11. Asynchronous Page Read AC waveforms

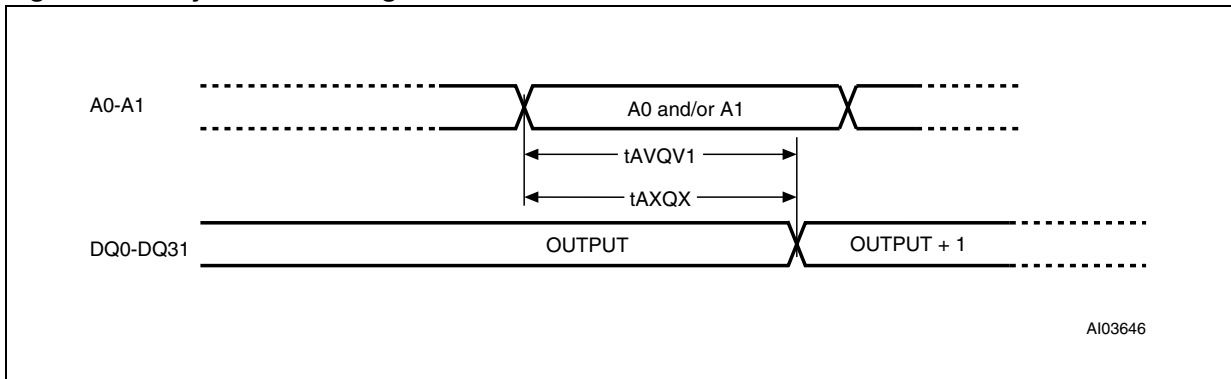
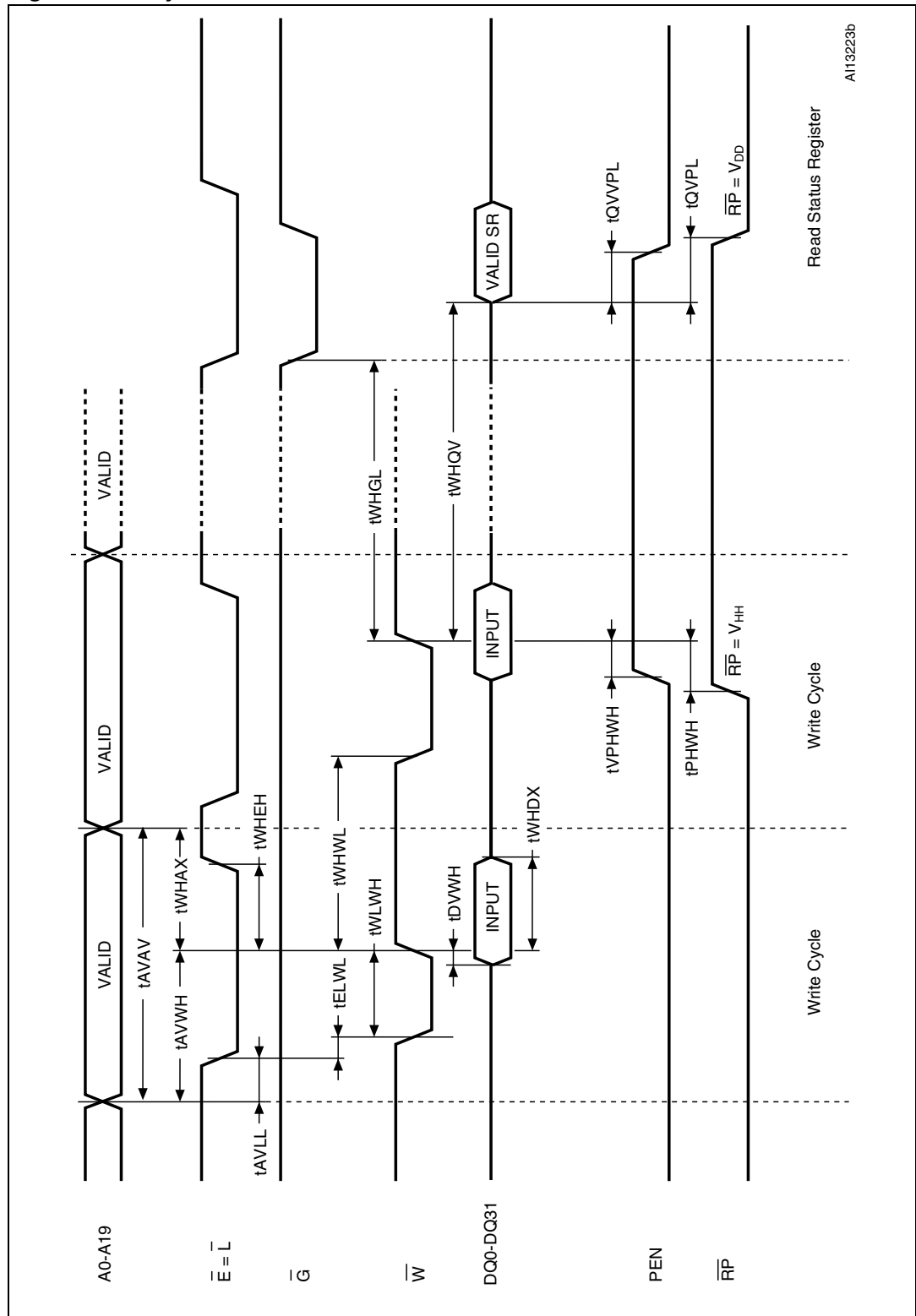


Table 20. Asynchronous Page Read AC characteristics<sup>(1)</sup>

| Symbol             | Parameter                               | Test condition                       | M58BWxxF |    | Unit |    |
|--------------------|-----------------------------------------|--------------------------------------|----------|----|------|----|
|                    |                                         |                                      | 45       | 55 |      |    |
| t <sub>AVQV1</sub> | Address Valid to Output Valid           | $\bar{E} = V_{IL}, \bar{G} = V_{IL}$ | Max      | 25 | 25   | ns |
| t <sub>AXQX</sub>  | Address Transition to Output Transition | $\bar{E} = V_{IL}, \bar{G} = V_{IL}$ | Min      | 0  | 0    | ns |

1. For other timings see [Table 19: Asynchronous Bus Read AC characteristics](#).

Figure 12. Asynchronous Write AC waveforms



A113233b



Table 21. Asynchronous Write and Latch controlled Write AC characteristics

| Symbol      | Parameter                               | Test condition     |     | M58BWxxF |     | Unit |
|-------------|-----------------------------------------|--------------------|-----|----------|-----|------|
|             |                                         |                    |     | 45       | 55  |      |
| $t_{AVAV}$  | Address Valid to Address Valid          |                    | Min | 45       | 55  | ns   |
| $t_{AVLH}$  | Address Valid to Latch Enable High      |                    | Min | 8        | 8   | ns   |
| $t_{AVLL}$  | Address Valid to Latch Enable Low       |                    | Min | 0        | 0   | ns   |
| $t_{AVWH}$  | Address Valid to Write Enable High      | $\bar{E} = V_{IL}$ | Min | 25       | 30  | ns   |
| $t_{DVWH}$  | Data Input Valid to Write Enable High   | $\bar{E} = V_{IL}$ | Min | 25       | 30  | ns   |
| $t_{ELLL}$  | Chip Enable Low to Latch Enable Low     |                    | Min | 0        | 0   | ns   |
| $t_{ELWL}$  | Chip Enable Low to Write Enable Low     |                    | Min | 0        | 0   | ns   |
| $t_{LHAX}$  | Latch Enable High to Address Transition |                    | Min | 5        | 5   | ns   |
| $t_{LLLH}$  | Latch Enable Low to Latch Enable High   |                    | Min | 10       | 10  | ns   |
| $t_{LLWH}$  | latch Enable Low to Write Enable High   | $\bar{E} = V_{IL}$ | Min | 25       | 30  | ns   |
| $t_{QVPL}$  | Output Valid to PEN Low                 |                    | Min | 0        | 0   | ns   |
| $t_{VPHWH}$ | PEN High to Write Enable High           |                    | Min | 0        | 0   | ns   |
| $t_{WHAX}$  | Write Enable High to Address Transition | $\bar{E} = V_{IL}$ | Min | 0        | 0   | ns   |
| $t_{WHDX}$  | Write Enable High to Input Transition   | $\bar{E} = V_{IL}$ | Min | 0        | 0   | ns   |
| $t_{WHEH}$  | Write Enable High to Chip Enable High   |                    | Min | 0        | 0   | ns   |
| $t_{WHGL}$  | Write Enable High to Output Enable Low  |                    | Min | 150      | 150 | ns   |
| $t_{WHQV}$  | Write Enable High to Output Valid       |                    | Min | 165      | 165 | ns   |
| $t_{WHWL}$  | Write Enable High to Write Enable Low   |                    | Min | 20       | 20  | ns   |
| $t_{WLWH}$  | Write Enable Low to Write Enable High   | $\bar{E} = V_{IL}$ | Min | 25       | 30  | ns   |
| $t_{QVPL}$  | Output Valid to Reset/Power-down Low    |                    | Min | 0        | 0   | ns   |

Figure 14. Synchronous Burst Read, Latch Enable controlled (data valid from 'n' clock rising edge)

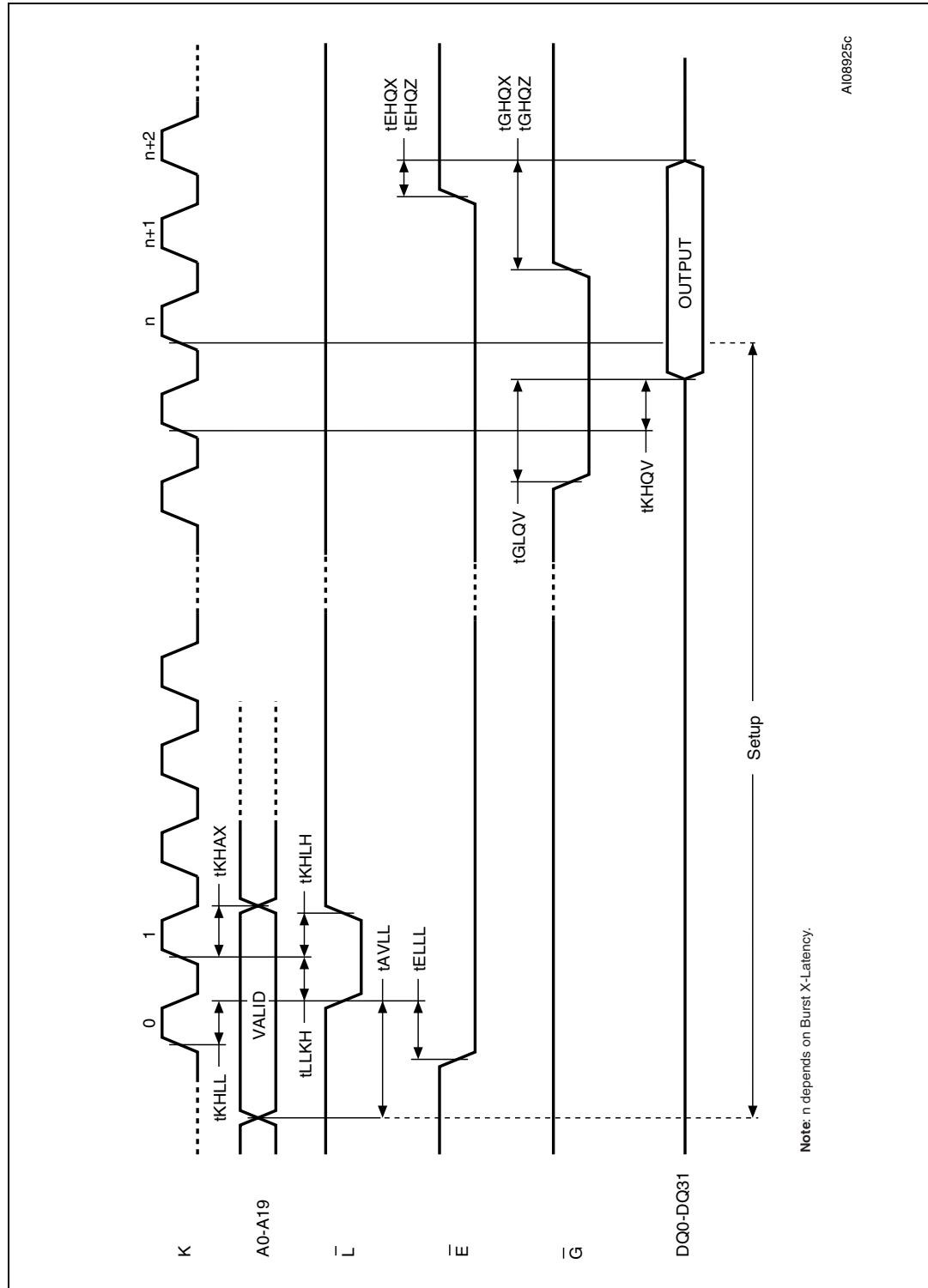


Figure 15. Synchronous Burst Read, Chip Enable controlled (data valid from 'n' clock rising edge)

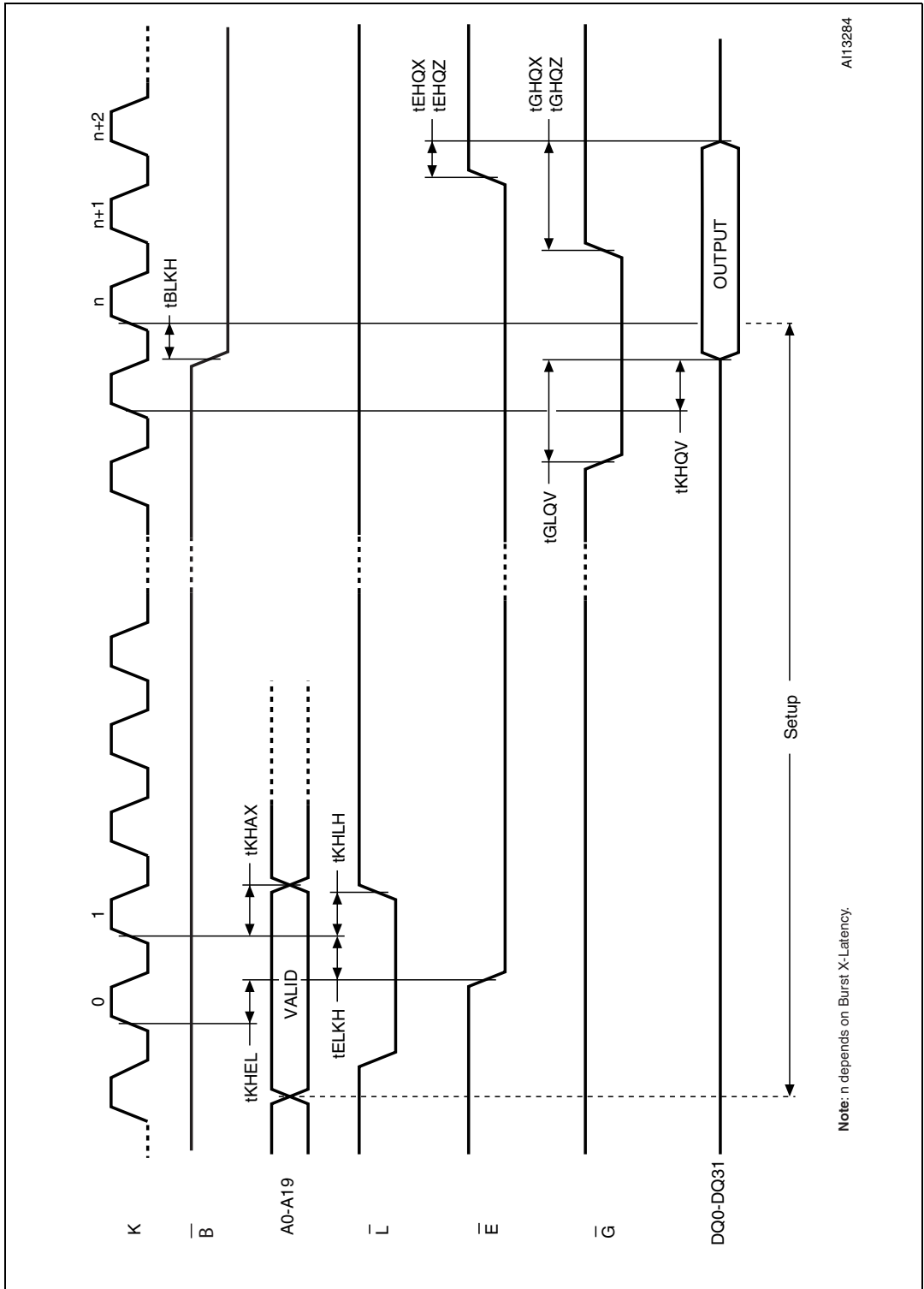
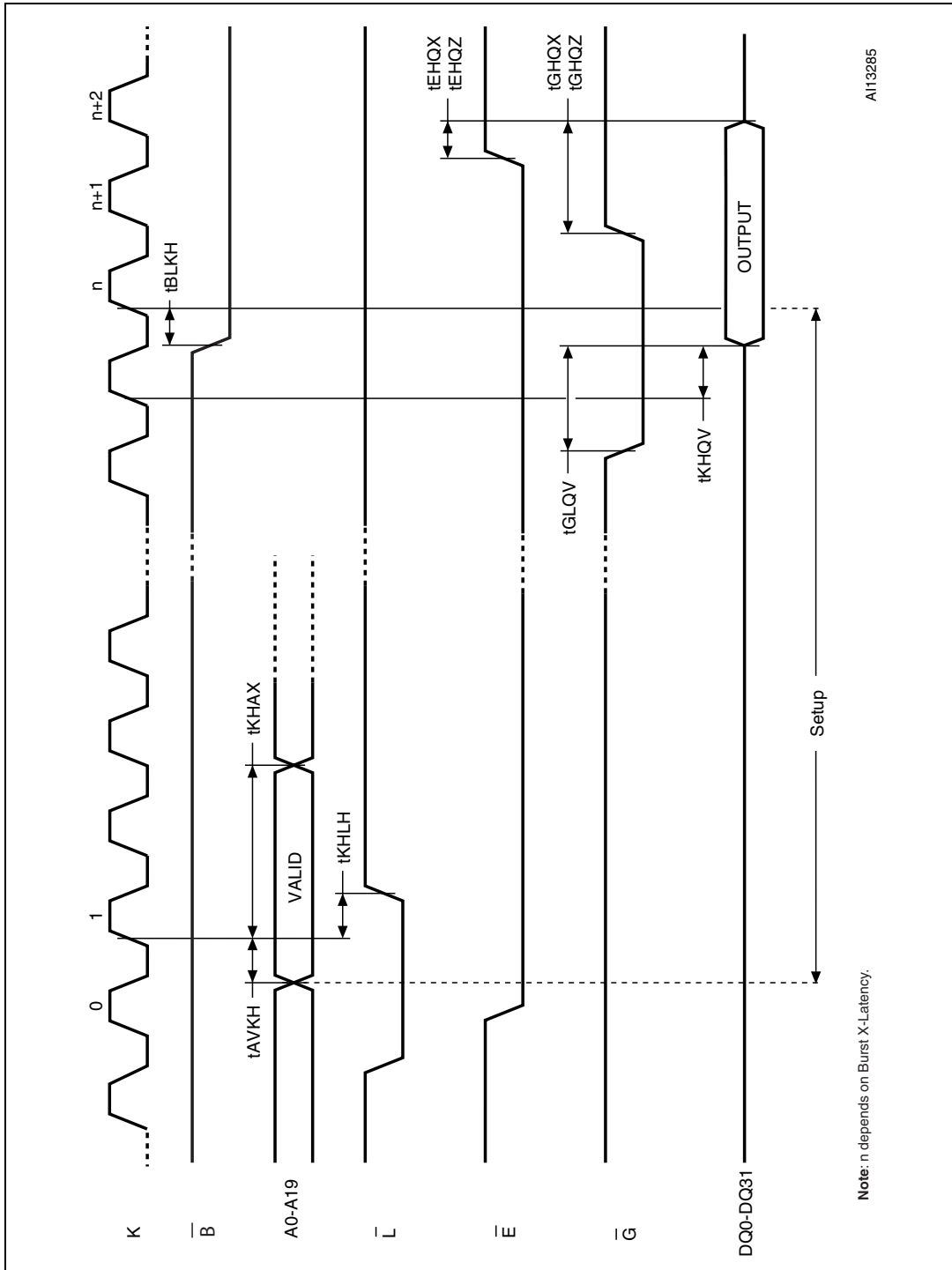




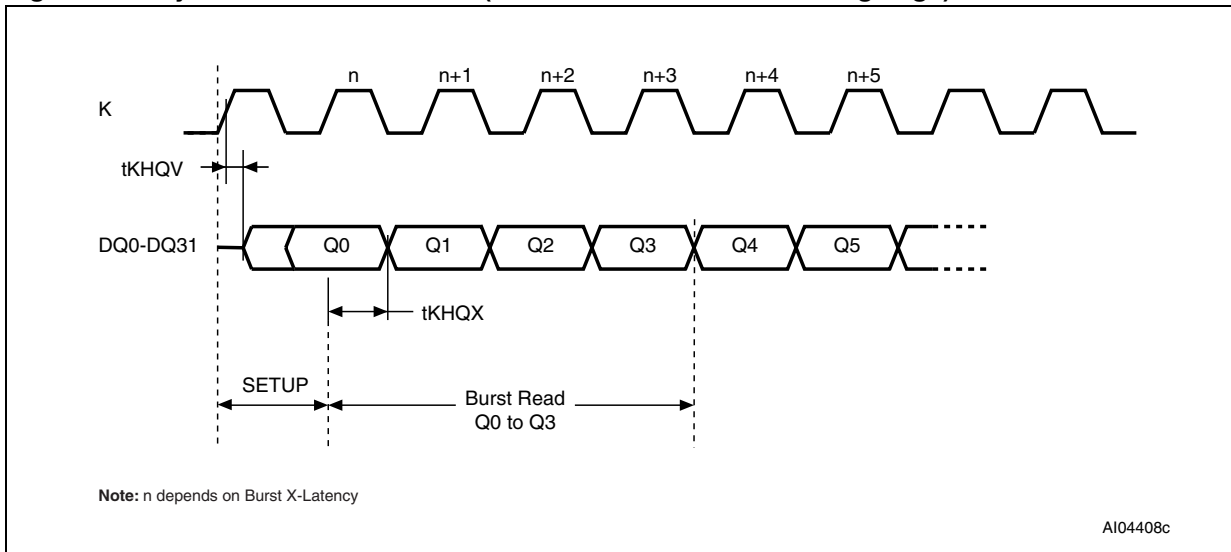
Figure 16. Synchronous Burst Read, Valid Address transition controlled (data valid from 'n' clock rising edge)



AI13285

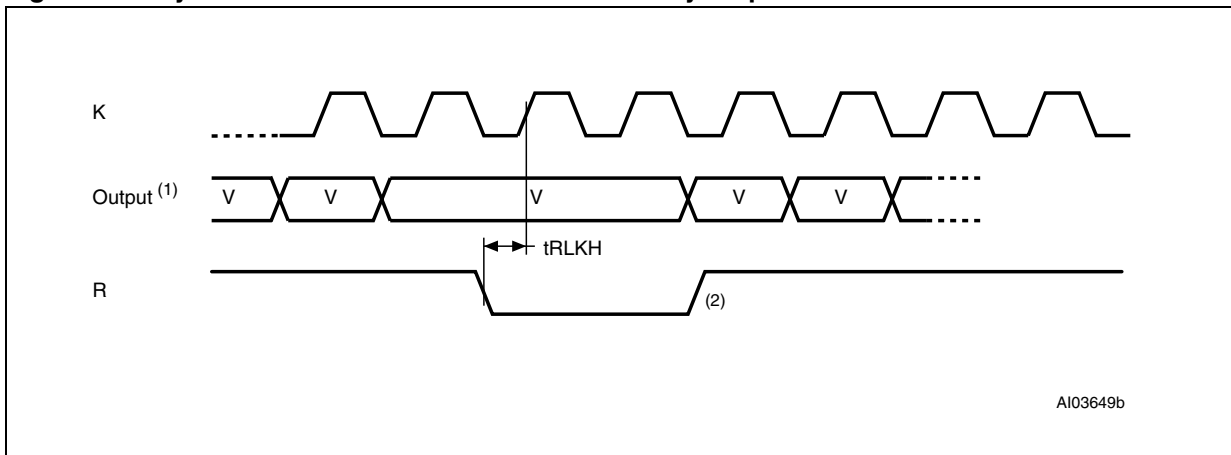
Note: n depends on Burst X-Latency.

**Figure 17. Synchronous Burst Read (data valid from 'n' clock rising edge)**



1. For set up signals and timings see Synchronous Burst Read.

**Figure 18. Synchronous Burst Read - valid data ready output**



- 1. Valid Data Ready = Valid Low during valid clock edge.
- 2. V= Valid output.
- 3. The internal timing of R follows DQ.

Figure 19. Synchronous Burst Read - Burst Address Advance

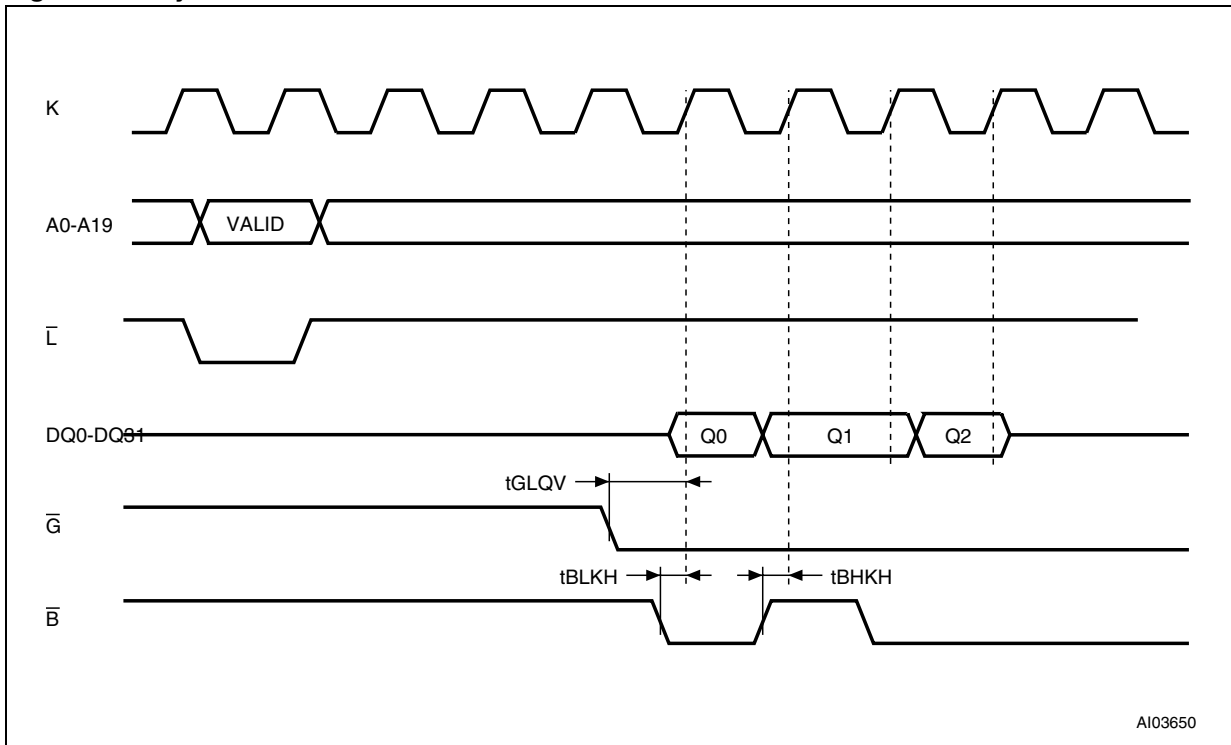


Figure 20. Clock input AC waveform

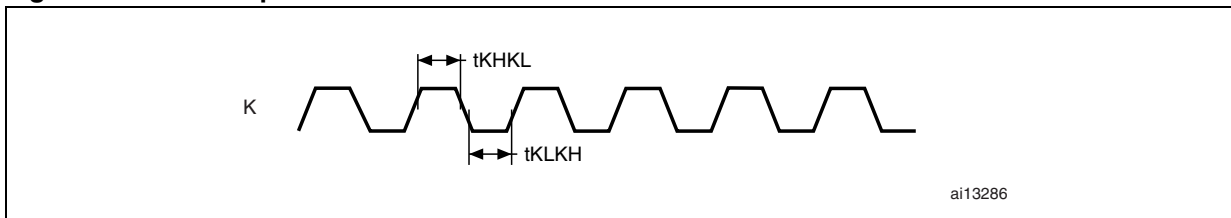
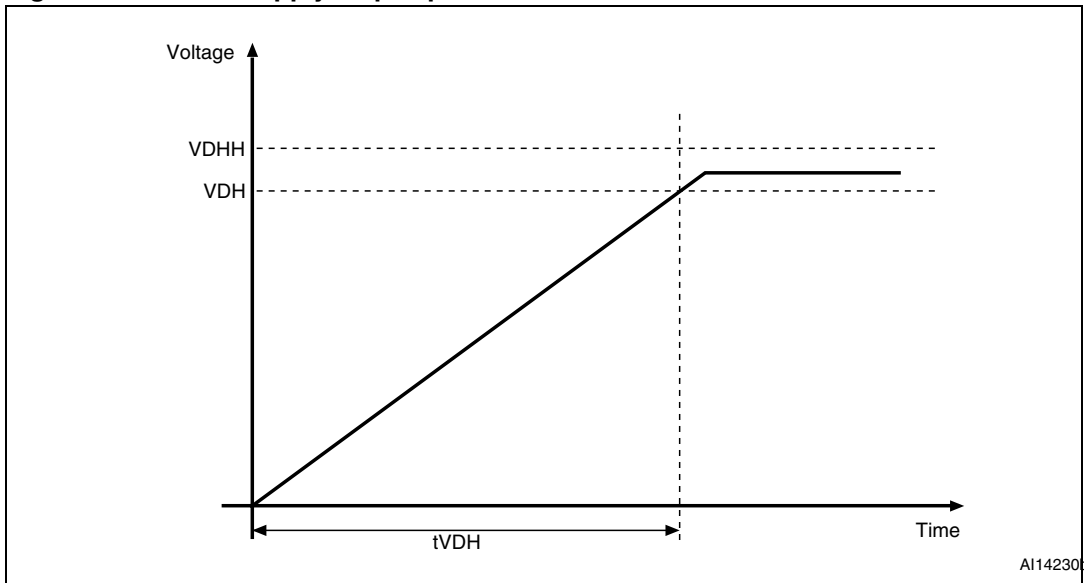


Table 22. Synchronous Burst Read AC characteristics<sup>(1)(2)</sup>

| Symbol            | Parameter                                      | Test condition                                                |          | M58BWxxF |    | Unit |    |
|-------------------|------------------------------------------------|---------------------------------------------------------------|----------|----------|----|------|----|
|                   |                                                |                                                               |          | 45       | 55 |      |    |
| f                 | Clock frequency                                | X-Latency = 3                                                 | Max      | 40       | 33 | MHz  |    |
|                   |                                                | X-Latency = 4                                                 | Max      | 56       | 40 | MHz  |    |
|                   |                                                | X-Latency = 5 or 6                                            | Max      | 75       | 56 | MHz  |    |
| t <sub>AVKH</sub> | Address Valid to Valid Clock Edge              | $\bar{E} = V_{IL}, \bar{L} = V_{IL}$<br>X-Latency = 3         | Min      | 12       | 13 | ns   |    |
|                   |                                                | $\bar{E} = V_{IL}, \bar{L} = V_{IL}$<br>X-Latency = 4, 5 or 6 | Min      | 6        | 7  | ns   |    |
| t <sub>KHKL</sub> | Clock High time                                |                                                               | Min      | 6        | 6  | ns   |    |
| t <sub>KLKH</sub> | Clock Low time                                 |                                                               | Min      | 6        | 6  | ns   |    |
| t <sub>BHKH</sub> | Burst Address Advance High to Valid Clock Edge | $\bar{E} = V_{IL}, \bar{G} = V_{IL}, \bar{L} = V_{IH}$        | Min      | 8        | 8  | ns   |    |
| t <sub>BLKH</sub> | Burst Address Advance Low to Valid Clock Edge  | $\bar{E} = V_{IL}, \bar{G} = V_{IL}, \bar{L} = V_{IH}$        | Min      | 8        | 8  | ns   |    |
| t <sub>ELKH</sub> | Chip Enable Low to Valid Clock Edge            | $\bar{L} = V_{IL}$<br>X-Latency = 3                           | Min      | 12       | 13 | ns   |    |
|                   |                                                | $\bar{L} = V_{IL}$<br>X-Latency = 4, 5 or 6                   | Min      | 6        | 7  | ns   |    |
| t <sub>GLQV</sub> | Output Enable Low to Output Valid              | $\bar{E} = V_{IL}, \bar{L} = V_{IH}$                          | Max      | 15       | 15 | ns   |    |
| t <sub>KHAX</sub> | Valid Clock Edge to Address Transition         | $\bar{E} = V_{IL}$                                            | Min      | 5        | 5  | ns   |    |
| t <sub>KHEL</sub> | Valid Clock Edge to Chip Enable Low            | $\bar{L} = V_{IL}$                                            | Min      | 0        | 0  | ns   |    |
| t <sub>KHLL</sub> | Valid Clock Edge to Latch Enable Low           | $\bar{E} = V_{IL}$                                            | Min      | 0        | 0  | ns   |    |
| t <sub>KHLH</sub> | Valid Clock Edge to Latch Enable High          | $\bar{E} = V_{IL}$                                            | Min      | 0        | 0  | ns   |    |
| t <sub>KHQX</sub> | Valid Clock Edge to Output Transition          | $\bar{E} = V_{IL}, \bar{G} = V_{IL}, \bar{L} = V_{IH}$        | Min      | 2        | 2  | ns   |    |
| t <sub>LLKH</sub> | Latch Enable Low to Valid Clock Edge           | $\bar{E} = V_{IL}$<br>X-Latency = 3                           | Min      | 12       | 13 | ns   |    |
|                   |                                                | $\bar{E} = V_{IL}$<br>X-Latency = 4, 5 or 6                   | M58BW16F | Min      | 6  | 5    | ns |
|                   |                                                |                                                               | M58BW32F | Min      | 6  | 7    | ns |
| t <sub>RLKH</sub> | Valid Data Ready Low to Valid Clock Edge       | $\bar{E} = V_{IL}, \bar{G} = V_{IL}, \bar{L} = V_{IH}$        | Min      | 6        | 6  | ns   |    |
| t <sub>KHQV</sub> | Valid Clock Edge to Output Valid               | $\bar{E} = V_{IL}, \bar{G} = V_{IL}, \bar{L} = V_{IH}$        | Max      | 8        | 8  | ns   |    |

1. Data output should be read on the valid clock edge.
2. For other timings see [Table 19: Asynchronous Bus Read AC characteristics](#).

Figure 21. Power supply slope specification



1. Please refer to the application note AN2601.

Table 23. Power supply AC and DC characteristics

| Symbol    | Description                                                 | Min         | Max   | Unit    |
|-----------|-------------------------------------------------------------|-------------|-------|---------|
| $V_{DH}$  | Minimum value of power supply ( $V_{DD}$ ) <sup>(1)</sup>   | $0.9V_{DD}$ |       | V       |
| $V_{DHH}$ | Maximum value of power supply ( $V_{DD}$ )                  |             | 3.6   | V       |
| $t_{VDH}$ | Time required from power supply to reach the $V_{DH}$ value | 300         | 50000 | $\mu s$ |

1. This threshold is 90% of the minimum value allowed to  $V_{DD}$ .

Figure 22. Reset, Power-down and Power-up AC waveforms - Control pins Low

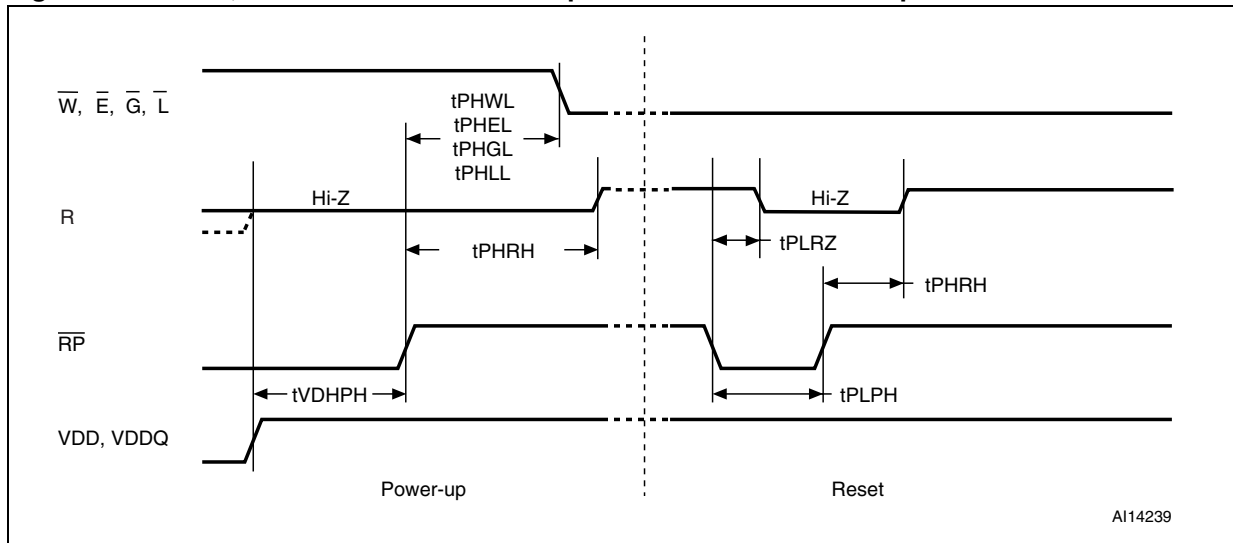


Figure 23. Reset, Power-down and Power-up AC waveforms - Control pins toggling

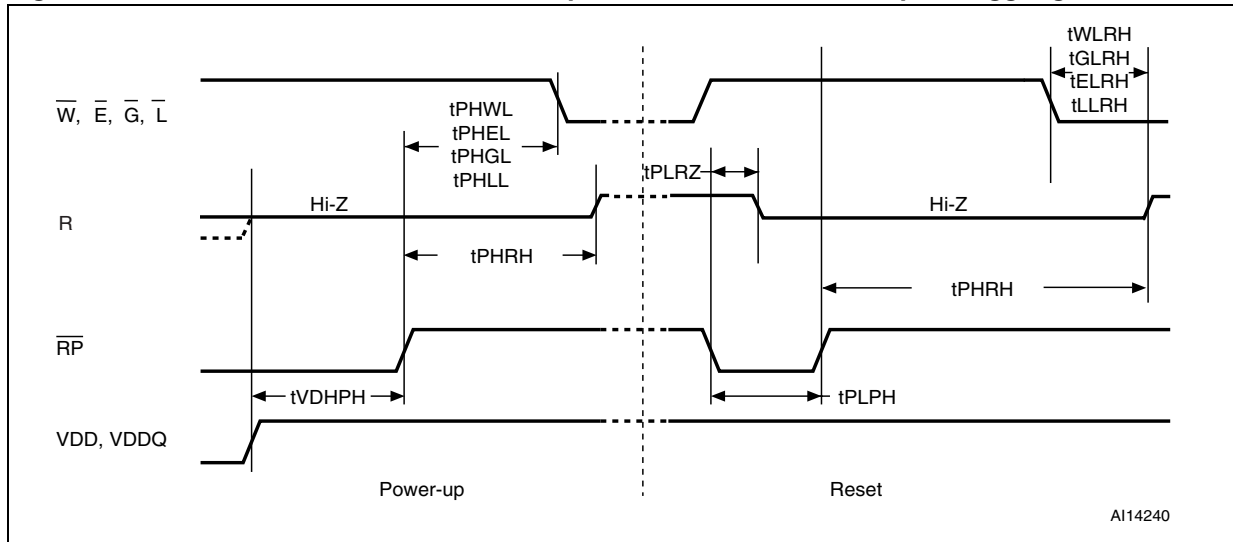


Table 24. Reset, Power-down and Power-up AC characteristics

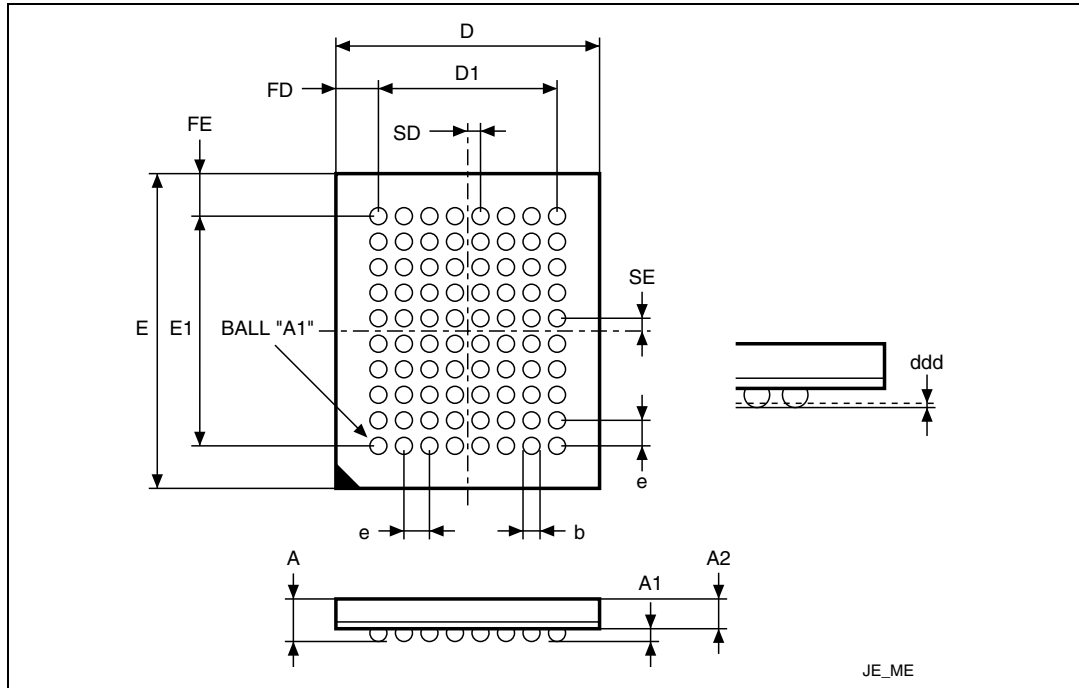
| Symbol           | Parameter                                         | Min | Max | Unit    |
|------------------|---------------------------------------------------|-----|-----|---------|
| $t_{PHEL}$       | Reset/Power-down High to Chip Enable Low          | 50  |     | ns      |
| $t_{PHLL}$       | Reset/Power-down High to Latch Enable Low         | 50  |     | ns      |
| $t_{PHQV}^{(1)}$ | Reset/Power-down High to Output Valid             |     | 95  | ns      |
| $t_{PHWL}$       | Reset/Power-down High to Write Enable Low         | 50  |     | ns      |
| $t_{PHGL}$       | Reset/Power-down High to Output Enable Low        | 50  |     | ns      |
| $t_{PLPH}$       | Reset/Power-down Low to Reset/Power-down High     | 100 |     | ns      |
| $t_{PHRH}^{(1)}$ | Reset/Power-down High to Valid Data Ready High    |     | 95  | ns      |
| $t_{VDHPH}$      | Supply voltages High to Reset/Power-down High     | 50  |     | $\mu$ s |
| $t_{PLRZ}$       | Reset/Power-down Low to Data Ready High Impedance |     | 80  | ns      |
| $t_{WLRH}$       | Write Enable Low to Data Ready High Impedance     |     | 80  | ns      |
| $t_{GLRH}$       | Output Enable Low to Data Ready High Impedance    |     | 80  | ns      |
| $t_{ELRH}$       | Chip Enable Low to Data Ready High Impedance      |     | 80  | ns      |
| $t_{LLRH}$       | Latch Enable Low to Data Ready High Impedance     |     | 80  | ns      |

1. This time is  $t_{PHEL} + t_{AVQV}$  or  $t_{PHEL} + t_{ELQV}$ .

## 8 Package mechanical

In order to meet environmental requirements, Numonyx offers these devices in ECOPACK® packages. ECOPACK® packages are lead-free. The category of second-level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label.

**Figure 24. LBG80 10 × 12 mm - 8 × 10 ball array, 1 mm pitch, bottom view package outline**



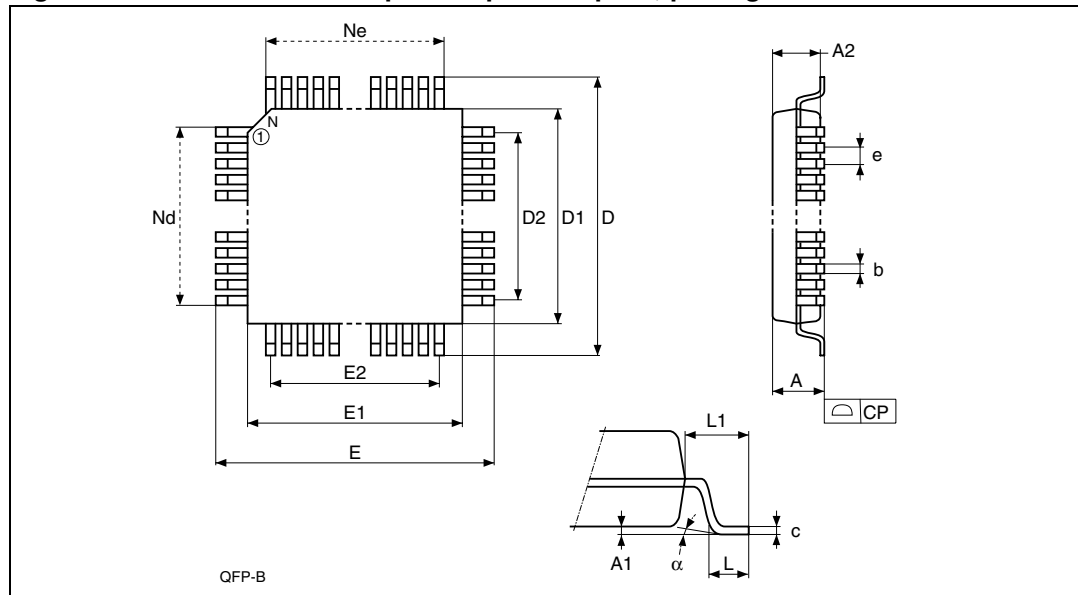
1. Drawing is not to scale.



**Table 25. LPGA80 10 × 12 mm - 8 × 10 active ball array, 1 mm pitch, package mechanical data**

| Symbol | millimeters |      |      | inches |       |       |
|--------|-------------|------|------|--------|-------|-------|
|        | Typ         | Min  | Max  | Typ    | Min   | Max   |
| A      |             |      | 1.60 |        |       | 0.063 |
| A1     |             | 0.40 |      |        | 0.016 |       |
| A2     |             |      | 1.05 |        |       | 0.041 |
| b      | 0.60        |      |      | 0.024  |       |       |
| D      | 10.00       | –    | –    | 0.394  | –     | –     |
| D1     | 7.00        | –    | –    | 0.276  | –     | –     |
| ddd    |             |      | 0.15 |        |       | 0.006 |
| E      | 12.00       | –    | –    | 0.472  | –     | –     |
| E1     | 9.00        | –    | –    | 0.354  | –     | –     |
| e      | 1.00        | –    | –    | 0.039  | –     | –     |
| FD     | 1.50        | –    | –    | 0.059  | –     | –     |
| FE     | 1.50        | –    | –    | 0.059  | –     | –     |
| SD     | 0.50        |      |      | 0.020  |       |       |
| SE     | 0.50        |      |      | 0.020  |       |       |

Figure 25. PQFP80 - 80 lead plastic quad flat pack, package outline



1. Drawing is not to scale.

Table 26. PQFP80 - 80 lead plastic quad flat pack, package mechanical data

| Symbol   | millimeters |       |       | inches |       |       |
|----------|-------------|-------|-------|--------|-------|-------|
|          | Typ         | Min   | Max   | Typ    | Min   | Max   |
| A        |             |       | 3.40  |        |       | 0.134 |
| A1       |             | 0.25  |       |        | 0.010 |       |
| A2       | 2.80        | 2.55  | 3.05  | 0.110  | 0.100 | 0.120 |
| b        |             | 0.30  | 0.45  |        | 0.012 | 0.018 |
| CP       |             |       | 0.10  |        |       | 0.004 |
| c        |             | 0.13  | 0.23  |        | 0.005 | 0.009 |
| D        | 23.20       | 22.95 | 23.45 | 0.913  | 0.903 | 0.923 |
| D1       | 20.00       | 19.90 | 20.10 | 0.787  | 0.783 | 0.791 |
| D2       | 18.40       | –     | –     | 0.724  | –     | –     |
| e        | 0.80        | –     | –     | 0.031  | –     | –     |
| E        | 17.20       | 16.95 | 17.45 | 0.677  | 0.667 | 0.687 |
| E1       | 14.00       | 13.90 | 14.10 | 0.551  | 0.547 | 0.555 |
| E2       | 12.00       | –     | –     | 0.472  | –     | –     |
| L        | 0.80        | 0.65  | 0.95  | 0.031  | 0.026 | 0.037 |
| L1       | 1.60        | –     | –     | 0.063  | –     | –     |
| $\alpha$ |             | 0°    | 7°    |        | 0°    | 7°    |
| N        |             | 80    |       |        | 80    |       |
| Nd       |             | 24    |       |        | 24    |       |
| Ne       |             | 16    |       |        | 16    |       |

## 9 Ordering information

**Table 27. Ordering information scheme**

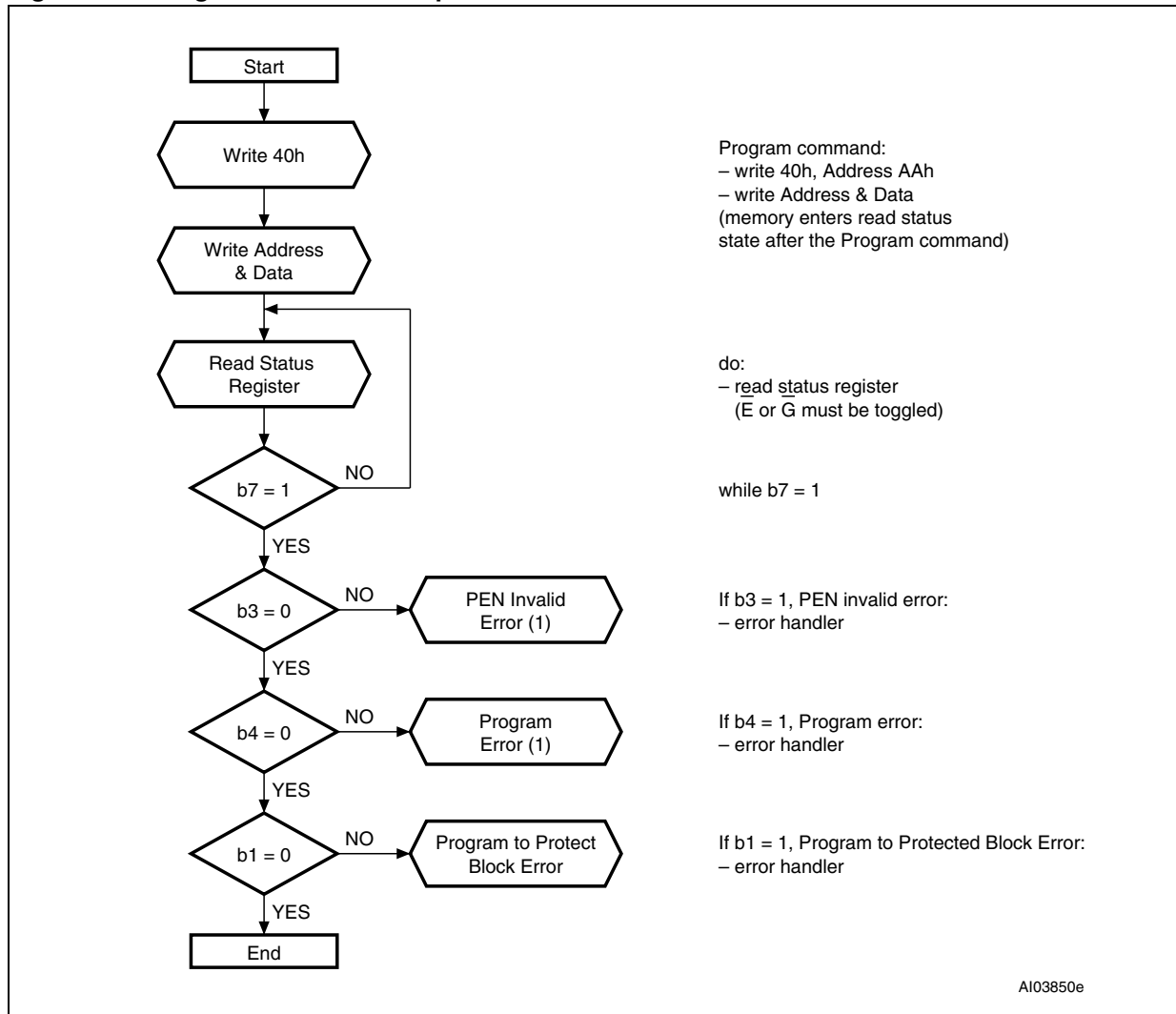
|                                                                                                                                                                                                                                                      |          |   |   |   |   |   |
|------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|----------|---|---|---|---|---|
| Example:                                                                                                                                                                                                                                             | M58BW32F | T | 4 | T | 3 | T |
| <b>Device type</b><br>M58                                                                                                                                                                                                                            |          |   |   |   |   |   |
| <b>Architecture</b><br>B = Burst mode                                                                                                                                                                                                                |          |   |   |   |   |   |
| <b>Operating voltage</b><br>W = [2.7 V to 3.6 V] V <sub>DD</sub> range for 45 ns speed class<br>[2.5 V to 3.3 V] V <sub>DD</sub> range for 55 ns speed class<br>[2.4 V to V <sub>DD</sub> ] V <sub>DDQ</sub> range for 45 ns and 55 ns speed classes |          |   |   |   |   |   |
| <b>Device function</b><br>32F = 32 Mbit (x 32), boot block, burst, 0.11 μm technology<br>16F = 16 Mbit (x 32), boot block, burst, 0.11 μm technology                                                                                                 |          |   |   |   |   |   |
| <b>Array matrix</b><br>T = Top boot<br>B = Bottom boot                                                                                                                                                                                               |          |   |   |   |   |   |
| <b>Speed</b><br>4 = 45 ns<br>5 = 55 ns                                                                                                                                                                                                               |          |   |   |   |   |   |
| <b>Package</b><br>T = PQFP80<br>ZA = LBGA80, 1.0 mm pitch                                                                                                                                                                                            |          |   |   |   |   |   |
| <b>Device grade</b><br>3 = Automotive grade certified <sup>(1)</sup> , -40 to 125 °C                                                                                                                                                                 |          |   |   |   |   |   |
| <b>Option</b><br>Blank = Standard packing<br>T = Tape & reel packing<br>F = ECOPACK® package, tape & reel 24 mm packing                                                                                                                              |          |   |   |   |   |   |

1. Qualified & characterized according to AEC Q100 & Q003 or equivalent, advanced screening according to AEC Q001 & Q002 or equivalent.

Devices are shipped from the factory with the memory content bits erased to '1'.  
For a list of available options (speed, package, etc) or for further information on any aspect of this device, please contact the Numonyx Sales Office nearest to you.

# Appendix A Flowcharts

Figure 26. Program flowchart and pseudocode



1. If an error is found, the Status Register must be cleared before further P/E operations.

Figure 27. Program Suspend & Resume flowchart and pseudocode

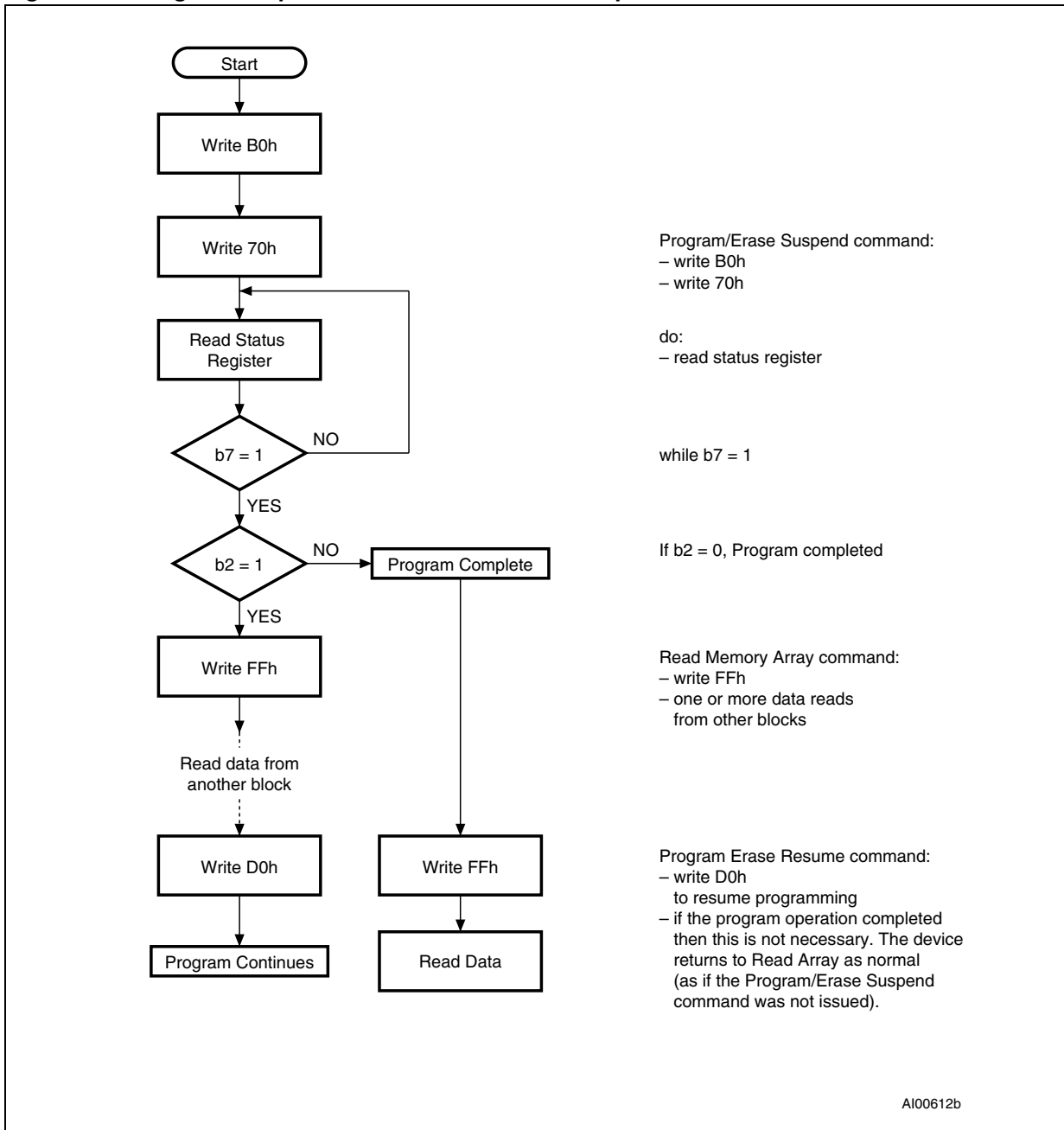
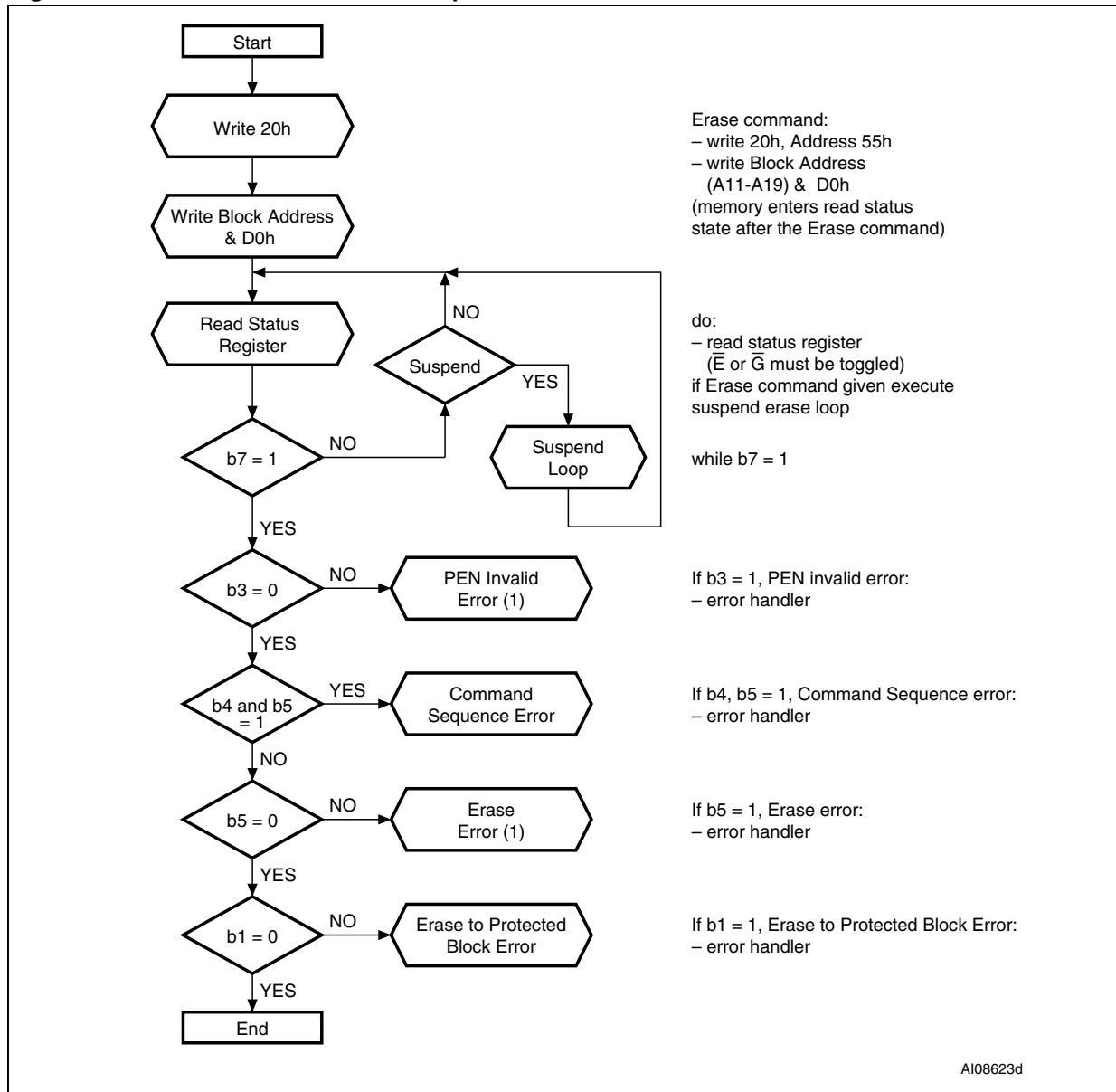


Figure 28. Block Erase flowchart and pseudocode



1. If an error is found, the Status Register must be cleared before further Program/Erase operations.

Figure 29. Erase Suspend & Resume flowchart and pseudocode

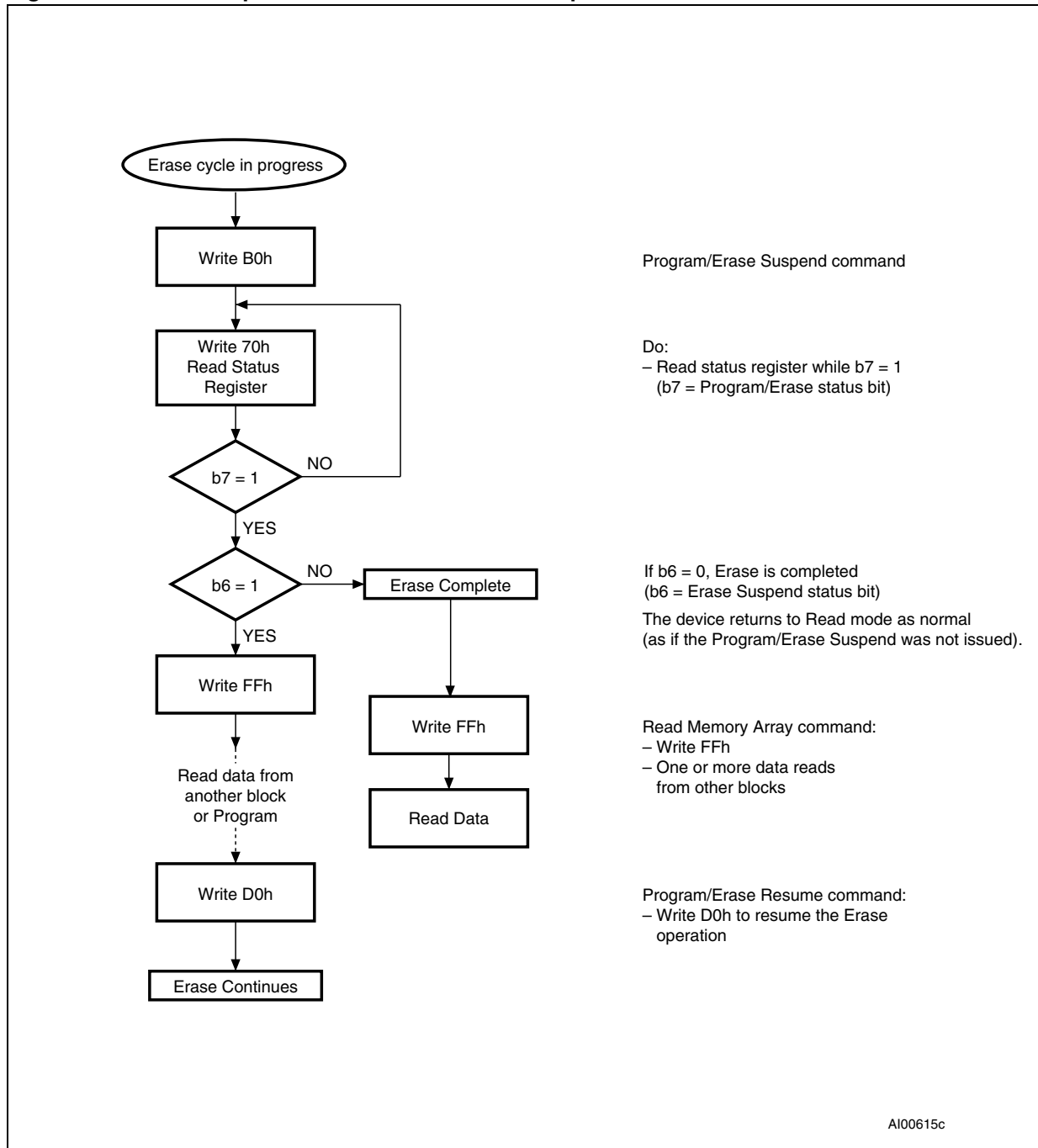


Figure 30. Power-up sequence followed by Synchronous Burst Read

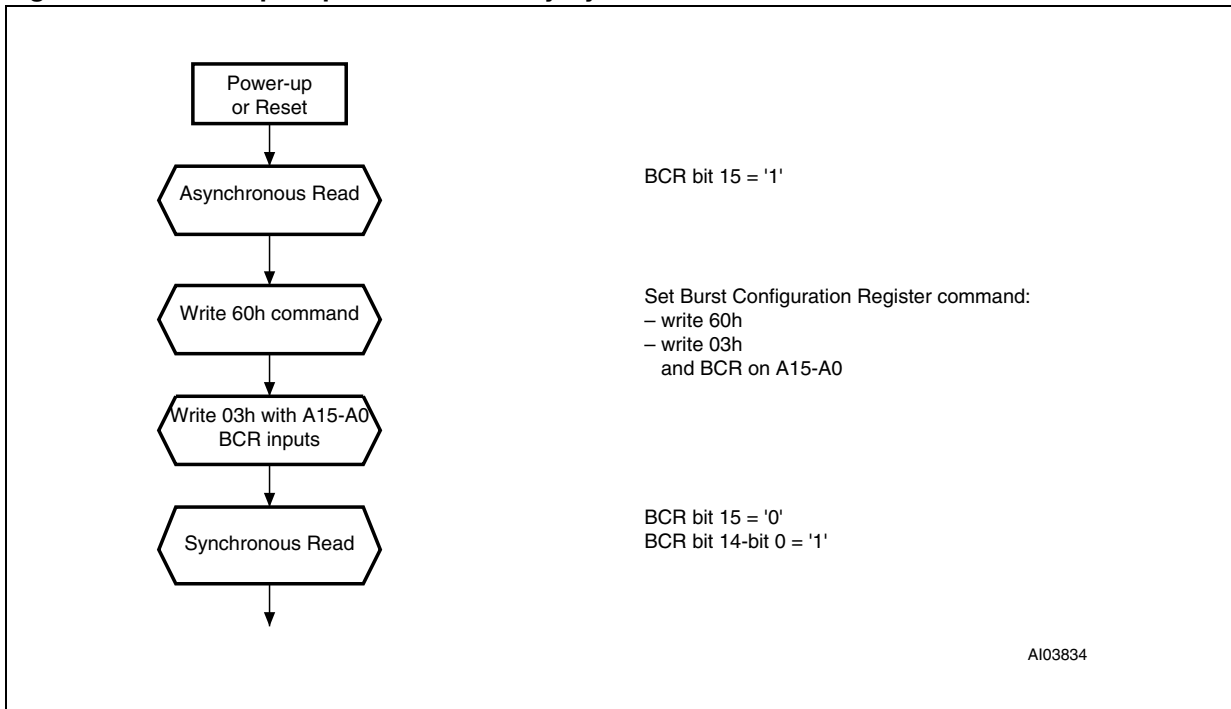
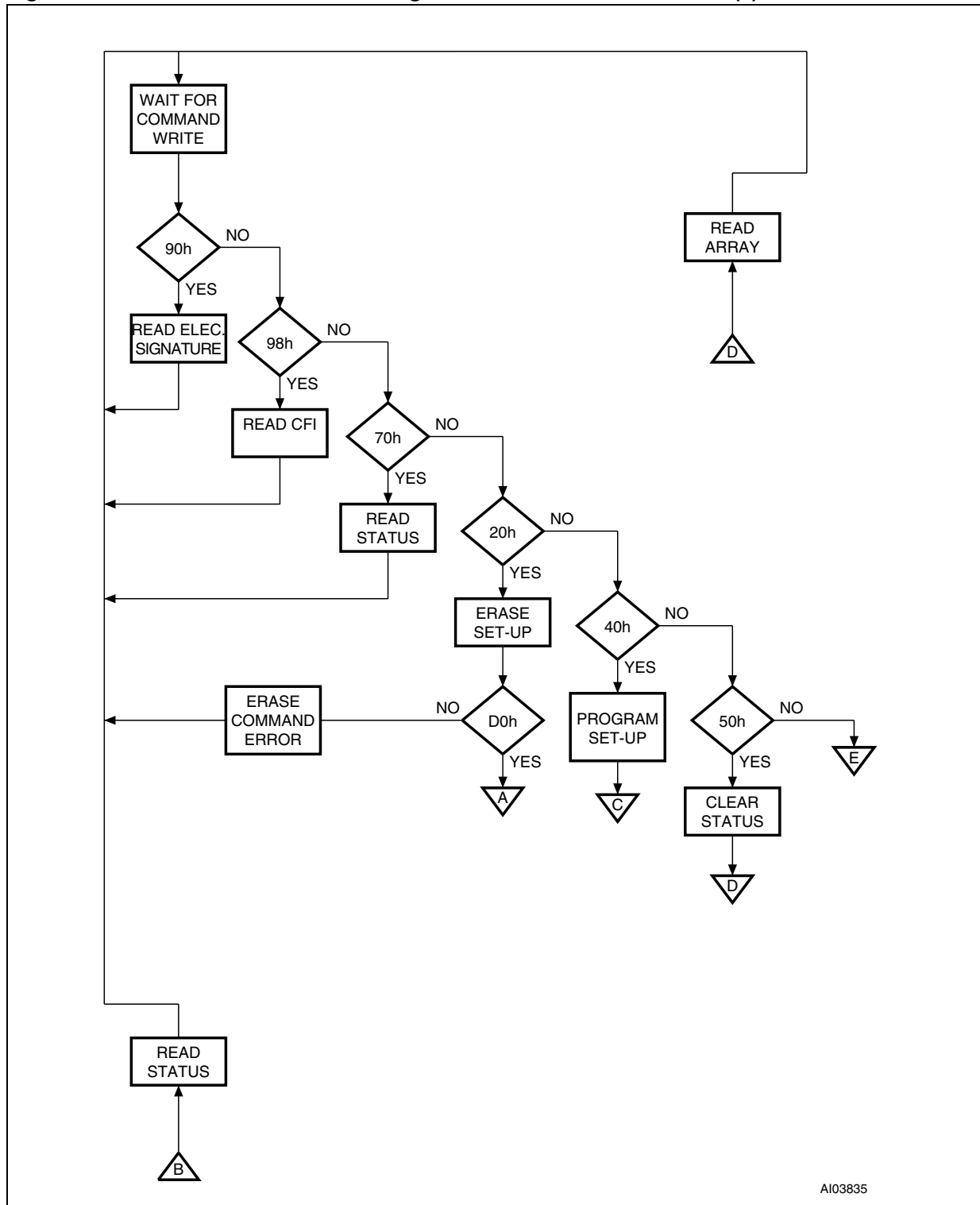




Figure 31. Command interface and Program/Erase controller flowchart (a)



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Figure 32. Command interface and Program/Erase controller flowchart (b)

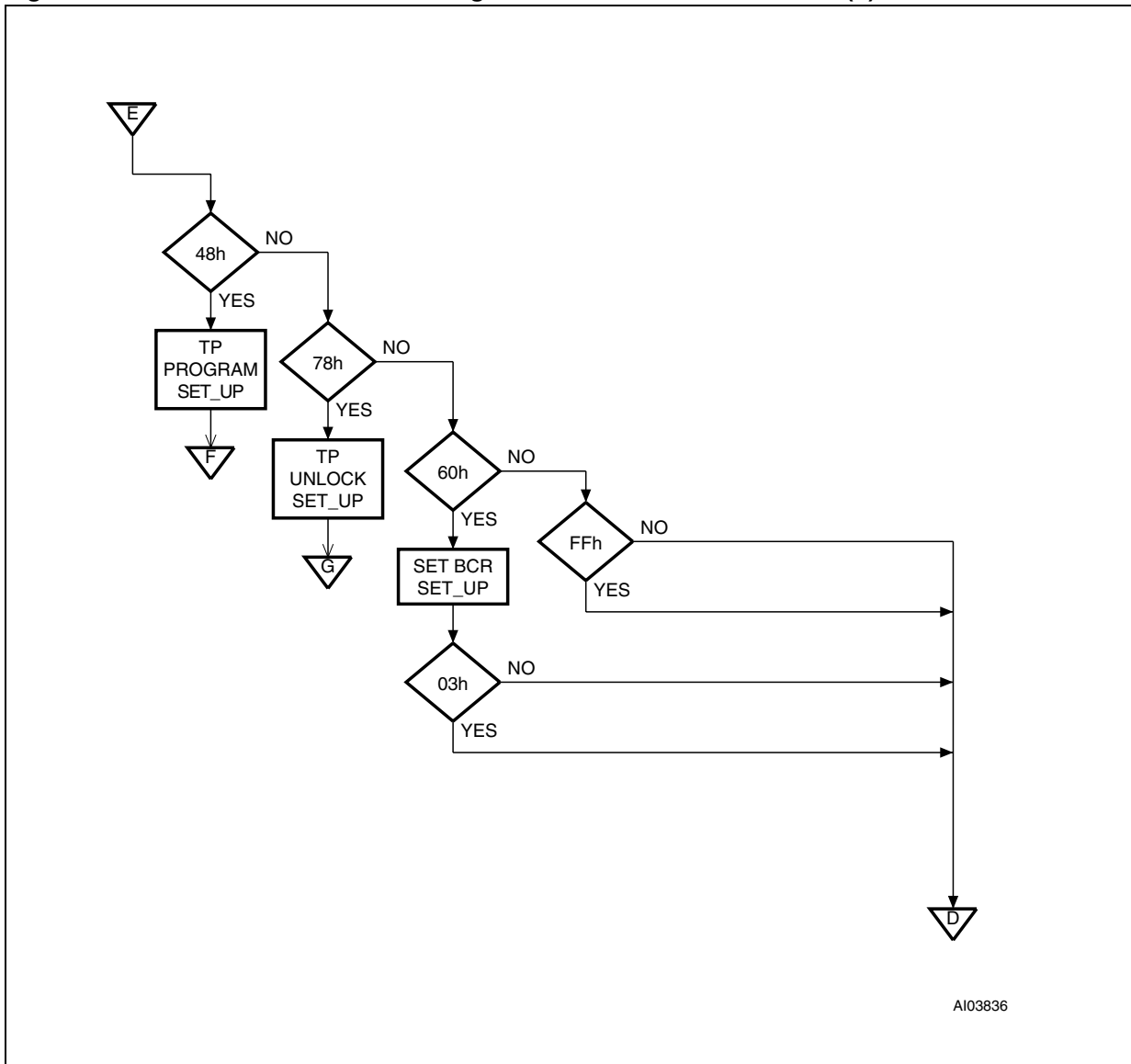


Figure 33. Command interface and Program/Erase controller flowchart (c)

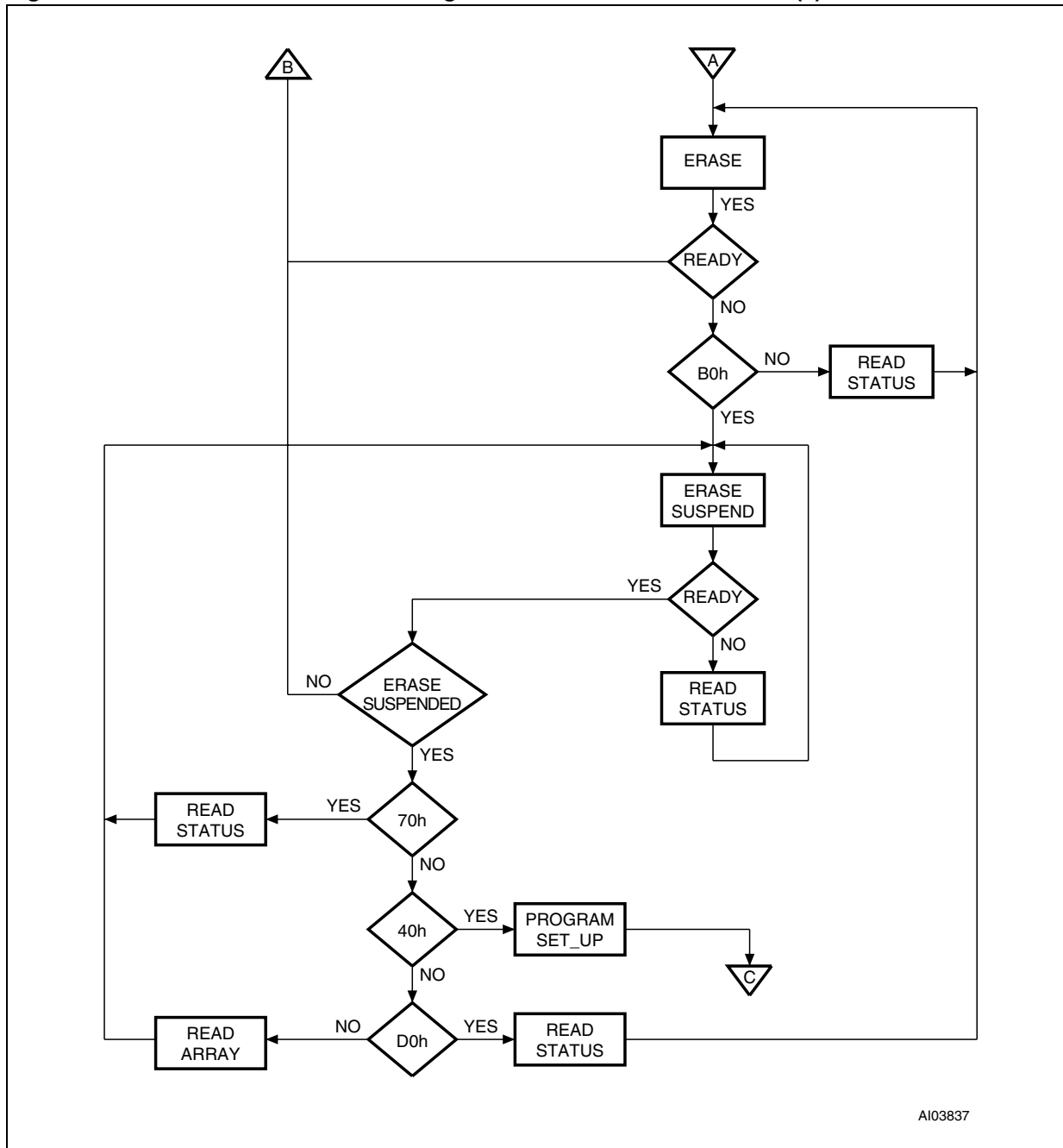
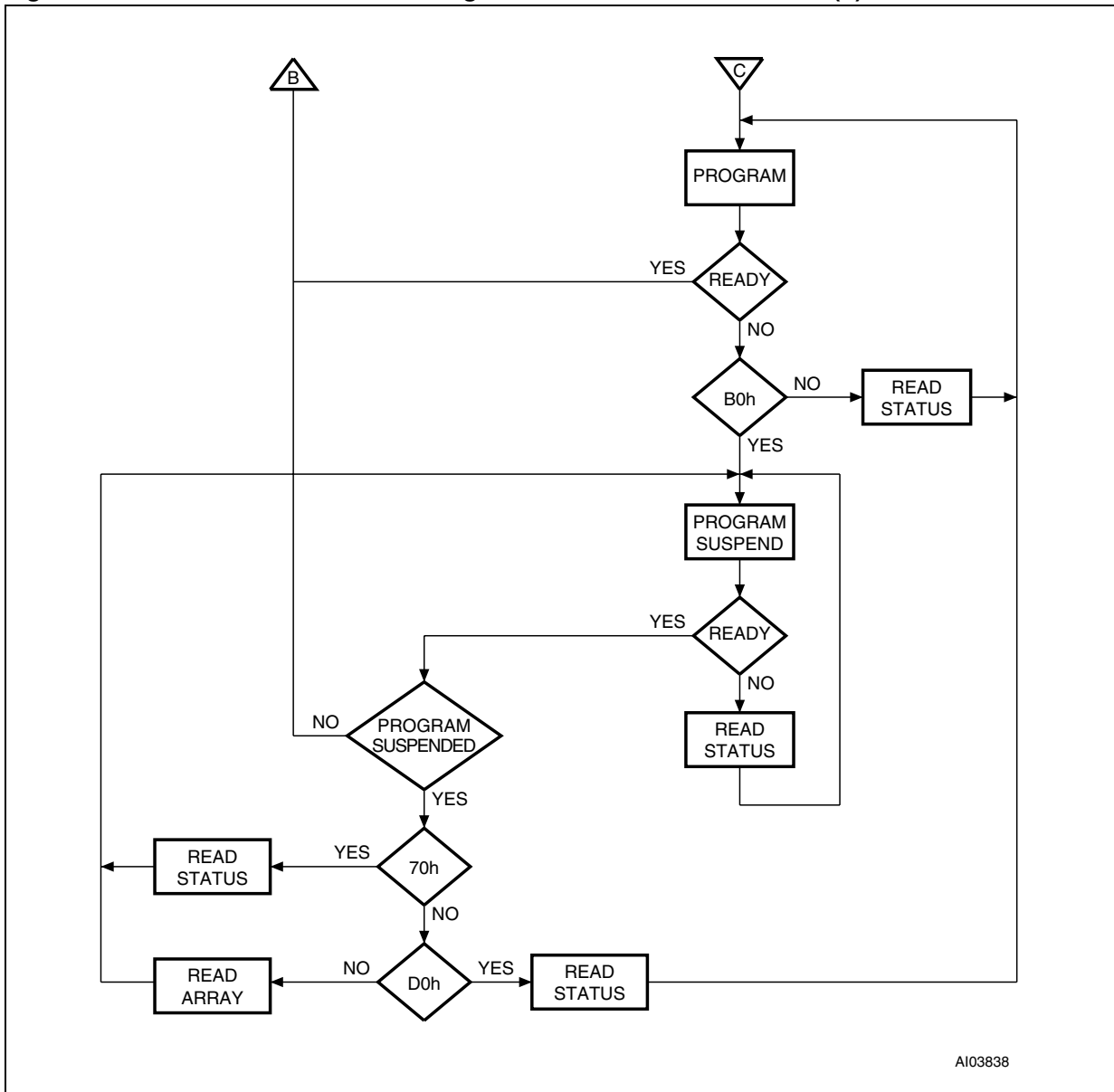
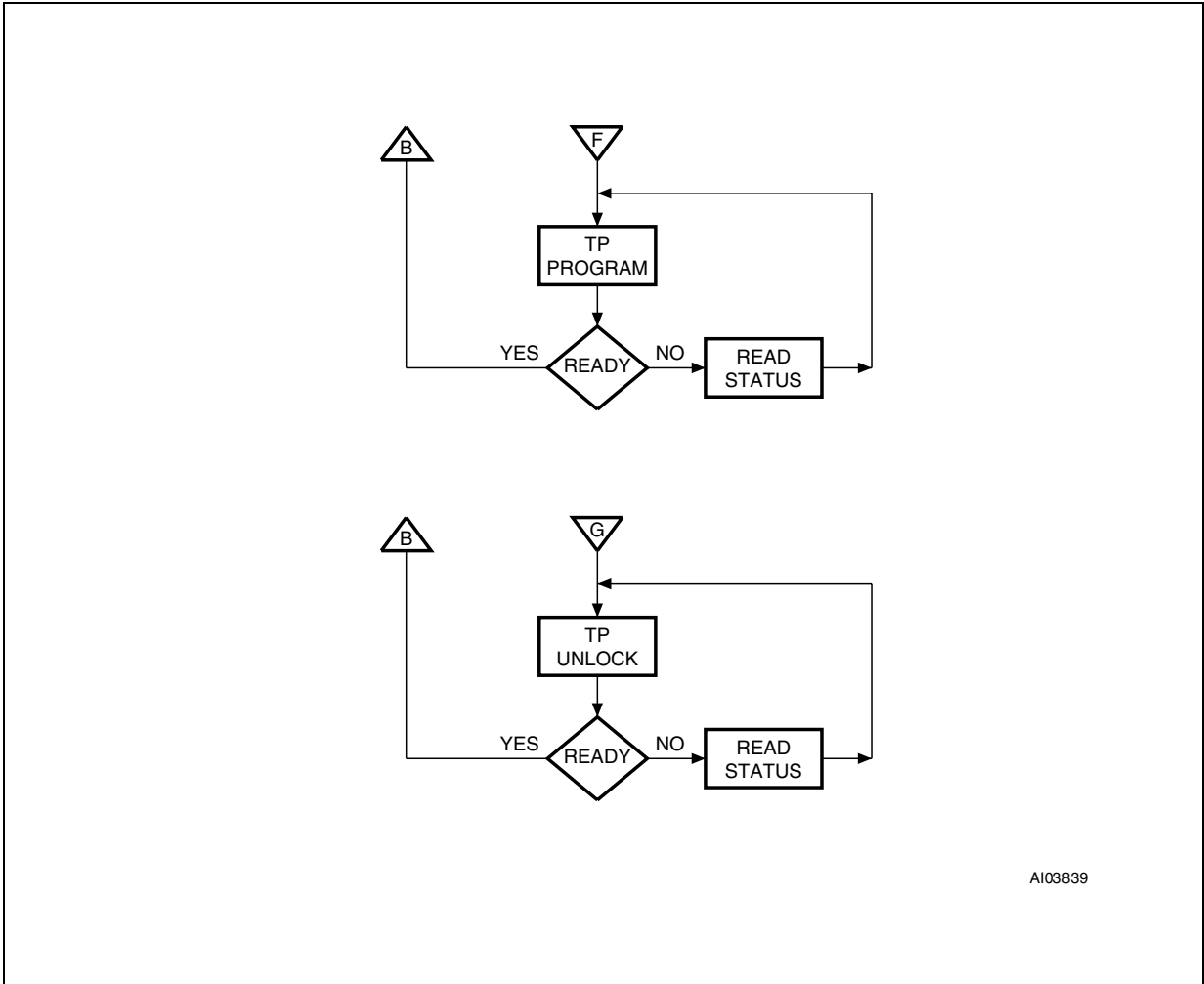


Figure 34. Command interface and Program/Erase controller flowchart (d)



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Figure 35. Command interface and Program/Erase controller flowchart (e)



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## Appendix B Common Flash interface (CFI)

The common Flash interface is a JEDEC approved, standardized data structure that can be read from the Flash memory device. It allows a system software to query the device to determine various electrical and timing parameters, density information and functions supported by the memory. The system can interface easily with the device, enabling the software to upgrade itself when necessary.

When the CFI Query command (RCFI) is issued the device enters CFI Query mode and the data structure is read from the memory. [Table 28](#), [Table 29](#), [Table 30](#), [Table 33](#) and [Table 32](#) show the addresses used to retrieve the data.

**Table 28. Query structure overview**

| Offset              | Sub-section name                                  | Description                                                           |                                                                                |
|---------------------|---------------------------------------------------|-----------------------------------------------------------------------|--------------------------------------------------------------------------------|
| 00h                 | 0020h                                             | Manufacturer code                                                     | Numonyx                                                                        |
| 01h                 | 883A<br>8839<br>8838<br>8837                      | Device code                                                           | M58BW16FT (top)<br>M58BW16FB (bottom)<br>M58BW32FT (top)<br>M58BW32FB (bottom) |
| 10h                 | CFI query identification string                   | Command set ID and algorithm data offset                              |                                                                                |
| 1Bh                 | System interface information                      | Device timing and voltage information                                 |                                                                                |
| 27h                 | Device geometry definition                        | Flash memory layout                                                   |                                                                                |
| P(h) <sup>(1)</sup> | Primary algorithm-specific extended query table   | Additional information specific to the primary algorithm (optional)   |                                                                                |
| A(h) <sup>(2)</sup> | Alternate algorithm-specific extended query table | Additional information specific to the alternate algorithm (optional) |                                                                                |

1. Offset 15h defines P which points to the primary algorithm extended query address table.
2. Offset 19h defines A which points to the alternate algorithm extended query address table.

**Table 29. CFI - Query address and data output<sup>(1)(2)</sup>**

| Address A0-Amax | Data                             |     | Instruction                                                    |
|-----------------|----------------------------------|-----|----------------------------------------------------------------|
| 10h             | 51h                              | "Q" | 51h; "Q"<br>Query ASCII string 52h; "R"<br>59h; "Y"            |
| 11h             | 52h                              | "R" |                                                                |
| 12h             | 59h                              | "Y" |                                                                |
| 13h             | 03h                              |     | Primary vendor:<br>Command set and control interface ID code   |
| 14h             | 00h                              |     |                                                                |
| 15h             | 35h (M58BW16F)<br>39h (M58BW32F) |     | Primary algorithm extended query address table:<br>P(h)        |
| 16h             | 00h                              |     |                                                                |
| 17h             | 00h                              |     | Alternate vendor:<br>Command set and control interface ID code |
| 18h             | 00h                              |     |                                                                |
| 19h             | 00h                              |     | Alternate algorithm extended query address table               |
| 1Ah             | 00h                              |     |                                                                |

1. The x 8 or byte address and the x 16 or word address mode are not available.
2. Query data are always presented on DQ7-DQ0. DQ31-DQ8 are set to '0'.

**Table 30. CFI - device voltage and timing specification**

| Address A0-Amax | Data               | Description                                             | Value |
|-----------------|--------------------|---------------------------------------------------------|-------|
| 1Bh             | 27h <sup>(1)</sup> | V <sub>DD</sub> min                                     | 2.7 V |
| 1Ch             | 36h <sup>(1)</sup> | V <sub>DD</sub> max                                     | 3.6 V |
| 1Dh             | xxxx xxxh          | Reserved                                                |       |
| 1Eh             | xxxx xxxh          | Reserved                                                |       |
| 1Fh             | 04h                | 2 <sup>n</sup> μs typical for word, double word program | 16 μs |
| 20h             | xxxx xxxh          | Reserved                                                |       |
| 21h             | 0Ah                | 2 <sup>n</sup> ms, typical time-out for Erase Block     | 1 s   |
| 22h             | xxxx xxxh          | Reserved                                                |       |
| 23h             | xxxx xxxh          | Reserved                                                |       |
| 24h             | xxxx xxxh          | Reserved                                                |       |
| 25h             | xxxx xxxh          | Reserved                                                |       |
| 26h             | xxxx xxxh          | Reserved                                                |       |

1. Bits are coded in binary code decimal, bit7 to bit4 are scaled in Volts and bit3 to bit0 in mV.

Table 31. M58BW16F device geometry definition

| Address A0-Amax | Data | Description                                                            | Value     |
|-----------------|------|------------------------------------------------------------------------|-----------|
| 27h             | 15h  | 2 <sup>n</sup> number of bytes memory size                             | 2 Mbytes  |
| 28h             | 03h  | Device interface sync./async.                                          | x 32      |
| 29h             | 00h  | Organization sync./async.                                              | Async.    |
| 2Ah             | 00h  | Maximum number of byte in multi-byte program = 2 <sup>n</sup>          | 32 bytes  |
| 2Bh             | 00h  |                                                                        |           |
| 2Ch             | 02h  | Bit7-0 = number of Erase Block regions in device                       | 2         |
| 2Dh             | 1Eh  | Number (n-1) of Erase Blocks of identical size; n=31                   | 31 blocks |
| 2Eh             | 00h  |                                                                        |           |
| 2Fh             | 00h  | Erase Block region information x 256 bytes per Erase Block (64 Kbytes) | 512 Kbits |
| 30h             | 01h  |                                                                        |           |
| 31h             | 07h  | Number (n-1) of Erase Blocks of identical size; n=8                    | 8 blocks  |
| 32h             | 00h  |                                                                        |           |
| 33h             | 20h  | Erase Block region information x 256 bytes per Erase Block (8 Kbytes)  | 64 Kbits  |
| 34h             | 00h  |                                                                        |           |



Table 32. M58BW16F extended query information

| Address offset  | Address Amax-A0 | Data (hex) |                                | Description                                                                                                                                                                                                                                                                                                                                                                                                                        |
|-----------------|-----------------|------------|--------------------------------|------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|
| (P)h            | 35h             | 50         | P                              | Query ASCII string - extended table                                                                                                                                                                                                                                                                                                                                                                                                |
| (P+1)h          | 36h             | 52         | R                              |                                                                                                                                                                                                                                                                                                                                                                                                                                    |
| (P+2)h          | 37h             | 49         | Y                              |                                                                                                                                                                                                                                                                                                                                                                                                                                    |
| (P+3)h          | 38h             | 31h        |                                | Major revision number                                                                                                                                                                                                                                                                                                                                                                                                              |
| (P+4)h          | 39h             | 31h        |                                | Minor revision number                                                                                                                                                                                                                                                                                                                                                                                                              |
| (P+5)h          | 3Ah             | 86h        |                                | Optional feature: (1=yes, 0=no)<br>bit0, Chip Erase supported (0=no)<br>bit1, Suspend Erase supported (1=yes)<br>bit2, Suspend Program supported (1=yes)<br>bit3, Lock/Unlock supported (0=no)<br>bit4, Queue Erase supported (0=no)<br>bit5, Instant individual block locking (0=no)<br>bit6, Protection bits supported (0=no)<br>bit7, Page Read supported (1=yes)<br>bit8, Synchronous Read supported (1=yes)<br>Bit9, Reserved |
| (P+6)h          | 3Bh             | 01h        |                                | Synchronous Read supported                                                                                                                                                                                                                                                                                                                                                                                                         |
| (P+7)h          | 3Ch             | 00h        |                                |                                                                                                                                                                                                                                                                                                                                                                                                                                    |
| (P+8)h          | 3Dh             | 00h        |                                |                                                                                                                                                                                                                                                                                                                                                                                                                                    |
| (P+9)h          | 3Eh             | 01h        |                                | Function allowed after Suspend:<br>Program allowed after Erase Suspend (1=yes)<br>Bit 7-1 reserved for future use                                                                                                                                                                                                                                                                                                                  |
| (P+A)h-(P+D)h   | 3Fh-42h         | Reserved   |                                |                                                                                                                                                                                                                                                                                                                                                                                                                                    |
| (P+13)h-(P+40)h | 48h-7Fh         | Reserved   |                                |                                                                                                                                                                                                                                                                                                                                                                                                                                    |
| (P+41)h         | 80h             | xxxx xxxxh | Unique device ID - 1 (16 bits) |                                                                                                                                                                                                                                                                                                                                                                                                                                    |
| (P+42)h         | 81h             | xxxx xxxxh | Unique device ID - 2 (16 bits) |                                                                                                                                                                                                                                                                                                                                                                                                                                    |
| (P+43)h         | 82h             | xxxx xxxxh | Unique device ID - 3 (16 bits) |                                                                                                                                                                                                                                                                                                                                                                                                                                    |
| (P+44)h         | 83h             | xxxx xxxxh | Unique device ID - 4 (16 bits) |                                                                                                                                                                                                                                                                                                                                                                                                                                    |

Table 33. M58BW32F device geometry definition

| Address A0-Amax | Data | Description                                                            | Value     |
|-----------------|------|------------------------------------------------------------------------|-----------|
| 27h             | 15h  | 2 <sup>n</sup> number of bytes memory size                             | 4 Mbytes  |
| 28h             | 03h  | Device interface sync./async.                                          | x 32      |
| 29h             | 00h  | Organization sync./async.                                              | Async.    |
| 2Ah             | 00h  | Maximum number of byte in multi-byte program = 2 <sup>n</sup>          | 32 bytes  |
| 2Bh             | 00h  |                                                                        |           |
| 2Ch             | 02h  | Bit7-0 = number of Erase Block regions in device                       | 3         |
| 2Dh             | 1Eh  | Number (n-1) of Erase Block regions of identical size;<br>n = 31       | 62 blocks |
| 2Eh             | 00h  |                                                                        |           |
| 2Fh             | 00h  | Erase Block region information x 256 bytes per Erase Block (64 Kbytes) | 512 Kbits |
| 30h             | 01h  |                                                                        |           |
| 31h             | 07h  | Number (n-1) of Erase blocks of identical size; n = 8                  | 8 blocks  |
| 32h             | 00h  |                                                                        |           |
| 33h             | 20h  | Erase Block region information x 256 bytes per Erase Block (8 Kbytes)  | 64 Kbits  |
| 34h             | 00h  |                                                                        |           |
| 35h             | 03h  | Number (n-1) of Erase Block of identical size; n = 8                   | 8 blocks  |
| 36h             | 00h  |                                                                        |           |
| 37h             | 40h  | Erase Block region information x 256 bytes per Erase block (16 Kbytes) | 128 Kbits |
| 38h             | 00h  |                                                                        |           |

Table 34. M58BW32F extended query information

| Address offset  | Address Amax-A0 | Data (hex) |                                | Description                                                                                                                                                                                                                                                                                                                                                                                                                         |
|-----------------|-----------------|------------|--------------------------------|-------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|
| (P)h            | 39h             | 50         | P                              | Query ASCII string - extended table                                                                                                                                                                                                                                                                                                                                                                                                 |
| (P+1)h          | 3Ah             | 52         | R                              |                                                                                                                                                                                                                                                                                                                                                                                                                                     |
| (P+2)h          | 3Bh             | 49         | Y                              |                                                                                                                                                                                                                                                                                                                                                                                                                                     |
| (P+3)h          | 3Ch             | 31h        |                                | Major revision number                                                                                                                                                                                                                                                                                                                                                                                                               |
| (P+4)h          | 3Dh             | 31h        |                                | Minor revision number                                                                                                                                                                                                                                                                                                                                                                                                               |
| (P+5)h          | 3Eh             | 86h        |                                | Optional feature: (1=yes, 0=no)<br>bit0, Chip Erase supported (0=no)<br>bit1, Suspend Erase supported (1=yes)<br>bit2, Suspend Program supported (1=yes)<br>bit3, Lock/Unlock supported (0=no)<br>bit4, Queue Erase supported (0=no)<br>bit5, Instant individual block locking (0=no)<br>bit6, Protection bits supported (0=no)<br>bit7, Page Read supported (1=yes)<br>bit8, Synchronous Read supported (1=yes)<br>Bit 9, Reserved |
| (P+6)h          | 3Fh             | 01h        |                                | Synchronous Read supported                                                                                                                                                                                                                                                                                                                                                                                                          |
| (P+7)h          | 40h             | 00h        |                                |                                                                                                                                                                                                                                                                                                                                                                                                                                     |
| (P+8)h          | 41h             | 00h        |                                |                                                                                                                                                                                                                                                                                                                                                                                                                                     |
| (P+9)h          | 42h             | 01h        |                                | Function allowed after Suspend:<br>Program allowed after Erase Suspend (1=yes)<br>Bit 7-1 reserved for future use                                                                                                                                                                                                                                                                                                                   |
| (P+A)h-(P+D)h   | 43h-46h         | Reserved   |                                |                                                                                                                                                                                                                                                                                                                                                                                                                                     |
| (P+13)h-(P+40)h | 4Ch-7Fh         | Reserved   |                                |                                                                                                                                                                                                                                                                                                                                                                                                                                     |
| (P+41)h         | 80h             | xxxx xxxh  | Unique device ID - 1 (16 bits) |                                                                                                                                                                                                                                                                                                                                                                                                                                     |
| (P+42)h         | 81h             | xxxx xxxh  | Unique device ID - 2 (16 bits) |                                                                                                                                                                                                                                                                                                                                                                                                                                     |
| (P+43)h         | 82h             | xxxx xxxh  | Unique device ID - 3 (16 bits) |                                                                                                                                                                                                                                                                                                                                                                                                                                     |
| (P+44)h         | 83h             | xxxx xxxh  | Unique device ID - 4 (16 bits) |                                                                                                                                                                                                                                                                                                                                                                                                                                     |

**Table 35. Protection register information**

| Address<br>A0-Amax | Data                   |                        | Instruction                                                                                                                                                                                                                                               | Value                  |                          |
|--------------------|------------------------|------------------------|-----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|------------------------|--------------------------|
|                    | M58BW16FT<br>M58BW16FB | M58BW32FT<br>M58BW32FB |                                                                                                                                                                                                                                                           | M58BW16FT<br>M58BW16FB | M58BW32FT<br>M58BW32FB   |
| (P+E)h             | 0x02<br>0x02           | 0x01<br>0x01           | Number of Protection register field in JEDEC ID space, Block region information X256 bytes                                                                                                                                                                | 2 x 64 Kb<br>2 x 64 Kb | 1 x 128 Kb<br>1 x 128 Kb |
| (P+F)h             | 0x01<br>0xFE           | 0x01<br>0xFE           | Protection field: this field describes user-available OTP Protection Register bytes.<br>Bits 7-0=physical low address<br>Bits 15-8=physical high address<br>Bits 23-16='n', 2n=Factory pre-programmed bytes<br>Bits 31-24='n', 2n=user programmable bytes | -                      | -                        |
| (P+10)h            | 0x01<br>0xFE           | 0x01<br>0xFE           |                                                                                                                                                                                                                                                           | -                      | -                        |
| (P+11)h            | 0x0<br>0x0             | 0x0<br>0x0             |                                                                                                                                                                                                                                                           | -                      | -                        |
| x256               | 0x12<br>0x12           | 0x12<br>0x12           |                                                                                                                                                                                                                                                           | 2 x 64 Kb<br>2 x 64 Kb | 1 x 128 Kb<br>1 x 128 Kb |

## Appendix C Block protection

### OTP protection

The OTP protection is an user-enabled feature that permanently protects specific blocks, so called "OTP blocks", against modify operations (program/erase). It is available:

- on one specific 128-kbit parameter block in the M58BW32F- block 1 (01000h-01FFFh) for bottom devices or block 72 (FE000h-FEFFFh) for top devices
- on two specific 64-kbit parameter blocks in the M58BW16F- block 2 and 3 (01000h-01FFFh) for bottom devices or block 36 and 35 (7E000h-7EFFFh) for top devices.

The default state is unprotected. However, once the protection has been enabled, it is impossible to disable it and the OTP blocks will remain "modify protected" for ever.

Obviously, this information is stored in internal non volatile registers.

### Activation sequence

If the user wants to make the OTP protection effective on a part, he has to issue the Lock OTP protection command.

The Lock OTP protection requires 2 write cycles:

- write (ADD=000AAh, DATA=49h) - Lock OTP Protection command 1
- write (ADD=00003h, DATA=0000 0000h) - Lock OTP Protection command 2

This sequence of commands has to be given with the Tuning Protection unlocked (if this protection is enabled on the part) and with Write Protect Enable WP\_N='1'. The user can check its execution polling on the SR in the same way as a normal Program Word command.

The program duration lasts about 35  $\mu$ s like for a standard Program Word command. It is also possible to detect the end of the operation by polling the Status Register.

Any Erase attempt returns A3h in the Status Register while any Program attempt returns 93h.

Once the first write cycle of the Lock OTP protection command is issued, a wrong address on second write cycle will cause the activation sequence to fail. The Status Register allows detecting this event and its value is then B1h (invalid sequence).

As a consequence, the protection is not active and the sequence must be restarted.

The Lock OTP Protection command cannot be suspended.

## 10 Revision history

**Table 36. Document revision history**

| Date        | Revision | Changes                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                          |
|-------------|----------|--------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|
| 09-Jun-2006 | 1        | Initial release.                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                 |
| 23-Nov-2006 | 2        | <p><math>V_{PEN}</math> signal renamed as PEN and <i>Program/Erase Enable (PEN)</i> modified.</p> <p>Continuous burst and wrap options are not available, X-Latencies 7 and 8 removed (see <i>Table 8: Burst Configuration Register</i> and <i>Table 9: Burst type definition</i>). Notes removed below <i>Table 8</i>.</p> <p><math>t_{WHQV}</math> timing modified in <i>Table 21: Asynchronous Write and Latch controlled Write AC characteristics</i>.</p> <p><math>I_{DD}</math> max modified and <math>I_{DD4}</math> added to <i>Table 18: DC characteristics</i>.</p> <p><math>t_{AXQX}</math> modified in <i>Table 20: Asynchronous Page Read AC characteristics</i>.</p> <p>Read access specified in <i>Asynchronous Bus Read</i> and <i>Synchronous Burst Read</i>.</p> <p><math>t_{AVKH}</math> and <math>t_{ALKH}</math> added and <math>t_{KHQV}</math> for 55 ns modified in <i>Table 22: Synchronous Burst Read AC characteristics</i>. <i>Figure 9</i>, <i>Figure 10</i>, <i>Figure 18</i> and <i>Figure 19</i> added. Double Word Program max modified and Minimum effective erase time added to <i>Table 12: Program, Erase times and endurance cycles</i>.</p> <p>All Asynchronous Bus Read AC characteristics brought together in <i>Table 19: Asynchronous Bus Read AC characteristics</i>. <math>t_{LLEL}</math> removed from <i>Table 19</i> and <i>Figure 7. Appendix B: Common Flash interface (CFI)</i> modified.</p> |
| 01-Oct-2007 | 3        | <p><i>Table 8: Burst Configuration Register</i>, <i>Table 30: CFI - device voltage and timing specification</i> and <i>Table 33: M58BW32F device geometry definition</i> updated.</p> <p>Minimum values for <math>t_{KHKL}</math>, <math>t_{KLKH}</math> and <math>t_{LLKH}</math> modified in <i>Table 22: Synchronous Burst Read AC characteristics</i>.</p> <p><math>t_{PHLL}</math>, <math>t_{PHRH}</math>, <math>t_{VDHPH}</math>, <math>t_{WLRH}</math>, <math>t_{GLRH}</math>, <math>t_{ELRH}</math>, and <math>t_{LLRH}</math> added in <i>Table 24: Reset, Power-down and Power-up AC characteristics</i>.</p> <p><math>t_{PLRH}</math> removed from <i>Table 24</i>.</p> <p>Modified <i>Figure 22: Reset, Power-down and Power-up AC waveforms - Control pins Low</i> and <i>Section 3.3.3: X-Latency bits (M13-M11)</i>.</p> <p><i>Appendix C: Block protection</i>, <i>Figure 23: Reset, Power-down and Power-up AC waveforms - Control pins toggling</i> and <i>Table 35: Protection register information</i> added.</p>                                                                                                                                                                                                                                                                                                                                                                                                            |
| 15-Jan-2008 | 4        | <p>Updated mechanical data of the LBGGA package and <i>Table 8: Burst Configuration Register</i>, <i>Table 12: Program, Erase times and endurance cycles</i>, <i>Table 18: DC characteristics</i>, <i>Table 21: Asynchronous Write and Latch controlled Write AC characteristics</i>, <i>Table 22: Synchronous Burst Read AC characteristics</i>, and <i>Section 2.7: Reset/Power-down (RP)</i>.</p> <p>Added <i>Figure 21: Power supply slope specification</i> and <i>Table 23: Power supply AC and DC characteristics</i>.</p> <p>Minor text changes.</p>                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                     |
| 19-Mar-2008 | 5        | Applied Numonyx branding.                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                        |

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